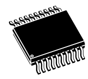
# STM32G050x6/x8

## $Arm^{®}$ $Cortex^{®}$-M0+ 32-bit MCU, up to 64 KB Flash, 18 KB RAM, 2x USART, timers, ADC, comm. I/Fs, 2.0-3.6 V

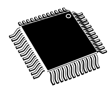
**Datasheet - production data**

## Features

- Includes ST state-of-the-art patented technology
- Core: $Arm^{®}$ 32-bit $Cortex^{®}$-M0+ CPU, frequency up to 64 MHz
- -40°C to 85°C operating temperature
- Memories
  - Up to 64 Kbytes of flash memory with protection
  - 18 Kbytes of SRAM (16 Kbytes with HW parity check)
- CRC calculation unit
- Reset and power management
  - Voltage range: 2.0 V to 3.6 V
  - Power-on/Power-down reset (POR/PDR)
  - Low-power modes:<br>Sleep, Stop, Standby
  - $V_{BAT}$ supply for RTC and backup registers
- Clock management
  - 4 to 48 MHz crystal oscillator
  - 32 kHz crystal oscillator with calibration
  - Internal 16 MHz RC with PLL option
  - Internal 32 kHz RC oscillator (±5 %)
- Up to 44 fast I/Os
  - All mappable on external interrupt vectors
  - Multiple 5 V-tolerant I/Os
- 7-channel DMA controller with flexible mapping
- 12-bit, 0.4 µs ADC (up to 16 ext. channels)
  - Up to 16-bit with hardware oversampling
  - Conversion range: 0 to 3.6V
- 14 timers(two 128 MHz capable): 16-bit for advanced motor control, one 32-bit and five 16-bit general-purpose, two basic 16-bit, two low-power 16-bit, two watchdogs, SysTick timer
- Calendar RTC with alarm and periodic wakeup from Stop/Standby



TSSOP20<br>(6.4 × 4.4 mm)



LQFP32<br>(7 × 7 mm)<br>LQFP48<br>(7 × 7 mm)

- Communication interfaces
  - Two $I^2C$-bus interfaces supporting Fast-mode Plus (1 Mbit/s) with extra current sink, one supporting SMBus/PMBus and wakeup from Stop mode
  - Two USARTs with master/slave synchronous SPI; one supporting ISO7816 interface, LIN, IrDA capability, auto baud rate detection and wakeup feature
  - Two SPIs (32 Mbit/s) with 4- to 16-bit programmable bitframe, one multiplexed with $I^2S$ interface; two extra SPIs through USARTs
- Development support: serial wire debug (SWD)
- All packages ECOPACK 2 compliant

**Table 1. Device summary**

| Reference | Part number |
|---|---|
| STM32G050x6 | STM32G050C6, STM32G050F6, STM32G050K6 |
| STM32G050x8 | STM32G050C8, STM32G050K8 |

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# 1 Introduction

This document provides information on STM32G050x6/x8 microcontrollers, such as description, functional overview, pin assignment and definition, electrical characteristics, packaging, and ordering codes.

Information on memory mapping and control registers is object of reference manual RM0444.

For information on the device errata with respect to the datasheet and reference manual, refer to the STM32G050x6/x8 errata sheet ES0544.

Information on Arm®[a] Cortex®-M0+ core is available from the www.arm.com website.

a. Arm is a registered trademark of Arm Limited (or its subsidiaries) in the US and/or elsewhere.

# 2 Description

The STM32G050x6/x8 mainstream microcontrollers are based on high-performance Arm® Cortex®-M0+ 32-bit RISC core operating at up to 64 MHz frequency. Offering a high level of integration, they are suitable for a wide range of applications in consumer, industrial and appliance domains and ready for the Internet of Things (IoT) solutions.

The devices incorporate a memory protection unit (MPU), high-speed embedded memories (18 Kbytes of SRAM and up to 64 Kbytes of flash program memory with read protection, write protection), DMA, an extensive range of system functions, enhanced I/Os, and peripherals. The devices offer standard communication interfaces (two $I^2C$s, two SPIs / one $I^2S$, and two USARTs), one 12-bit ADC (2.5 MSps) with up to 19 channels, a low-power RTC, an advanced control PWM timer, five general-purpose 16-bit timers, two watchdog timers, and a SysTick timer.

The devices operate within ambient temperatures from -40 to 85°C and with supply voltages from 2.0 V to 3.6 V. Optimized dynamic consumption combined with a comprehensive set of power-saving modes allows the design of low-power applications.

VBAT direct battery input allows keeping RTC and backup registers powered.

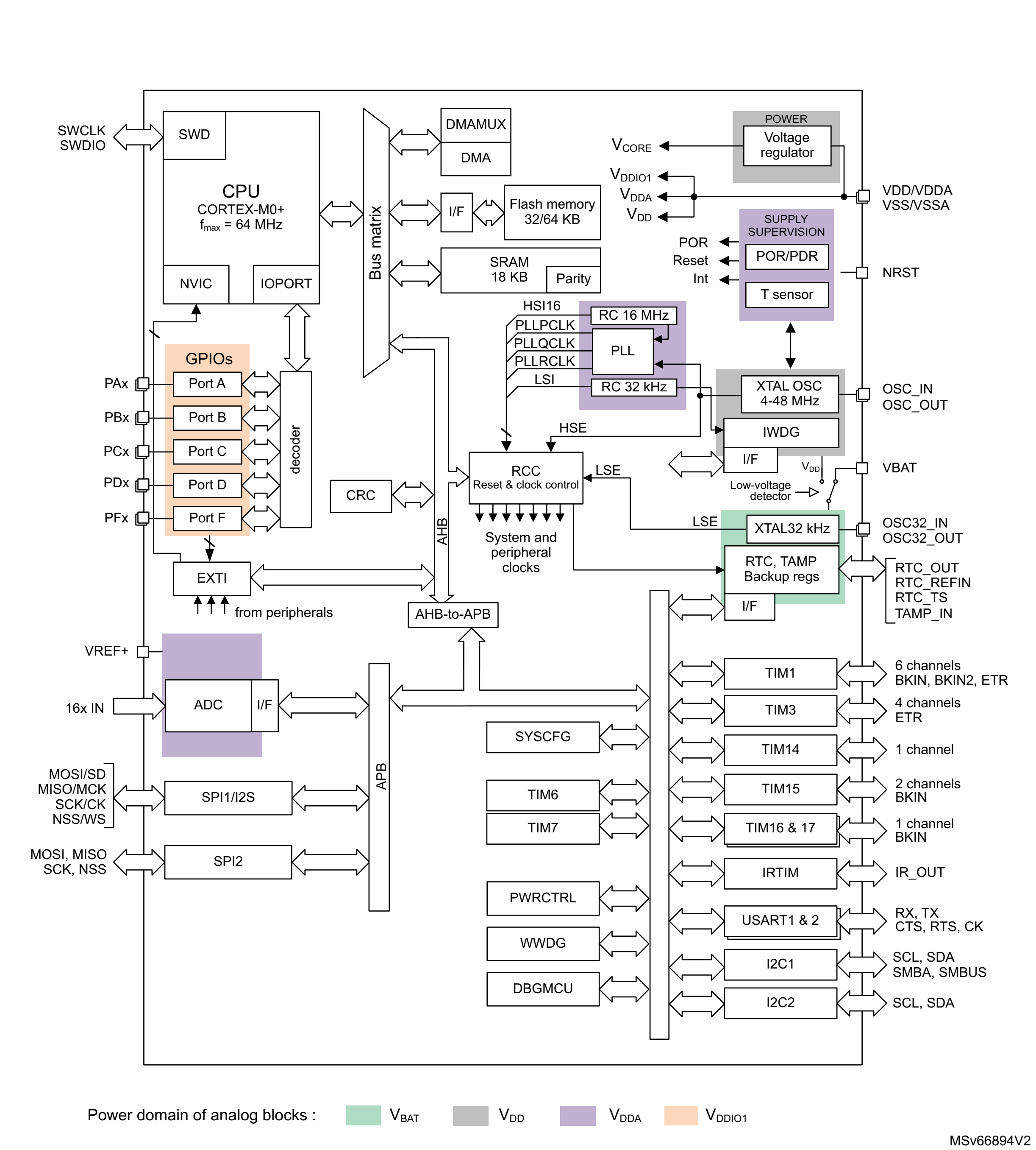
The devices come in packages with 20 to 48 pins.

**Table 2. STM32G050x6/x8 family device features and peripheral counts**

<table>
<tr><th colspan="2" rowspan="2">Peripheral</th><th colspan="5">STM32G050_</th></tr>
<tr><th>_F6</th><th>_K6</th><th>_K8</th><th>_C6</th><th>_C8</th></tr>
<tr><td colspan="2">Flash memory (Kbyte)</td><td>32</td><td>32</td><td>64</td><td>32</td><td>64</td></tr>
<tr><td colspan="2">SRAM (Kbyte)</td><td colspan="5">16 (parity-protected) or 18 (not parity-protected)</td></tr>
<tr><td rowspan="5">Timers</td><td>Advanced control</td><td colspan="5">1 (16-bit)</td></tr>
<tr><td>General-purpose</td><td colspan="5">5 (16-bit)</td></tr>
<tr><td>Basic</td><td colspan="5">2 (16-bit)</td></tr>
<tr><td>SysTick</td><td colspan="5">1</td></tr>
<tr><td>Watchdog</td><td colspan="5">2</td></tr>
<tr><td rowspan="3">Comm. interfaces</td><td>SPI [I2S][1]</td><td colspan="5">2 [1] + 2 extra through USARTs</td></tr>
<tr><td>I2C</td><td colspan="5">2</td></tr>
<tr><td>USART</td><td colspan="5">2</td></tr>
<tr><td colspan="2">RTC</td><td colspan="5">Yes</td></tr>
<tr><td colspan="2">Tamper pins</td><td colspan="5">2</td></tr>
<tr><td colspan="2">RNG / AES</td><td colspan="5">No / No</td></tr>
<tr><td colspan="2">GPIOs</td><td>18</td><td colspan="2">30</td><td colspan="2">44</td></tr>
<tr><td colspan="2">Wakeup pins</td><td colspan="5">4</td></tr>
<tr><td colspan="2">12-bit ADC channels<br>(external + internal)</td><td>14 + 2</td><td colspan="2">16 + 2</td><td colspan="2">16 + 3</td></tr>
<tr><td colspan="2">Max. CPU frequency</td><td colspan="5">64 MHz</td></tr>
<tr><td colspan="2">Operating voltage</td><td colspan="5">2.0 to 3.6 V</td></tr>
<tr><td colspan="2">Operating temperature[2]</td><td colspan="5">Ambient: -40 to 85 °C<br>Junction: -40 to 105 °C</td></tr>
<tr><td colspan="2">Number of pins</td><td>20</td><td colspan="2">32</td><td colspan="2">48</td></tr>
</table>

1. The numbers in brackets denote the count of SPI interfaces configurable as $I^2S$ interface.
2. Depends on order code. Refer to *Section 7: Ordering information* for details.

**Figure 1. Block diagram**



# 3 Functional overview

## 3.1 Arm® Cortex®-M0+ core with MPU

The Cortex-M0+ is an entry-level 32-bit Arm Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture, easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area- and power-optimized 32-bit core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to embedded Arm core, the STM32G050x6/x8 devices are compatible with Arm tools and software.

The Cortex-M0+ is tightly coupled with a nested vectored interrupt controller (NVIC) described in *Section 3.13.1*.

## 3.2 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

## 3.3 Embedded flash memory

STM32G050x6/x8 devices feature up to 64 Kbytes of embedded flash memory available for storing code and data.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  – Level 0: no readout protection
  – Level 1: memory readout protection: the flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  – Level 2: chip readout protection: debug features (Cortex-M0+ serial wire), boot in RAM and bootloader selection are disabled. This selection is irreversible.

**Table 3. Access status versus readout protection level and execution modes**

| Area | Protection level | User execution | | | Debug, boot from RAM or boot from system memory (loader) | | |
|---|---|---|---|---|---|---|---|
| | | Read | Write | Erase | Read | Write | Erase |
| User memory | 1 | Yes | Yes | Yes | No | No | No |
| | 2 | Yes | Yes | Yes | N/A | N/A | N/A |
| System memory | 1 | Yes | No | No | Yes | No | No |
| | 2 | Yes | No | No | N/A | N/A | N/A |
| Option bytes | 1 | Yes | Yes | Yes | Yes | Yes | Yes |
| | 2 | Yes | No | No | N/A | N/A | N/A |
| Backup registers | 1 | Yes | Yes | N/A(1) | No | No | N/A(1) |
| | 2 | Yes | Yes | N/A | N/A | N/A | N/A |
| OTP | 1 | Yes | Yes | N/A | Yes | No | N/A |
| | 2 | Yes | Yes | N/A | N/A | N/A | N/A |

1. Erased upon RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.

The whole non-volatile memory embeds the error correction code (ECC) feature supporting:

- single error detection and correction
- double error detection
- readout of the ECC fail address from the ECC register

## 3.4 Embedded SRAM

STM32G050x6/x8 devices have 16 Kbytes of embedded SRAM with parity. Hardware parity check allows memory data errors to be detected, which contributes to increasing functional safety of applications.

When the parity protection is not required because the application is not safety-critical, the parity memory bits can be used as additional SRAM, to increase its total size to 18 Kbytes.

The memory can be read/write-accessed at CPU clock speed, with 0 wait states.

## 3.5 Boot modes

At startup, the boot pin and boot selector option bit are used to select one of the three boot options:

- boot from User flash memory
- boot from System memory
- boot from embedded SRAM

The boot pin is shared with a standard GPIO and can be enabled through the boot selector option bit. If the BOOT0 pin selects the boot from the main flash memory of which the first location is empty, the flash memory empty checker forces the boot from the system memory.

The system memory contains an embedded boot loader. It manages the flash memory reprogramming through one of the following interfaces:

- USART on pins PA9/PA10 or PA2/PA3
- $I^2C$-bus on pins PB6/PB7 or PB10/PB11

When boot loader is executed, it configures some of the GPIOs out of their by-default high-Z state. Refer to AN2606 for more details on the boot loader and on the GPIO configuration when booting from the system memory.

## 3.6 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link time and stored at a given memory location.

## 3.7 Power supply management

### 3.7.1 Power supply schemes

The STM32G050x6/x8 devices require a 2.0 V to 3.6 V operating supply voltage ($V_{DD}$). Several different power supplies are provided to specific peripherals:

- $V_{DD}$ = 2.0 to 3.6 V

  $V_{DD}$ is the external power supply for the internal regulator and the system analog such as reset, power management and internal clocks. It is provided externally through VDD/VDDA pin.
- $V_{DDA}$ = 2.0 V to 3.6 V

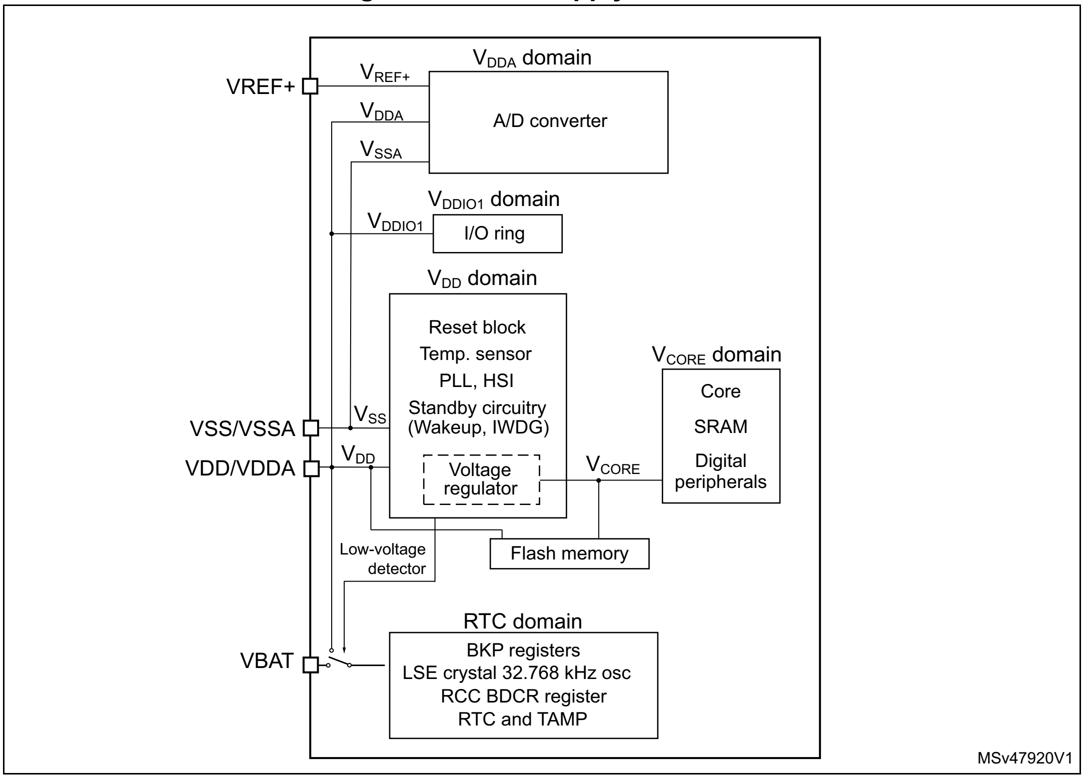
  $V_{DDA}$ is the analog power supply for the A/D converter. $V_{DDA}$ voltage level is identical to $V_{DD}$ voltage as it is provided externally through VDD/VDDA pin.
- $V_{DDIO1}$ = $V_{DD}$

  $V_{DDIO1}$ is the power supply for the I/Os. $V_{DDIO1}$ voltage level is identical to $V_{DD}$ voltage as it is provided externally through VDD/VDDA pin.

- $V_{BAT}$ = 1.55 V to 3.6 V. $V_{BAT}$ is the power supply (through a power switch) for RTC, TAMP, low-speed external 32.768 kHz oscillator and backup registers when $V_{DD}$ is not present. $V_{BAT}$ is provided externally through VBAT pin. When this pin is not available on the package, VBAT bonding pad is internally bonded to the VDD/VDDA pin.
- $V_{REF+}$ is the analog peripheral input reference voltage. When $V_{DDA}$ < 2 V, $V_{REF+}$ must be equal to $V_{DDA}$. When $V_{DDA}$ ≥ 2 V, $V_{REF+}$ must be between 2 V and $V_{DDA}$. It can be grounded when the analog peripherals using $V_{REF+}$ are not active.

  $V_{REF+}$ is delivered through VREF+ pin. On packages without VREF+ pin, $V_{REF+}$ is internally connected with $V_{DD}$.
- $V_{CORE}$ is an internal supply for digital peripherals, SRAM and flash memory. It is produced by an embedded linear voltage regulator. On top of $V_{CORE}$, the flash memory is also powered from $V_{DD}$.

**Figure 2. Power supply overview**




### 3.7.2 Power supply supervisor

The device has an integrated power-on/power-down (POR/PDR) reset active in all power modes and ensuring proper operation upon power-on and power-down. It maintains the device in reset when the supply voltage is below $V_{POR/PDR}$ threshold, without the need for an external reset circuit.

### 3.7.3 Voltage regulator

Two embedded linear voltage regulators, main regulator (MR) and low-power regulator (LPR), supply most of digital circuitry in the device.

The MR is used in Run and Sleep modes. The LPR is used in Low-power run, Low-power sleep and Stop modes.

In Standby mode, both regulators are powered down and their outputs set in high-impedance state, such as to bring their current consumption close to zero. However, SRAM data retention is possible in Standby mode, in which case the LPR remains active and it only supplies the SRAM.

### 3.7.4 Low-power modes

By default, the microcontroller is in Run mode after system or power reset. It is up to the user to select one of the low-power modes described below.

#### Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

#### Low-power run mode

This mode is achieved with $V_{CORE}$ supplied by the low-power regulator to minimize the regulator's operating current. The code can be executed from SRAM or from flash memory, and the CPU frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16.

#### Low-power sleep mode

This mode is entered from the low-power run mode. Only the CPU clock is stopped. When wakeup is triggered by an event or an interrupt, the system reverts to the Low-power run mode.

#### Stop 0 and Stop 1 modes

In Stop 0 and Stop 1 modes, the device achieves the lowest power consumption while retaining the SRAM and register contents. All clocks in the $V_{CORE}$ domain are stopped. The PLL, as well as the HSI16 RC oscillator and the HSE crystal oscillator are disabled. The LSE or LSI keep running. The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

Some peripherals with wakeup capability can enable the HSI16 RC during Stop mode, so as to get clock for processing the wakeup event. The main regulator remains active in Stop 0 mode while it is turned off in Stop 1 mode.

#### Standby mode

The Standby mode is used to achieve the lowest power consumption, with POR/PDR always active in this mode. The main regulator is switched off to power down $V_{CORE}$ domain. The low-power regulator is either switched off or kept active. In the latter case, it only supplies SRAM to ensure data retention. The PLL, as well as the HSI16 RC oscillator and the HSE crystal oscillator are also powered down. The RTC can remain active (Standby mode with RTC, Standby mode without RTC).

For each I/O, the software can determine whether a pull-up, a pull-down or no resistor shall be applied to that I/O during Standby mode.

Upon entering Standby mode, register contents are lost except for registers in the RTC domain and standby circuitry. The SRAM contents can be retained through register setting.

The device exits Standby mode upon external reset event (NRST pin), IWDG reset event, wakeup event (WKUP pin, configurable rising or falling edge), RTC event (alarm, periodic wakeup, timestamp), TAMP event, or when a failure is detected on LSE (CSS on LSE).

### 3.7.5 Reset mode

During and upon exiting reset, the schmitt triggers of I/Os are disabled so as to reduce power consumption. In addition, when the reset source is internal, the built-in pull-up resistor on NRST pin is deactivated.

### 3.7.6 VBAT operation

The $V_{BAT}$ power domain, consuming very little energy, includes RTC, and LSE oscillator and backup registers.

In VBAT mode, the RTC domain is supplied from VBAT pin. The power source can be, for example, an external battery or an external supercapacitor. Two anti-tamper detection pins are available.

The RTC domain can also be supplied from $V_{DD}$.

By means of a built-in switch, an internal voltage supervisor allows automatic switching of RTC domain powering between $V_{DD}$ and voltage from VBAT pin to ensure that the supply voltage of the RTC domain ($V_{BAT}$) remains within valid operating conditions. If both voltages are valid, the RTC domain is supplied from $V_{DD}$.

An internal circuit for charging the battery on VBAT pin can be activated if the $V_{DD}$ voltage is within a valid range.

*Note: External interrupts and RTC alarm/events cannot cause the microcontroller to exit the VBAT mode, as in that mode the $V_{DD}$ is not within a valid range.*

## 3.8 Interconnect of peripherals

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep and Stop modes.

**Table 4. Interconnect of peripherals**

| Interconnect source | Interconnect destination | Interconnect action | Run Low-power run | Sleep Low-power sleep | Stop |
|---|---|---|---|---|---|
| TIMx | TIMx | Timer synchronization or chaining | Y | Y | - |
| | ADCx | Conversion triggers | Y | Y | - |
| | DMA | Memory-to-memory transfer trigger | Y | Y | - |
| ADCx | TIM1 | Timer triggered by analog watchdog | Y | Y | - |

**Table 4. Interconnect of peripherals (continued)**

| Interconnect source | Interconnect destination | Interconnect action | Run Low-power run | Sleep Low-power sleep | Stop |
|---|---|---|---|---|---|
| RTC | TIM16 | Timer input channel from RTC events | Y | Y | - |
| All clock sources (internal and external) | TIM14,16,17 | Clock source used as input channel for RC measurement and trimming | Y | Y | - |
| CSS<br>RAM (parity error)<br>Flash memory (ECC error) | TIM1,15,16,17 | Timer break | Y | Y | - |
| CPU (hard fault) | TIM1,15,16,17 | Timer break | Y | - | - |
| GPIO | TIMx | External trigger | Y | Y | - |
| | ADC | Conversion external trigger | Y | Y | - |

## 3.9 Clocks and startup

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler:** to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **System clock source:** three different sources can deliver SYSCLK system clock:
  - 4-48 MHz high-speed oscillator with external crystal or ceramic resonator (HSE). It can supply clock to system PLL. The HSE can also be configured in bypass mode for an external clock.
  - 16 MHz high-speed internal RC oscillator (HSI16), trimmable by software. It can supply clock to system PLL.
  - System PLL with maximum output frequency of 64 MHz. It can be fed with HSE or HSI16 clocks.

- **Auxiliary clock source:** two ultra-low-power clock sources for the real-time clock (RTC):
  - 32.768 kHz low-speed oscillator with external crystal (LSE), supporting four drive capability modes. The LSE can also be configured in bypass mode for using an external clock.
  - 32 kHz low-speed internal RC oscillator (LSI) with ±5% accuracy, also used to clock an independent watchdog.
- **Peripheral clock sources:** several peripherals ( I2S, USARTs, I2Cs, ADC) have their own clock independent of the system clock.
- **Clock security system (CSS):** in the event of HSE clock failure, the system clock is automatically switched to HSI16 and, if enabled, a software interrupt is generated. LSE clock failure can also be detected and generate an interrupt. The CCS feature can be enabled by software.
- **Clock output:**
  - **MCO (microcontroller clock output)** provides one of the internal clocks for external use by the application
  - **LSCO (low speed clock output)** provides LSI or LSE in all low-power modes (except in VBAT operation).

Several prescalers allow the application to configure AHB and APB domain clock frequencies, 64 MHz at maximum.

## 3.10 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function (AF). Most of the GPIO pins are shared with special digital or analog functions.

Through a specific sequence, this special function configuration of I/Os can be locked, such as to avoid spurious writing to I/O control registers.

## 3.11 Direct memory access controller (DMA)

The direct memory access (DMA) controller is a bus master and system peripheral with single-AHB architecture.

With 7 channels, it performs data transfers between memory-mapped peripherals and/or memories, to offload the CPU.

Each channel is dedicated to managing memory access requests from one or more peripherals. The unit includes an arbiter for handling the priority between DMA requests.

Main features of the DMA controller:

- Single-AHB master
- Peripheral-to-memory, memory-to-peripheral, memory-to-memory and peripheral-to-peripheral data transfers
- Access, as source and destination, to on-chip memory-mapped devices such as flash memory, SRAM, and AHB and APB peripherals
- All DMA channels independently configurable:
  – Each channel is associated either with a DMA request signal coming from a peripheral, or with a software trigger in memory-to-memory transfers. This configuration is done by software.
  – Priority between the requests is programmable by software (four levels per channel: very high, high, medium, low) and by hardware in case of equality (such as request to channel 1 has priority over request to channel 2).
  – Transfer size of source and destination are independent (byte, half-word, word), emulating packing and unpacking. Source and destination addresses must be aligned on the data size.
  – Support of transfers from/to peripherals to/from memory with circular buffer management
  – Programmable number of data to be transferred: 0 to $2^{16}$ - 1
- Generation of an interrupt request per channel. Each interrupt request originates from any of the three DMA events: transfer complete, half transfer, or transfer error.

## 3.12 DMA request multiplexer (DMAMUX)

The DMAMUX request multiplexer enables routing a DMA request line between the peripherals and the DMA controller. Each channel selects a unique DMA request line, unconditionally or synchronously with events from its DMAMUX synchronization inputs. DMAMUX may also be used as a DMA request generator from programmable events on its input trigger signals.

## 3.13 Interrupts and events

The device flexibly manages events causing interrupts of linear program execution, called exceptions. The Cortex-M0+ processor core, a nested vectored interrupt controller (NVIC) and an extended interrupt/event controller (EXTI) are the assets contributing to handling the exceptions. Exceptions include core-internal events such as, for example, a division by zero and, core-external events such as logical level changes on physical lines. Exceptions result in interrupting the program flow, executing an interrupt service routine (ISR) then resuming the original program flow.

The processor context (contents of program pointer and status registers) is stacked upon program interrupt and unstacked upon program resume, by hardware. This avoids context stacking and unstacking in the interrupt service routines (ISRs) by software, thus saving time, code and power. The ability to abandon and restart load-multiple and store-multiple operations significantly increases the device’s responsiveness in processing exceptions.

### 3.13.1 Nested vectored interrupt controller (NVIC)

The configurable nested vectored interrupt controller is tightly coupled with the core. It handles physical line events associated with a non-maskable interrupt (NMI) and maskable interrupts, and Cortex-M0+ exceptions. It provides flexible priority management.

The tight coupling of the processor core with NVIC significantly reduces the latency between interrupt events and start of corresponding interrupt service routines (ISRs). The ISR vectors are listed in a vector table, stored in the NVIC at a base address. The vector address of an ISR to execute is hardware-built from the vector table base address and the ISR order number used as offset.

If a higher-priority interrupt event happens while a lower-priority interrupt event occurring just before is waiting for being served, the later-arriving higher-priority interrupt event is served first. Another optimization is called tail-chaining. Upon a return from a higher-priority ISR then start of a pending lower-priority ISR, the unnecessary processor context unstacking and stacking is skipped. This reduces latency and contributes to power efficiency.

Features of the NVIC:

- Low-latency interrupt processing
- 4 priority levels
- Handling of a non-maskable interrupt (NMI)
- Handling of 32 maskable interrupt lines
- Handling of 10 Cortex-M0+ exceptions
- Later-arriving higher-priority interrupt processed first
- Tail-chaining
- Interrupt vector retrieval by hardware

### 3.13.2 Extended interrupt/event controller (EXTI)

The extended interrupt/event controller adds flexibility in handling physical line events and allows identifying wake-up events at processor wakeup from Stop mode.

The EXTI controller has a number of channels, of which some with rising, falling or rising, and falling edge detector capability. Any GPIO and a few peripheral signals can be connected to these channels.

The channels can be independently masked.

The EXTI controller can capture pulses shorter than the internal clock period.

A register in the EXTI controller latches every event even in Stop mode, which allows the software to identify the origin of the processor's wake-up from Stop mode or, to identify the GPIO and the edge event having caused an interrupt.

## 3.14 Analog-to-digital converter (ADC)

A native 12-bit analog-to-digital converter is embedded into STM32G050x6/x8 devices. The ADC has up to 16 external channels and 3 internal channels (temperature sensor, voltage reference, $V_{BAT}$ monitoring). It performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of ~2.5 MSps even with a low CPU speed. An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate in the whole $V_{DD}$ supply range.

The ADC features a hardware oversampler up to 256 samples, improving the resolution to 16 bits (refer to AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions with timers.

### 3.14.1 Temperature sensor

The temperature sensor (TS) generates a voltage $V_{TS}$ that varies linearly with temperature.

The temperature sensor is internally connected to an ADC input to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor may vary from part to part due to process variation, the uncalibrated internal temperature sensor is suitable only for relative temperature measurements.

To improve the accuracy of the temperature sensor, each part is individually factory-calibrated by ST. The resulting calibration data are stored in the part's engineering bytes, accessible in read-only mode.

**Table 5. Temperature sensor calibration values**

| Calibration value name | Description | Memory address |
|---|---|---|
| TS_CAL1 | TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), $V_{DDA}$ = $V_{REF+}$ = 3.0 V (± 10 mV) | 0x1FFF 75A8 - 0x1FFF 75A9 |

### 3.14.2 Internal voltage reference ($V_{REFINT}$)

The internal voltage reference ($V_{REFINT}$) provides a stable (bandgap) voltage output for the ADC. $V_{REFINT}$ is internally connected to an ADC input. The $V_{REFINT}$ voltage is individually precisely measured for each part by ST during production test and stored in the part's engineering bytes. It is accessible in read-only mode.

**Table 6. Internal voltage reference calibration values**

| Calibration value name | Description | Memory address |
|---|---|---|
| $V_{REFINT}$ | Raw data acquired at a temperature of 30 °C (± 5 °C), $V_{DDA}$ = $V_{REF+}$ = 3.0 V (± 10 mV) | 0x1FFF 75AA - 0x1FFF 75AB |

### 3.14.3 $V_{BAT}$ battery voltage monitoring

This embedded hardware feature allows the application to measure the $V_{BAT}$ battery voltage using an internal ADC input. As the $V_{BAT}$ voltage may be higher than $V_{DDA}$ and thus outside the ADC input range, the VBAT pin is internally connected to a bridge divider by three. As a consequence, the converted digital value is one third the $V_{BAT}$ voltage.

## 3.15 Timers and watchdogs

The device includes an advanced-control timer, five general-purpose timers, two basic timers, two watchdog timers and a SysTick timer. *Table 7* compares features of the advanced-control, general-purpose and basic timers.

**Table 7. Timer feature comparison**

| Timer type | Timer | Counter resolution | Counter type | Maximum operating frequency | Prescaler factor | DMA request generation | Capture/ compare channels | Comple-mentary outputs |
|---|---|---|---|---|---|---|---|---|
| Advanced-control | TIM1 | 16-bit | Up, down, up/down | 64 MHz | Integer from 1 to $2^{16}$ | Yes | 4 + 2 internal | 3 |
| General-purpose | TIM3 | 16-bit | Up, down, up/down | 64 MHz | Integer from 1 to $2^{16}$ | Yes | 4 | - |
| | TIM14 | 16-bit | Up | 64 MHz | Integer from 1 to $2^{16}$ | No | 1 | - |
| | TIM15 | 16-bit | Up | 64 MHz | Integer from 1 to $2^{16}$ | Yes | 2 | 1 |
| | TIM16 TIM17 | 16-bit | Up | 64 MHz | Integer from 1 to $2^{16}$ | Yes | 1 | 1 |
| Basic | TIM6 TIM7 | 16-bit | Up | 64 MHz | Integer from 1 to $2^{16}$ | Yes | - | - |

### 3.15.1 Advanced-control timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM unit multiplexed on 6 channels. It has complementary PWM outputs with programmable inserted dead-times. It can also be seen as a complete general-purpose timer. The four independent channels can be used for:

- input capture
- output compare
- PWM output (edge or center-aligned modes) with full modulation capability (0-100%)
- one-pulse mode output

On top of these, there are two internal channels that can be used.

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled, so as to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIMx timers (described in *Section 3.15.2*) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

### 3.15.2 General-purpose timers (TIM3, 14, 15, 16, 17)

There are five synchronizable general-purpose timers embedded in the device (refer to *Table 7* for comparison). Each general-purpose timer can be used to generate PWM outputs or act as a simple timebase.

- TIM3

  This is a full-featured general-purpose timer with 16-bit auto-reload up/downcounter and 16-bit prescaler.

  It has four independent channels for input capture/output compare, PWM or one-pulse mode output. It can operate in combination with other general-purpose timers via the Timer Link feature for synchronization or event chaining. It can generate independent DMA request and support quadrature encoders. Its counter can be frozen in debug mode.
- TIM14

  This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. It has one channel for input capture/output compare, PWM output or one-pulse mode output. Its counter can be frozen in debug mode.
- TIM15, TIM16, TIM17

  These are general-purpose timers featuring:
  - 16-bit auto-reload upcounter and 16-bit prescaler
  - 2 channels and 1 complementary channel for TIM15
  - 1 channel and 1 complementary channel for TIM16 and TIM17

  All channels can be used for input capture/output compare, PWM or one-pulse mode output. The timers can operate together via the Timer Link feature for synchronization or event chaining. They can generate independent DMA request. Their counters can be frozen in debug mode.

### 3.15.3 Basic timers (TIM6 and TIM7)

These timers can be used as generic 16-bit timebases.

### 3.15.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 32 kHz internal RC (LSI). Independent of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. Its counter can be frozen in debug mode.

### 3.15.5 System window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked by the system clock. It has an early-warning interrupt capability. Its counter can be frozen in debug mode.

### 3.15.6 SysTick timer

This timer is dedicated to real-time operating systems, but it can also be used as a standard down counter.

Features of SysTick timer:

- 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

## 3.16 Real-time clock (RTC), tamper (TAMP) and backup registers

The device embeds an RTC and five 32-bit backup registers, located in the RTC domain of the silicon die.

The ways of powering the RTC domain are described in *Section 3.7.6*.

The RTC is an independent BCD timer/counter.

Features of the RTC:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month
- Programmable alarm
- On-the-fly correction from 1 to 32767 RTC clock pulses, usable for synchronization with a master clock
- Reference clock detection - a more precise second-source clock (50 or 60 Hz) can be used to improve the calendar precision
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy
- Two anti-tamper detection pins with programmable filter
- Timestamp feature to save a calendar snapshot, triggered by an event on the timestamp pin or a tamper event, or by switching to VBAT mode
- 17-bit auto-reload wakeup timer (WUT) for periodic events, with programmable resolution and period
- Multiple clock sources and references:
  – A 32.768 kHz external crystal (LSE)
  – An external resonator or oscillator (LSE)
  – The internal low-power RC oscillator (LSI, with typical frequency of 32 kHz)
  – The high-speed external clock (HSE) divided by 32

When clocked by LSE, the RTC operates in VBAT mode and in all low-power modes. When clocked by LSI, the RTC does not operate in VBAT mode, but it does in low-power modes.

All RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wake the device up from the low-power modes.

The backup registers allow keeping 20 bytes of user application data in the event of $V_{DD}$ failure, if a valid backup supply voltage is provided on VBAT pin. They are not affected by the system reset, power reset, and upon the device’s wakeup from Standby mode.

## 3.17 Inter-integrated circuit interface (I2C)

The device embeds two I2C peripherals. Refer to *Table 8* for the features.

The $I^2C$-bus interface handles communication between the microcontroller and the serial $I^2C$-bus. It controls all $I^2C$-bus-specific sequencing, protocol, arbitration and timing.

Features of the I2C peripheral:

- $I^2C$-bus specification and user manual rev. 5 compatibility:
  - Slave and master modes, multimaster capability
  - Standard-mode (Sm), with a bitrate up to 100 kbit/s
  - Fast-mode (Fm), with a bitrate up to 400 kbit/s
  - Fast-mode Plus (Fm+), with a bitrate up to 1 Mbit/s and extra output drive I/Os
  - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
  - Programmable setup and hold times
  - Clock stretching
- SMBus specification rev 3.0 compatibility:
  - Hardware PEC (packet error checking) generation and verification with ACK control
  - Command and data acknowledge control
  - Address resolution protocol (ARP) support
  - Host and Device support
  - SMBus alert
  - Timeouts and idle condition detection
- PMBus rev 1.3 standard compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent of the PCLK reprogramming
- Wakeup from Stop mode on address match
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

**Table 8. $I^2C$ implementation**

| $I^2C$ features[(1)] | I2C1 | I2C2 |
|---|---|---|
| Standard mode (up to 100 kbit/s) | X | X |
| Fast mode (up to 400 kbit/s) | X | X |
| Fast Mode Plus (up to 1 Mbit/s) with extra output drive I/Os | X | X |
| Programmable analog and digital noise filters | X | X |
| SMBus/PMBus hardware support | X | - |
| Independent clock | X | - |
| Wakeup from Stop mode on address match | X | - |

1. X: supported

## 3.18 Universal synchronous/asynchronous receiver transmitter (USART)

The device embeds universal synchronous/asynchronous receivers/transmitters that communicate at speeds of up to 8 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 DE signals, multiprocessor communication mode, SPI synchronous communication and single-wire half-duplex communication mode. Some can also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability and auto baud rate feature, and have a clock domain independent of the CPU clock, which allows them to wake up the MCU from Stop mode. The wakeup events from Stop mode are programmable and can be:

- start bit detection
- any received data frame
- a specific programmed data frame

All USART interfaces can be served by the DMA controller.

**Table 9. USART implementation**

| USART modes/features(1) | USART1 | USART2 |
|---|---|---|
| Hardware flow control for modem | X | X |
| Continuous communication using DMA | X | X |
| Multiprocessor communication | X | X |
| SPI emulation master/slave (synchronous mode) | X | X |
| Smartcard mode | X | - |
| Single-wire half-duplex communication | X | X |
| IrDA SIR ENDEC block | X | - |
| LIN mode | X | - |
| Dual clock domain and wakeup from Stop mode | X | - |
| Receiver timeout interrupt | X | - |
| Modbus communication | X | - |
| Auto baud rate detection | X | - |
| Driver Enable | X | X |

1. X: supported

## 3.19 Serial peripheral interface (SPI)

The device contains two SPIs running at up to 32 Mbits/s in master and slave modes. It supports half-duplex, full-duplex and simplex communications. A 3-bit prescaler gives eight master mode frequencies. The frame size is configurable from 4 bits to 16 bits. The SPI peripherals support NSS pulse mode, TI mode and hardware CRC calculation.

The SPI peripherals can be served by the DMA controller.

The $I^2S$ interface mode of the SPI peripheral (if supported, see the following table) supports four different audio standards can operate as master or slave, in half-duplex communication mode. It can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by an 8-bit programmable linear prescaler. When operating in master mode, it can output a clock for an external audio component at 256 times the sampling frequency.

**Table 10. SPI/I2S implementation**

| SPI features(1) | SPI1 | SPI2 |
|---|---|---|
| Hardware CRC calculation | X | X |
| Rx/Tx FIFO | X | X |
| NSS pulse mode | X | X |
| $I^2S$ mode | X | - |
| TI mode | X | X |

1. X = supported.

## 3.20 Development support

### 3.20.1 Serial wire debug port (SW-DP)

An Arm SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

# 4 Pinouts, pin description and alternate functions

**Figure 3. STM32G050Fx TSSOP20 pinout**

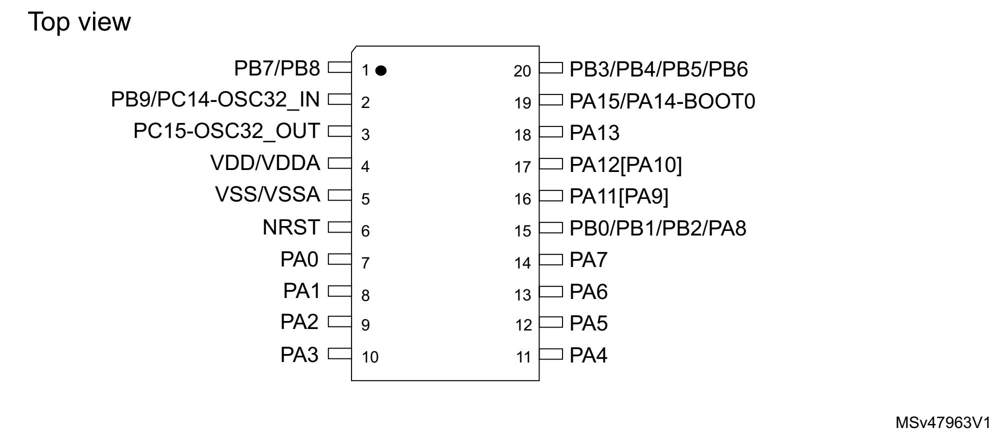



**Figure 4. STM32G050KxT LQFP32 pinout**

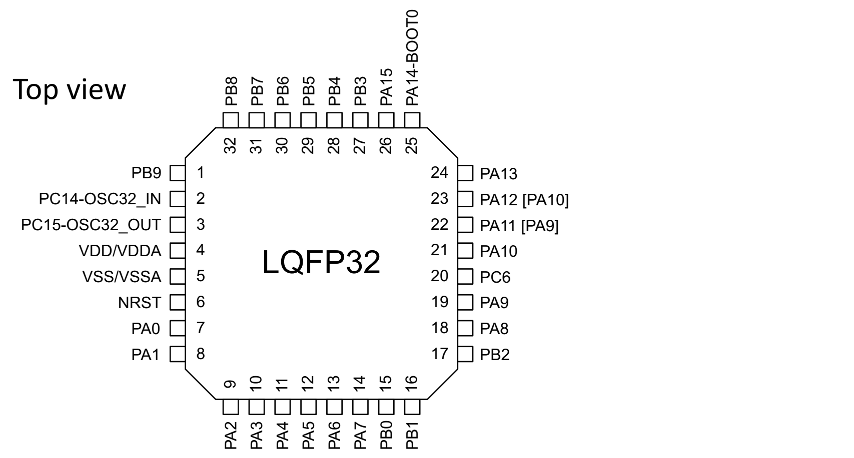


**Figure 5. STM32G050CxT LQFP48 pinout**

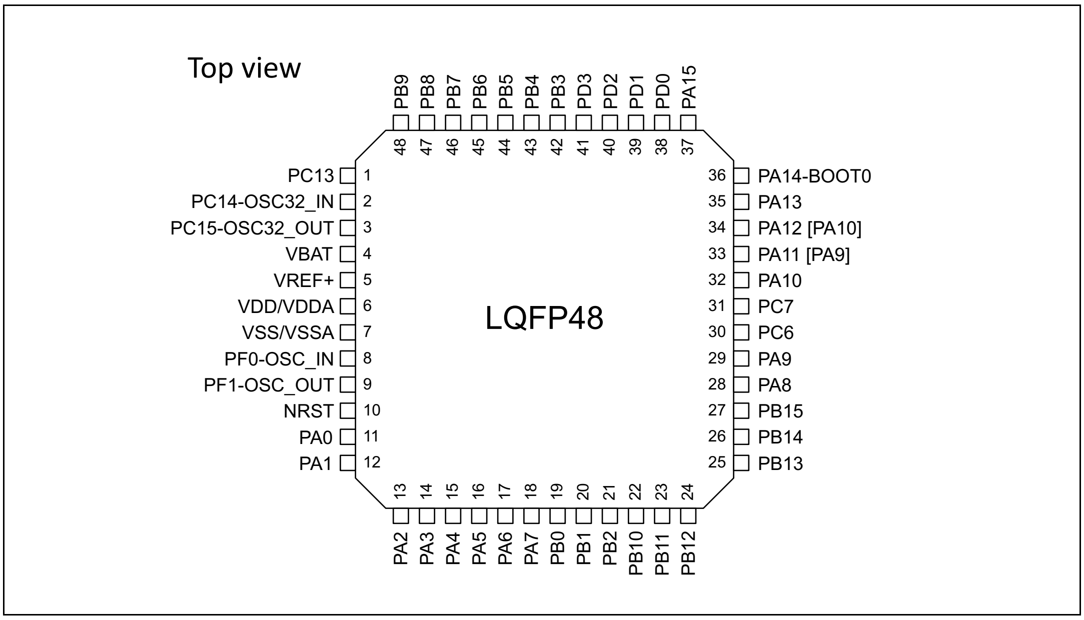



**Table 11. Terms and symbols used in *Pin assignment and description* table**

| Column | | Symbol | Definition |
|---|---|---|---|
| Pin name | | Terminal name corresponds to its by-default function at reset, unless otherwise specified in parenthesis under the pin name. | |
| Pin type | | S | Supply pin |
| | | I | Input only pin |
| | | I/O | Input / output pin |
| I/O structure | | FT | 5 V tolerant I/O |
| | | TT | 3.6 V tolerant I/O |
| | | RST | Reset pin with embedded weak pull-up resistor |
| | | **Options for TT or FT I/Os** | |
| | | _f | I/O, Fm+ capable |
| | | _a | I/O, with analog switch function |
| | | _e | I/O, with switchable diode to $V_{DDIO1}$ |
| Note | | Upon reset, all I/Os are set as analog inputs, unless otherwise specified. | |
| Pin functions | Alternate functions | Functions selected through GPIOx_AFR registers | |
| | Additional functions | Functions directly selected/enabled through peripheral registers | |

**Table 12. Pin assignment and description**

| Pin | | | Pin name (function upon reset) | Pin type | I/O structure | Note | Alternate functions | Additional functions |
|---|---|---|---|---|---|---|---|---|
| TSSOP20 | LQFP32 | LQFP48 | | | | | | |
| - | - | 1 | PC13 | I/O | FT | - | TIM1_BK | TAMP_IN1, RTC_TS, RTC_OUT1, WKUP2 |
| - | - | 2 | PC14-OSC32_IN (PC14) | I/O | FT | - | TIM1_BK2 | OSC32_IN |
| 2 | 2 | - | PC14-OSC32_IN (PC14) | I/O | FT | - | TIM1_BK2 | OSC32_IN, OSC_IN |
| 3 | 3 | 3 | PC15-OSC32_OUT (PC15) | I/O | FT | - | OSC32_EN, OSC_EN, TIM15_BKIN | OSC32_OUT |
| - | - | 4 | VBAT | S | - | - | - | VBAT |
| - | - | 5 | VREF+ | S | - | - | - | - |
| 4 | 4 | 6 | VDD/VDDA | S | - | - | - | - |
| 5 | 5 | 7 | VSS/VSSA | S | - | - | - | - |
| - | - | 8 | PF0-OSC_IN (PF0) | I/O | FT | - | TIM14_CH1 | OSC_IN |
| - | - | 9 | PF1-OSC_OUT (PF1) | I/O | FT | - | OSC_EN, TIM15_CH1N | OSC_OUT |
| 6 | 6 | 10 | NRST | I/O | RST | - | - | - |
| 7 | 7 | 11 | PA0 | I/O | FT_a | - | SPI2_SCK, USART2_CTS, | ADC_IN0, TAMP_IN2,WKUP1 |
| 8 | 8 | 12 | PA1 | I/O | FT_ea | - | SPI1_SCK/I2S1_CK, USART2_RTS_DE_CK, I2C1_SMBA, TIM15_CH1N, EVENTOUT | ADC_IN1 |
| 9 | 9 | 13 | PA2 | I/O | FT_a | - | SPI1_MOSI/I2S1_SD, TIM15_CH1N, USART2_TX, | ADC_IN2, WKUP4, LSCO |
| 10 | 10 | 14 | PA3 | I/O | FT_ea | - | SPI2_MISO, USART2_RX, , TIM15_CH2EVENTOUT | ADC_IN3 |
| - | - | 15 | PA4 | I/O | TT_a | - | SPI1_NSS/I2S1_WS, SPI2_MOSI, TIM14_CH1, EVENTOUT | ADC_IN4, RTC_OUT2 |
| 11 | 11 | - | PA4 | I/O | TT_a | - | SPI1_NSS/I2S1_WS, SPI2_MOSI, TIM14_CH1, EVENTOUT | ADC_IN4, TAMP_IN1, RTC_TS, RTC_OUT1, WKUP2 |
| 12 | 12 | 16 | PA5 | I/O | TT_ea | - | SPI1_SCK/I2S1_CK, EVENTOUT | ADC_IN5 |
| 13 | 13 | 17 | PA6 | I/O | FT_ea | - | SPI1_MISO/I2S1_MCK, TIM3_CH1, TIM1_BK, TIM16_CH1 | ADC_IN6 |

Table 12. Pin assignment and description (continued)

| Pin | | | Pin name (function upon reset) | Pin type | I/O structure | Note | Alternate functions | Additional functions |
|---|---|---|---|---|---|---|---|---|
| TSSOP20 | LQFP32 | LQFP48 | | | | | | |
| 14 | 14 | 18 | PA7 | I/O | FT_a | - | SPI1_MOSI/I2S1_SD, TIM3_CH2, TIM1_CH1N, TIM14_CH1, TIM17_CH1 | ADC_IN7 |
| 15 | 15 | 19 | PB0 | I/O | FT_ea | - | SPI1_NSS/I2S1_WS, TIM3_CH3, TIM1_CH2N | ADC_IN8 |
| 15 | 16 | 20 | PB1 | I/O | FT_ea | - | TIM14_CH1, TIM3_CH4, TIM1_CH3N, EVENTOUT | ADC_IN9 |
| 15 | 17 | 21 | PB2 | I/O | FT_ea | - | SPI2_MISO,EVENTOUT | ADC_IN10 |
| - | - | 22 | PB10 | I/O | FT_fa | - | SPI2_SCK, I2C2_SCL | ADC_IN11 |
| - | - | 23 | PB11 | I/O | FT_fa | - | SPI2_MOSI, I2C2_SDA | ADC_IN15 |
| - | - | 24 | PB12 | I/O | FT_a | - | SPI2_NSS, TIM15_BKIN, TIM1_BK, EVENTOUT | ADC_IN16 |
| - | - | 25 | PB13 | I/O | FT_f | - | SPI2_SCK, TIM1_CH1N, I2C2_SCL, TIM15_CH1L, EVENTOUT | - |
| - | - | 26 | PB14 | I/O | FT_f | - | SPI2_MISO, TIM1_CH2N, TIM15_CH1, I2C2_SDA, EVENTOUT | - |
| - | - | 27 | PB15 | I/O | FT | - | SPI2_MOSI, TIM1_CH3N, TIM15_CH1N, EVENTOUT | RTC_REFIN |
| 15 | 18 | 28 | PA8 | I/O | FT | - | MCO, SPI2_NSS, TIM1_CH1, EVENTOUT | - |
| - | 19 | 29 | PA9 | I/O | FT_f | - | MCO, USART1_TX, TIM15_BKIN, TIM1_CH2, SPI2_MISO, I2C1_SCL, EVENTOUT | - |
| - | 20 | 30 | PC6 | I/O | FT | - | TIM3_CH1 | - |
| - | - | 31 | PC7 | I/O | FT | - | TIM3_CH2 | - |
| - | 21 | 32 | PA10 | I/O | FT_f | - | SPI2_MOSI, USART1_RX, TIM1_CH3, TIM17_BK, I2C1_SDA, EVENTOUT | - |
| - | - | 33 | PA11 [PA9] | I/O | FT_f | - | SPI1_MISO/I2S1_MCK, USART1_CTS, TIM1_CH4, TIM1_BK2, I2C2_SCL | - |
| 16 | 22 | - | PA11 [PA9] | I/O | FT_fa | - | SPI1_MISO/I2S1_MCK, USART1_CTS, TIM1_CH4, TIM1_BK2, I2C2_SCL | ADC_IN15 |
| - | - | 34 | PA12 [PA10] | I/O | FT_fa | - | SPI1_MOSI/I2S1_SD, USART1_RTS_DE_CK, TIM1_ETR, I2S_CKIN, I2C2_SDA | - |

**Table 12. Pin assignment and description (continued)**

| Pin | | | Pin name (function upon reset) | Pin type | I/O structure | Note | Alternate functions | Additional functions |
|---|---|---|---|---|---|---|---|---|
| TSSOP20 | LQFP32 | LQFP48 | | | | | | |
| 17 | 23 | - | PA12 [PA10] | I/O | FT_fa | - | SPI1_MOSI/I2S1_SD, USART1_RTS_DE_CK, TIM1_ETR, I2S_CKIN, I2C2_SDA | ADC_IN16 |
| 18 | 24 | 35 | PA13 | I/O | FT_ea | - | SWDIO, IR_OUT, EVENTOUT | ADC_IN17 |
| 19 | 25 | 36 | PA14-BOOT0 | I/O | FT_a | - | SWCLK, USART2_TX, EVENTOUT | ADC_IN18, BOOT0 |
| 19 | 26 | 37 | PA15 | I/O | FT | - | SPI1_NSS/I2S1_WS, USART2_RX, EVENTOUT | - |
| - | - | 38 | PD0 | I/O | FT | - | EVENTOUT, SPI2_NSS, TIM16_CH1 | - |
| - | - | 39 | PD1 | I/O | FT | - | EVENTOUT, SPI2_SCK, TIM17_CH1 | - |
| - | - | 40 | PD2 | I/O | FT | - | TIM3_ETR, TIM1_CH1N | - |
| - | - | 41 | PD3 | I/O | FT | - | USART2_CTS, SPI2_MISO, TIM1_CH2N | - |
| 20 | 27 | 42 | PB3 | I/O | FT | - | SPI1_SCK/I2S1_CK, TIM1_CH2, USART1_RTS_DE_CK, EVENTOUT | - |
| 20 | 28 | 43 | PB4 | I/O | FT | - | SPI1_MISO/I2S1_MCK, TIM3_CH1, USART1_CTS, TIM17_BK, EVENTOUT | - |
| 20 | 29 | 44 | PB5 | I/O | FT | - | SPI1_MOSI/I2S1_SD, TIM3_CH2, TIM16_BK, I2C1_SMBA | WKUP6 |
| 20 | 30 | 45 | PB6 | I/O | FT_f | - | USART1_TX, TIM1_CH3, TIM16_CH1N, SPI2_MISO, I2C1_SCL, EVENTOUT | - |
| - | - | 46 | PB7 | I/O | FT_fa | - | USART1_RX, SPI2_MOSI, TIM17_CH1N, I2C1_SDA, EVENTOUT | - |
| 1 | 31 | - | PB7 | I/O | FT_fa | - | USART1_RX, SPI2_MOSI, TIM17_CH1N, I2C1_SDA, EVENTOUT | ADC_IN11 |
| 1 | 32 | 47 | PB8 | I/O | FT_f | - | SPI2_SCK, TIM16_CH1, TIM15_BKIN, I2C1_SCL, EVENTOUT | - |
| 2 | 1 | 48 | PB9 | I/O | FT_f | - | IR_OUT, TIM17_CH1, SPI2_NSS, I2C1_SDA, EVENTOUT | - |

**Table 13. Port A alternate function mapping**

| Port | AF0 | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 |
|---|---|---|---|---|---|---|---|---|
| PA0 | SPI2_SCK | USART2_CTS | - | - | - | - | - | - |
| PA1 | SPI1_SCK/ I2S1_CK | USART2_RTS _DE_CK | - | - | - | TIM15_CH1N | I2C1_SMBA | EVENTOUT |
| PA2 | SPI1_MOSI/ I2S1_SD | USART2_TX | - | - | - | TIM15_CH1 | - | - |
| PA3 | SPI2_MISO | USART2_RX | - | - | - | TIM15_CH2 | - | EVENTOUT |
| PA4 | SPI1_NSS/ I2S1_WS | SPI2_MOSI | - | - | TIM14_CH1 | - | - | EVENTOUT |
| PA5 | SPI1_SCK/ I2S1_CK | - | - | - | - | - | - | EVENTOUT |
| PA6 | SPI1_MISO/ I2S1_MCK | TIM3_CH1 | TIM1_BKIN | - | - | TIM16_CH1 | - | - |
| PA7 | SPI1_MOSI/ I2S1_SD | TIM3_CH2 | TIM1_CH1N | - | TIM14_CH1 | TIM17_CH1 | - | - |
| PA8 | MCO | SPI2_NSS | TIM1_CH1 | - | - | - | - | EVENTOUT |
| PA9 | MCO | USART1_TX | TIM1_CH2 | - | SPI2_MISO | TIM15_BKIN | I2C1_SCL | EVENTOUT |
| PA10 | SPI2_MOSI | USART1_RX | TIM1_CH3 | - | - | TIM17_BKIN | I2C1_SDA | EVENTOUT |
| PA11 | SPI1_MISO/ I2S1_MCK | USART1_CTS | TIM1_CH4 | - | - | TIM1_BKIN2 | I2C2_SCL | - |
| PA12 | SPI1_MOSI/ I2S1_SD | USART1_RTS _DE_CK | TIM1_ETR | - | - | I2S_CKIN | I2C2_SDA | - |
| PA13 | SWDIO | IR_OUT | - | - | - | - | - | EVENTOUT |
| PA14 | SWCLK | USART2_TX | - | - | - | - | - | EVENTOUT |
| PA15 | SPI1_NSS/ I2S1_WS | USART2_RX | - | - | - | - | - | EVENTOUT |

**Table 14. Port B alternate function mapping**

| Port | AF0 | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 |
|---|---|---|---|---|---|---|---|---|
| PB0 | SPI1_NSS/ I2S1_WS | TIM3_CH3 | TIM1_CH2N | - | - | - | - | - |
| PB1 | TIM14_CH1 | TIM3_CH4 | TIM1_CH3N | - | - | - | - | EVENTOUT |
| PB2 | - | SPI2_MISO | - | - | - | - | - | EVENTOUT |
| PB3 | SPI1_SCK/ I2S1_CK | TIM1_CH2 | - | - | USART1_RTS _DE_CK | - | - | EVENTOUT |
| PB4 | SPI1_MISO/ I2S1_MCK | TIM3_CH1 | - | - | USART1_CTS | TIM17_BKIN | - | EVENTOUT |
| PB5 | SPI1_MOSI/ I2S1_SD | TIM3_CH2 | TIM16_BKIN | - | - | - | I2C1_SMBA | - |
| PB6 | USART1_TX | TIM1_CH3 | TIM16_CH1N | - | SPI2_MISO | - | I2C1_SCL | EVENTOUT |
| PB7 | USART1_RX | SPI2_MOSI | TIM17_CH1N | - | - | - | I2C1_SDA | EVENTOUT |
| PB8 | - | SPI2_SCK | TIM16_CH1 | - | - | TIM15_BKIN | I2C1_SCL | EVENTOUT |
| PB9 | IR_OUT | - | TIM17_CH1 | - | - | SPI2_NSS | I2C1_SDA | EVENTOUT |
| PB10 | - | - | - | - | - | SPI2_SCK | I2C2_SCL | - |
| PB11 | SPI2_MOSI | - | - | - | - | - | I2C2_SDA | - |
| PB12 | SPI2_NSS | - | TIM1_BKIN | - | - | TIM15_BKIN | - | EVENTOUT |
| PB13 | SPI2_SCK | - | TIM1_CH1N | - | - | TIM15_CH1N | I2C2_SCL | EVENTOUT |
| PB14 | SPI2_MISO | - | TIM1_CH2N | - | - | TIM15_CH1 | I2C2_SDA | EVENTOUT |
| PB15 | SPI2_MOSI | - | TIM1_CH3N | - | TIM15_CH1N | TIM15_CH2 | - | EVENTOUT |

**Table 15. Port C alternate function mapping**

| Port | AF0 | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 |
|---|---|---|---|---|---|---|---|---|
| PC6 | - | TIM3_CH1 | - | - | - | - | - | - |
| PC7 | - | TIM3_CH2 | - | - | - | - | - | - |
| PC13 | - | - | TIM1_BKIN | - | - | - | - | - |
| PC14 | - | - | TIM1_BKIN2 | - | - | - | - | - |
| PC15 | OSC32_EN | OSC_EN | TIM15_BKIN | - | - | - | - | - |

**Table 16. Port D alternate function mapping**

| Port | AF0 | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 |
|---|---|---|---|---|---|---|---|---|
| PD0 | EVENTOUT | SPI2_NSS | TIM16_CH1 | - | - | - | - | - |
| PD1 | EVENTOUT | SPI2_SCK | TIM17_CH1 | - | - | - | - | - |
| PD2 | - | TIM3_ETR | TIM1_CH1N | - | - | - | - | - |
| PD3 | USART2_CTS | SPI2_MISO | TIM1_CH2N | - | - | - | - | - |

**Table 17. Port F alternate function mapping**

| Port | AF0 | AF1 | AF2 | AF3 | AF4 | AF5 | AF6 | AF7 |
|---|---|---|---|---|---|---|---|---|
| PF0 | - | - | TIM14_CH1 | - | - | - | - | - |
| PF1 | OSC_EN | - | TIM15_CH1N | - | - | - | - | - |

# 5 Electrical characteristics

## 5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to $V_{SS}$.

Parameter values defined at temperatures or in temperature ranges out of the ordering information scope are to be ignored.

Packages used for characterizing certain electrical parameters may differ from the commercial packages as per the ordering information.

### 5.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A$ = 25 °C and $T_A$ = $T_A$(max) (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

### 5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A$ = 25 °C, $V_{DD}$ = $V_{DDA}$ = 3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

### 5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

### 5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

### 5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

**Figure 6. Pin loading conditions**

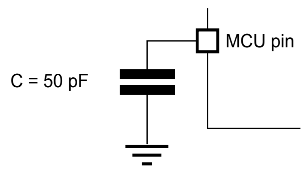
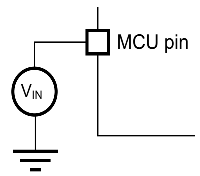
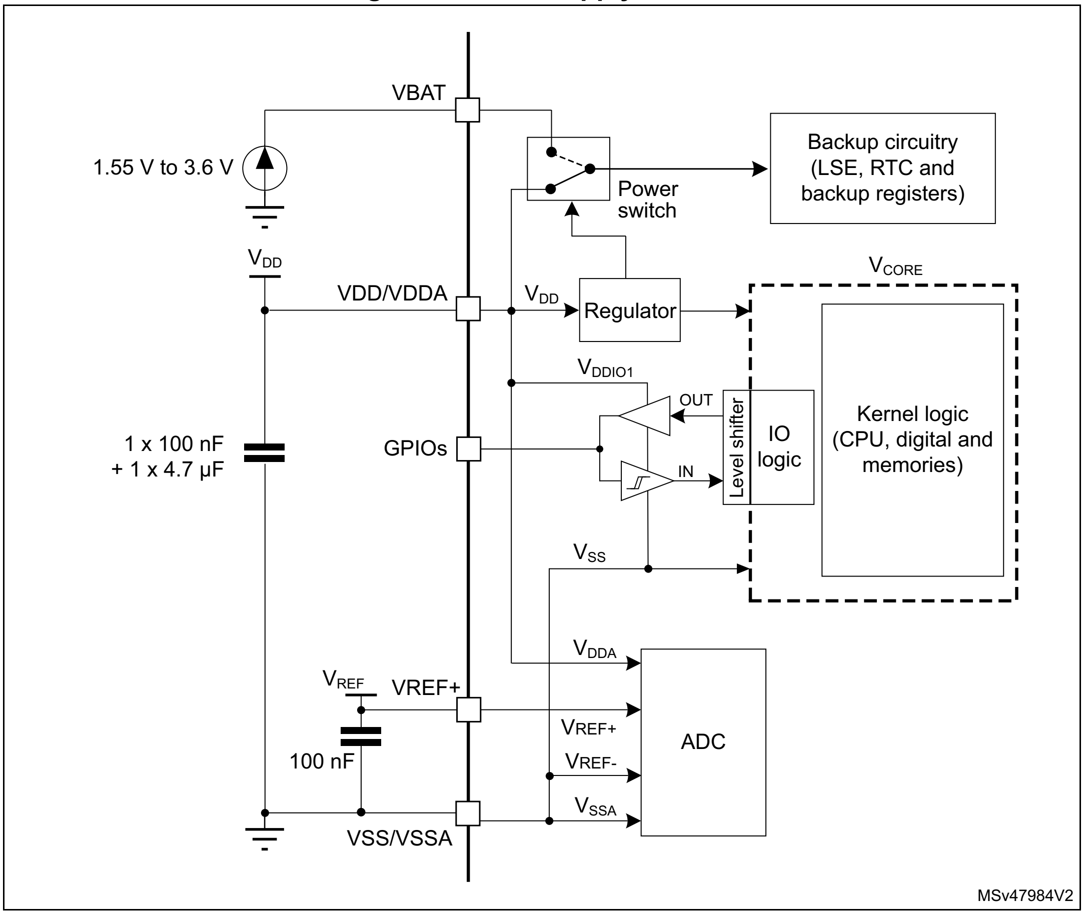



**Figure 7. Pin input voltage**



### 5.1.6 Power supply scheme

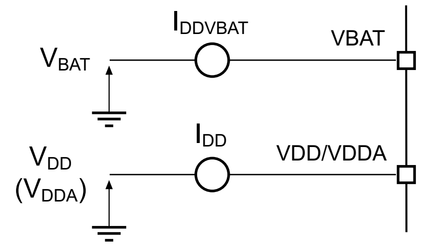
**Figure 8. Power supply scheme**




**Caution:** Power supply pin pair (VDD/VDDA and VSS/VSSA) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

### 5.1.7 Current consumption measurement

**Figure 9. Current consumption measurement scheme**




## 5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 18*, *Table 19* and *Table 20* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. The device mission profile (application conditions) is compliant with the JEDEC JESD47 qualification standard.

All voltages are defined with respect to $V_{SS}$.

**Table 18. Voltage characteristics**

| Symbol | Ratings | Min | Max | Unit |
|---|---|---|---|---|
| $V_{DD}$ | External supply voltage | -0.3 | 4.0 | V |
| $V_{BAT}$ | External supply voltage on VBAT pin | -0.3 | 4.0 | V |
| $V_{REF+}$ | External voltage on VREF+ pin | -0.3 | Min($V_{DD}$ + 0.4, 4.0) | V |
| $V_{IN}$(1) | Input voltage on FT_xx | -0.3 | $V_{DD}$ + 4.0(2)(3) | V |
| | Input voltage on any other pin | -0.3 | 4.0 | |

1. Refer to *Table 19* for the maximum allowed injected current values.
2. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
3. When an FT_a pin is used by an analog peripheral such as ADC, the maximum $V_{IN}$ is 4 V.

**Table 19. Current characteristics**

| Symbol | Ratings | Max | Unit |
|---|---|---|---|
| $I_{VDD/VDDA}$ | Current into VDD/VDDA power pin (source)(1) | 100 | mA |
| $I_{VSS/VSSA}$ | Current out of VSS/VSSA ground pin (sink)(2) | 100 | mA |
| $I_{IO(PIN)}$ | Output current sunk by any I/O and control pin except FT_f | 15 | mA |
| | Output current sunk by any FT_f pin | 20 | |
| | Output current sourced by any I/O and control pin | 15 | |

**Table 19. Current characteristics (continued)**

| Symbol | Ratings | Max | Unit |
|---|---|---|---|
| $\Sigma I_{IO(PIN)}$ | Total output current sunk by sum of all I/Os and control pins | 80 | mA |
| | Total output current sourced by sum of all I/Os and control pins | 80 | |
| $I_{INJ(PIN)}$(2) | Injected current on a FT_xx pin | -5 / NA(3) | mA |
| | Injected current on a TT_a pin(4) | -5 / 0 | |
| $\Sigma\|I_{INJ(PIN)}\|$ | Total injected current (sum of all I/Os and control pins)(5) | 25 | mA |

1. All main power (VDD/VDDA, VBAT) and ground (VSS/VSSA) pins must always be connected to the external power supplies, in the permitted range.
2. A positive injection is induced by $V_{IN} > V_{DDIO1}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer also to *Table 18: Voltage characteristics* for the maximum allowed input voltage values.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. On these I/Os, any current injection disturbs the analog performances of the device.
5. When several inputs are submitted to a current injection, the maximum $\Sigma|I_{INJ(PIN)}|$ is the absolute sum of the negative injected currents (instantaneous values).

**Table 20. Thermal characteristics**

| Symbol | Ratings | Value | Unit |
|---|---|---|---|
| $T_{STG}$ | Storage temperature range | -65 to +150 | °C |
| $T_J$ | Maximum junction temperature | 150 | °C |

## 5.3 Operating conditions

### 5.3.1 General operating conditions

**Table 21. General operating conditions**

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $f_{HCLK}$ | Internal AHB clock frequency | - | 0 | 64 | MHz |
| $f_{PCLK}$ | Internal APB clock frequency | - | 0 | 64 | |
| $V_{DD/DDA}$ | Supply voltage | - | 2.0(1) | 3.6 | V |
| $V_{BAT}$ | Backup operating voltage | - | 1.55 | 3.6 | V |
| $V_{IN}$ | I/O input voltage | - | -0.3 | Min($V_{DD}$ + 3.6, 5.5)(2) | V |
| | | TT_xx | -0.3 | $V_{DD}$ + 0.3 | |
| $T_A$ | Ambient temperature(3) | - | -40 | 85 | °C |
| $T_J$ | Junction temperature | - | -40 | 105 | °C |

1. When RESET is released functionality is guaranteed down to $V_{PDR}$ min.
2. For operation with voltage higher than $V_{DD}$ +0.3 V, the internal pull-up and pull-down resistors must be disabled.
3. The $T_A$(max) applies to $P_D$(max). At $P_D$ < $P_D$(max) the ambient temperature is allowed to go higher than $T_A$(max) provided that the junction temperature $T_J$ does not exceed $T_J$(max). Refer to *Section 6.5: Thermal characteristics*.

### 5.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 22* are derived from tests performed under the ambient temperature condition summarized in *Table 21*.

**Table 22. Operating conditions at power-up / power-down**

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $t_{VDD}$ | $V_{DD}$ slew rate | $V_{DD}$ rising | - | ∞ | µs/V |
| | | $V_{DD}$ falling | 10 | ∞ | |

### 5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 23* are derived from tests performed under the ambient temperature conditions summarized in *Table 21*.

**Table 23. Embedded reset and power control block characteristics**

| Symbol | Parameter | Conditions[(1)] | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $t_{RSTTEMPO}$[(2)] | POR temporization when $V_{DD}$ crosses $V_{POR}$ | $V_{DD}$ rising | - | 250 | 400 | µs |
| $V_{POR}$[(2)] | Power-on reset threshold | - | 2.06 | 2.10 | 2.14 | V |
| $V_{PDR}$[(2)] | Power-down reset threshold | - | 1.96 | 2.00 | 2.04 | V |
| $V_{hyst\_POR\_PDR}$ | Hysteresis of $V_{POR}$ and $V_{PDR}$ | Hysteresis in continuous mode | - | 20 | - | mV |
| | | Hysteresis in other mode | - | 30 | - | |

1. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.
2. Specified by design. Not tested in production.

### 5.3.4 Embedded voltage reference

The parameters given in *Table 24* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

**Table 24. Embedded internal voltage reference**

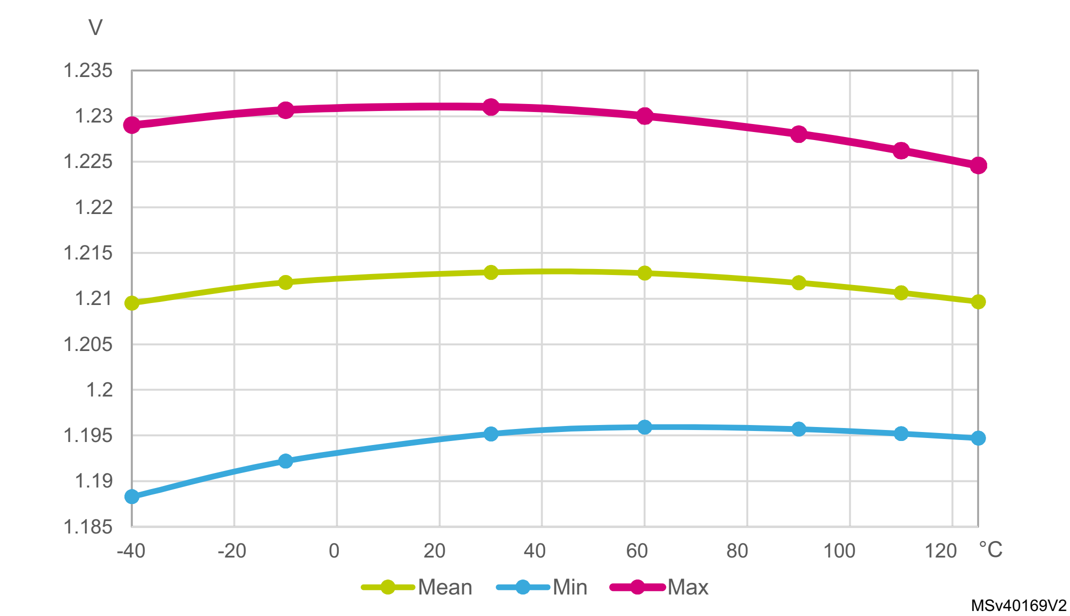
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{REFINT}$ | Internal reference voltage | -40°C < $T_J$ < 105°C | 1.182 | 1.212 | 1.232 | V |
| $t_{S\_vrefint}$[(1)] | ADC sampling time when reading the internal reference voltage | - | 4[(2)] | - | - | µs |
| $t_{start\_vrefint}$ | Start time of reference voltage buffer when ADC is enable | - | - | 8 | 12[(2)] | µs |
| $I_{DD(VREFINTBUF)}$ | $V_{REFINT}$ buffer consumption from $V_{DD}$ when converted by ADC | - | - | 12.5 | 20[(2)] | µA |
| $\Delta V_{REFINT}$ | Internal reference voltage spread over the temperature range | $V_{DD}$ = 3 V | - | 5 | 7.5[(2)] | mV |

**Table 24. Embedded internal voltage reference (continued)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $T_{Coeff\_vrefint}$ | Temperature coefficient | - | - | 30 | 50(2) | ppm/°C |
| $A_{Coeff}$ | Long term stability | 1000 hours, T = 25 °C | - | 300 | 1000(2) | ppm |
| $V_{DDCoeff}$ | Voltage coefficient | 3.0 V < $V_{DD}$ < 3.6 V | - | 250 | 1200(2) | ppm/V |
| $V_{REFINT\_DIV1}$ | 1/4 reference voltage | - | 24 | 25 | 26 | % $V_{REFINT}$ |
| $V_{REFINT\_DIV2}$ | 1/2 reference voltage | | 49 | 50 | 51 | |
| $V_{REFINT\_DIV3}$ | 3/4 reference voltage | | 74 | 75 | 76 | |

1. The shortest sampling time can be determined in the application by multiple iterations.
2. Specified by design. Not tested in production.

**Figure 10. $V_{REFINT}$ vs. temperature**




### 5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 9: Current consumption measurement scheme*.

### Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The flash memory access time is adjusted with the minimum wait states number, depending on the $f_{HCLK}$ frequency (refer to the table “Number of wait states according to CPU clock (HCLK) frequency” available in the RM0444 reference manual).
- When the peripherals are enabled $f_{PCLK} = f_{HCLK}$
- For flash memory and shared peripherals $f_{PCLK} = f_{HCLK} = f_{HCLKS}$

Unless otherwise stated, values given in *Table 25* through *Table 31* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

**Table 25. Current consumption in Run and Low-power run modes at different die temperatures**

| Symbol | Parameter | Conditions | | | Typ | | Max[1] | | Unit |
|---|---|---|---|---|---|---|---|---|---|
| | | General | $f_{HCLK}$ | Fetch from[2] | 25°C | 85°C | 25°C | 85°C | |
| $I_{DD(Run)}$ | Supply current in Run mode | Range 1; PLL enabled; $f_{HCLK} = f_{HSI}$ bypass (≤16 MHz), $f_{HCLK} = f_{PLLRCLK}$ (>16 MHz);[3] | 64 MHz | Flash memory | 5.8 | 5.9 | 7.4 | 7.7 | mA |
| | | | 56 MHz | | 5.1 | 5.2 | 6.5 | 6.7 | |
| | | | 48 MHz | | 4.5 | 4.7 | 5.8 | 6.1 | |
| | | | 32 MHz | | 3.1 | 3.3 | 4.1 | 4.2 | |
| | | | 24 MHz | | 2.5 | 2.6 | 3.3 | 3.4 | |
| | | | 16 MHz | | 1.6 | 1.7 | 2.1 | 2.2 | |
| | | | 64 MHz | SRAM | 5.2 | 5.3 | 6.6 | 6.7 | |
| | | | 56 MHz | | 4.6 | 4.7 | 5.8 | 5.9 | |
| | | | 48 MHz | | 4.1 | 4.2 | 5.3 | 5.4 | |
| | | | 32 MHz | | 2.9 | 3.0 | 3.7 | 3.9 | |
| | | | 24 MHz | | 2.1 | 2.3 | 2.9 | 3.1 | |
| | | | 16 MHz | | 1.4 | 1.5 | 1.9 | 2.0 | |
| | | Range 2; PLL enabled; $f_{HCLK} = f_{HSI}$ bypass (≤16 MHz), $f_{HCLK} = f_{PLLRCLK}$ (>16 MHz);[3] | 16 MHz | Flash memory | 1.27 | 1.32 | 1.76 | 1.87 | |
| | | | 8 MHz | | 0.70 | 0.79 | 1.10 | 1.10 | |
| | | | 2 MHz | | 0.26 | 0.34 | 0.44 | 0.77 | |
| | | | 16 MHz | SRAM | 1.16 | 1.21 | 1.54 | 1.54 | |
| | | | 8 MHz | | 0.63 | 0.70 | 0.88 | 0.88 | |
| | | | 2 MHz | | 0.24 | 0.32 | 0.44 | 0.77 | |

Table 25. Current consumption in Run and Low-power run modes at different die temperatures (continued)

| Symbol | Parameter | Conditions: General | Conditions: $f_{HCLK}$ | Conditions: Fetch from(2) | Typ 25°C | Typ 85°C | Max(1) 25°C | Max(1) 85°C | Unit |
|---|---|---|---|---|---|---|---|---|---|
| $I_{DD(LPRun)}$ | Supply current in Low-power run mode | PLL disabled; $f_{HCLK} = f_{HSE}$ bypass (> 32 kHz), $f_{HCLK} = f_{LSE}$ bypass (= 32 kHz); (3) | 2 MHz | Flash memory | 187 | 424 | 550 | 726 | µA |
| | | | 1 MHz | | 101 | 314 | 490 | 660 | |
| | | | 500 kHz | | 59 | 154 | 429 | 589 | |
| | | | 125 kHz | | 26 | 90 | 341 | 517 | |
| | | | 32 kHz | | 18 | 70 | 308 | 495 | |
| | | | 2 MHz | SRAM | 167 | 379 | 506 | 660 | |
| | | | 1 MHz | | 90 | 286 | 440 | 605 | |
| | | | 500 kHz | | 52 | 138 | 385 | 539 | |
| | | | 125 kHz | | 23 | 81 | 308 | 473 | |
| | | | 32 kHz | | 16 | 63 | 275 | 451 | |

1. Based on characterization results, not tested in production.
2. Prefetch and cache enabled when fetching from flash memory. Code compiled with high optimization for space in SRAM.
3. $V_{DD}$ = 3.0 V for values in Typ columns and 3.6 V for values in Max columns, all peripherals disabled.

Table 26. Current consumption in Sleep and Low-power sleep modes

| Symbol | Parameter | Conditions: General | Conditions: Voltage scaling | Conditions: $f_{HCLK}$ | Typ 25°C | Typ 85°C | Max(1) 25°C | Max(1) 85°C | Unit |
|---|---|---|---|---|---|---|---|---|---|
| $I_{DD(Sleep)}$ | Supply current in Sleep mode | Flash memory enabled; $f_{HCLK} = f_{HSE}$ bypass (≤16 MHz; PLL disabled), $f_{HCLK} = f_{PLLRCLK}$ (>16 MHz; PLL enabled); All peripherals disabled | Range 1 | 64 MHz | 1.5 | 1.7 | 1.8 | 2.3 | mA |
| | | | | 56 MHz | 1.4 | 1.5 | 1.7 | 2.2 | |
| | | | | 48 MHz | 1.2 | 1.3 | 1.4 | 1.9 | |
| | | | | 32 MHz | 0.9 | 1.0 | 1.1 | 1.4 | |
| | | | | 24 MHz | 0.8 | 0.8 | 0.9 | 1.3 | |
| | | | | 16 MHz | 0.4 | 0.5 | 0.6 | 0.9 | |
| | | | Range 2 | 16 MHz | 0.4 | 0.4 | 0.4 | 0.8 | |
| | | | | 8 MHz | 0.2 | 0.3 | 0.3 | 0.7 | |
| | | | | 2 MHz | 0.1 | 0.2 | 0.2 | 0.4 | |
| $I_{DD(LPSleep)}$ | Supply current in Low-power sleep mode | Flash memory disabled; PLL disabled; $f_{HCLK} = f_{HSE}$ bypass (> 32 kHz), $f_{HCLK} = f_{LSE}$ bypass (= 32 kHz); All peripherals disabled | | 2 MHz | 53 | 127 | 92 | 198 | µA |
| | | | | 1 MHz | 34 | 100 | 106 | 154 | |
| | | | | 500 kHz | 24 | 86 | 85 | 143 | |
| | | | | 125 kHz | 17 | 72 | 59 | 132 | |
| | | | | 32 kHz | 15 | 67 | 33 | 132 | |

1. Based on characterization results, not tested in production.

**Table 27. Current consumption in Stop 0 mode**

| Symbol | Parameter | Conditions | | Typ | | Max(1) | | Unit |
|---|---|---|---|---|---|---|---|---|
| | | $V_{DD}$ | | 25°C | 85°C | 25°C | 85°C | |
| $I_{DD(Stop\ 0)}$ | Supply current in Stop 0 mode | HSI kernel ON | 2.4 V | 292 | 347 | 325 | 440 | µA |
| | | | 3 V | 297 | 347 | 330 | 451 | |
| | | | 3.6 V | 297 | 352 | 336 | 451 | |
| | | HSI kernel OFF | 2.4V | 106 | 171 | 138 | 231 | |
| | | | 3V | 108 | 176 | 138 | 231 | |
| | | | 3.6V | 110 | 182 | 143 | 242 | |

1. Based on characterization results, not tested in production.

**Table 28. Current consumption in Stop 1 mode**

| Symbol | Parameter | Conditions | | | Typ | | Max(1) | | Unit |
|---|---|---|---|---|---|---|---|---|---|
| | | | RTC | $V_{DD}$ | 25°C | 85°C | 25°C | 85°C | |
| $I_{DD(Stop\ 1)}$ | Supply current in Stop 1 mode | Flash memory not powered | Disabled | 2.4 V | 5 | 55 | 12 | 132 | µA |
| | | | | 3 V | 5 | 56 | 18 | 143 | |
| | | | | 3.6 V | 6 | 57 | 22 | 154 | |
| | | | Enabled (clocked by LSE bypass) | 2.4 V | 6 | 56 | 14 | 132 | |
| | | | | 3 V | 6 | 56 | 20 | 143 | |
| | | | | 3.6 V | 6 | 57 | 25 | 154 | |
| | | Flash memory powered | Disabled | 2.4 V | 9 | 60 | 15 | 154 | |
| | | | | 3 V | 10 | 61 | 21 | 164 | |
| | | | | 3.6 V | 10 | 62 | 26 | 176 | |

1. Based on characterization results, not tested in production.

**Table 29. Current consumption in Standby mode**

| Symbol | Parameter | Conditions | | Typ | | Max(1) | | Unit |
|---|---|---|---|---|---|---|---|---|
| | | General | $V_{DD}$ | 25°C | 85°C | 25°C | 85°C | |
| $I_{DD(Standby)}$ | Supply current in Standby mode | RTC disabled | 2.4 V | 0.2 | 2.8 | 0.6 | 11 | µA |
| | | | 3.0 V | 0.3 | 3.4 | 0.5 | 11 | |
| | | | 3.6 V | 0.5 | 4.0 | 1.0 | 14 | |
| | | RTC enabled, clocked by LSI | 2.4 V | 0.5 | 3.1 | 0.7 | 11 | |
| | | | 3.0 V | 0.7 | 3.7 | 1.2 | 11 | |
| | | | 3.6 V | 1.0 | 4.4 | 1.8 | 14 | |
| | | IWDG enabled, clocked by LSI | 2.4 V | 0.4 | 3.0 | 0.9 | 11 | |
| | | | 3.0 V | 0.6 | 3.6 | 1.4 | 14 | |
| | | | 3.6 V | 0.8 | 4.2 | 2.1 | 14 | |

1. Based on characterization results, not tested in production.

**Table 30. Current consumption in VBAT mode**

| Symbol | Parameter | Conditions | | Typ | | Unit |
|---|---|---|---|---|---|---|
| | | RTC | $V_{BAT}$ | 25°C | 85°C | |
| $I_{DD\_VBAT}$ | Supply current in VBAT mode | Enabled, clocked by LSE bypass at 32.768 kHz | 1.8 V | 198 | 429 | nA |
| | | | 2.4 V | 286 | 539 | |
| | | | 3.0 V | 374 | 671 | |
| | | | 3.6 V | 484 | 842 | |
| | | Enabled, clocked by LSE crystal at 32.768 kHz | 1.8 V | 330 | 550 | |
| | | | 2.4 V | 429 | 671 | |
| | | | 3.0 V | 506 | 770 | |
| | | | 3.6 V | 638 | 941 | |
| | | Disabled | 1.8 V | 2.20 | 220 | |
| | | | 2.4 V | 4.40 | 259 | |
| | | | 3.0 V | 5.50 | 303 | |
| | | | 3.6 V | 11.0 | 369 | |

## I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

### I/O static current consumption

All the I/Os used with internal or external pull-up or pull-down resistor generate current consumption when the pin is externally or internally tied low or high, respectively. The value of this current consumption can be simply computed by using the pull-up/pull-down resistor values. For internal pull-up/pull-down resistors, the indicative values are given in *Table 48: I/O static characteristics*. Any other external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

**Caution:** Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

**I/O dynamic current consumption**

In addition to the internal peripheral current consumption measured previously (see *Table 31: Current consumption of peripherals*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal and external) connected to the pin:

$$I_{SW} = V_{DDIO1} \times f_{SW} \times C$$

where

$I_{SW}$ is the current sunk by a switching I/O to charge/discharge the capacitive load

$V_{DDIO1}$ is the I/O supply voltage

$f_{SW}$ is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

$C_S$ is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- All I/O pins are in Analog mode
- The given value is calculated by measuring the difference of the current consumptions:
  - when the peripheral is clocked on
  - when the peripheral is clocked off
- Ambient operating temperature and supply voltage conditions summarized in *Table 18: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in the following table. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

**Table 31. Current consumption of peripherals**

| Peripheral | Bus | Consumption in µA/MHz | | |
|---|---|---|---|---|
| | | Range 1 | Range 2 | Low-power run and sleep |
| IOPORT Bus | IOPORT | 0.5 | 0.4 | 0.3 |
| GPIOA | IOPORT | 2.5 | 2.1 | 2.4 |
| GPIOB | IOPORT | 2.5 | 2.1 | 2.4 |
| GPIOC | IOPORT | 0.8 | 0.7 | 0.9 |
| GPIOD | IOPORT | 0.7 | 0.6 | 0.8 |
| GPIOF | IOPORT | 0.5 | 0.4 | 0.6 |
| Bus matrix | AHB | 0.01 | 0.01 | 0.03 |
| All AHB Peripherals | AHB | 11.0 | 9.0 | 10.0 |
| DMA1/DMAMUX | AHB | 3.9 | 3.2 | 3.5 |
| CRC | AHB | 0.4 | 0.3 | 0.4 |
| FLASH | AHB | 4.9 | 4.1 | 4.6 |
| All APB peripherals | APB | 59.0 | 49.0 | 55.5 |
| AHB to APB bridge(1) | APB | 0.2 | 0.2 | 0.1 |
| PWR | APB | 0.5 | 0.4 | 0.4 |
| SYSCFG | APB | 0.4 | 0.3 | 0.3 |
| WWDG | APB | 0.4 | 0.3 | 0.4 |
| TIM1 | APB | 6.6 | 5.5 | 6.0 |
| TIM3 | APB | 4.1 | 3.4 | 3.8 |
| TIM6 | APB | 1.1 | 0.9 | 1.0 |
| TIM7 | APB | 0.8 | 0.7 | 0.6 |
| TIM14 | APB | 1.4 | 1.1 | 1.1 |
| TIM15 | APB | 3.6 | 3.0 | 3.3 |
| TIM16 | APB | 2.2 | 1.8 | 2.0 |
| TIM17 | APB | 0.8 | 0.7 | 0.6 |
| I2C1 | APB | 3.5 | 2.9 | 3.2 |
| I2C2 | APB | 0.8 | 0.6 | 0.6 |
| SPI1 | APB | 3.2 | 2.7 | 2.9 |
| SPI2 | APB | 2.0 | 1.6 | 1.8 |
| USART1 | APB | 6.9 | 5.7 | 6.5 |
| USART2 | APB | 1.8 | 1.5 | 1.6 |
| ADC | APB | 2.7 | 2.2 | 2.3 |

1. The AHB to APB Bridge is automatically active when at least one peripheral is ON on the APB.

### 5.3.6 Wakeup time from low-power modes and voltage scaling transition times

The wakeup times given in *Table 32* are the latency between the event and the execution of the first user instruction.

**Table 32. Low-power mode wakeup times(1)**

| Symbol | Parameter | Conditions | Typ | Max | Unit |
|---|---|---|---|---|---|
| $t_{WUSLEEP}$ | Wakeup time from Sleep to Run mode | - | 11 | 11 | CPU cycles |
| $t_{WULPSLEEP}$ | Wakeup time from Low-power sleep mode | Transiting to Low-power-run-mode execution in flash memory not powered in Low-power sleep mode;<br>HCLK = HSI16 / 8 = 2 MHz | 11 | 14 | CPU cycles |
| $t_{WUSTOP0}$ | Wakeup time from Stop 0 | Transiting to Run-mode execution in flash memory not powered in Stop 0 mode;<br>HCLK = HSI16 = 16 MHz;<br>Regulator in Range 1 or Range 2 | 5.6 | 6 | µs |
| | | Transiting to Run-mode execution in SRAM or in flash memory powered in Stop 0 mode;<br>HCLK = HSI16 = 16 MHz;<br>Regulator in Range 1 or Range 2 | 2 | 2.4 | |
| $t_{WUSTOP1}$ | Wakeup time from Stop 1 | Transiting to Run-mode execution in flash memory not powered in Stop 1 mode;<br>HCLK = HSI16 = 16 MHz;<br>Regulator in Range 1 or Range 2 | 9.0 | 11.2 | µs |
| | | Transiting to Run-mode execution in SRAM or in flash memory powered in Stop 1 mode;<br>HCLK = HSI16 = 16 MHz;<br>Regulator in Range 1 or Range 2 | 5 | 7.5 | |
| | | Transiting to Low-power-run-mode execution in flash memory not powered in Stop 1 mode;<br>HCLK = HSI16/8 = 2 MHz;<br>Regulator in low-power mode (LPR = 1 in PWR_CR1) | 22 | 25.3 | |
| | | Transiting to Low-power-run-mode execution in SRAM or in flash memory powered in Stop 1 mode;<br>HCLK = HSI16 / 8 = 2 MHz;<br>Regulator in low-power mode (LPR = 1 in PWR_CR1) | 18 | 23.5 | |
| $t_{WUSTBY}$ | Wakeup time from Standby mode | Transiting to Run mode;<br>HCLK = HSI16 = 16 MHz;<br>Regulator in Range 1 | 14.5 | 30 | µs |
| $t_{WULPRUN}$ | Wakeup time from Low-power run mode(2) | Transiting to Run mode;<br>HSISYS = HSI16/8 = 2 MHz | 5 | 7 | µs |

1. Based on characterization results, not tested in production.
2. Time until REGLPF flag is cleared in PWR_SR2.

**Table 33. Regulator mode transition times[1]**

| Symbol | Parameter | Conditions | Typ | Max | Unit |
|---|---|---|---|---|---|
| $t_{VOST}$ | Transition times between regulator Range 1 and Range 2[2] | HSISYS = HSI16 | 20 | 40 | µs |

1. Based on characterization results, not tested in production.
2. Time until VOSF flag is cleared in PWR_SR2.

## 5.3.7 External clock source characteristics

### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

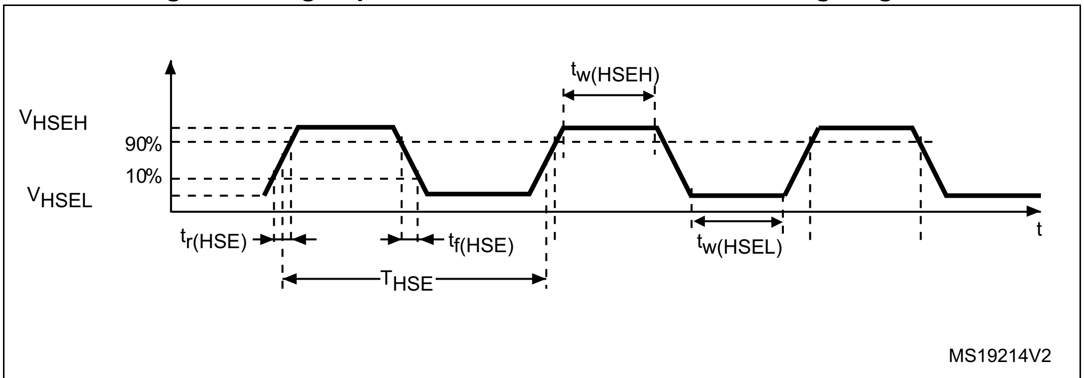
The external clock signal has to respect the I/O characteristics in *Section 5.3.14*. See *Figure 11* for recommended clock input waveform.

**Table 34. High-speed external user clock characteristics[1]**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{HSE\_ext}$ | User external clock source frequency | Voltage scaling Range 1 | - | 8 | 48 | MHz |
| | | Voltage scaling Range 2 | - | 8 | 26 | |
| $V_{HSEH}$ | OSC_IN input pin high level voltage | - | 0.7 $V_{DDIO1}$ | - | $V_{DDIO1}$ | V |
| $V_{HSEL}$ | OSC_IN input pin low level voltage | - | $V_{SS}$ | - | 0.3 $V_{DDIO1}$ | V |
| $t_{w(HSEH)}$ $t_{w(HSEL)}$ | OSC_IN high or low time | Voltage scaling Range 1 | 7 | - | - | ns |
| | | Voltage scaling Range 2 | 18 | - | - | |

1. Specified by design. Not tested in production.

**Figure 11. High-speed external clock source AC timing diagram**



### Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

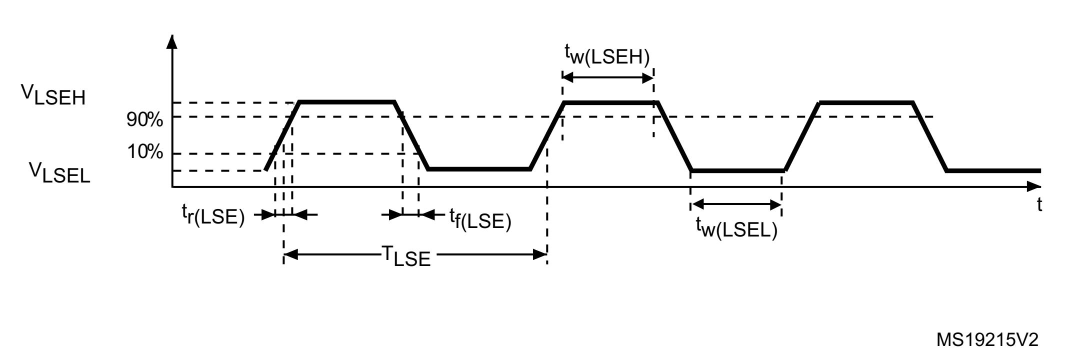
The external clock signal has to respect the I/O characteristics in *Section 5.3.14*. See *Figure 12* for recommended clock input waveform.

**Table 35. Low-speed external user clock characteristics(1)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{LSE\_ext}$ | User external clock source frequency | - | - | 32.768 | 1000 | kHz |
| $V_{LSEH}$ | OSC32_IN input pin high level voltage | - | 0.7 $V_{DDIO1}$ | - | $V_{DDIO1}$ | V |
| $V_{LSEL}$ | OSC32_IN input pin low level voltage | - | $V_{SS}$ | - | 0.3 $V_{DDIO1}$ | V |
| $t_{w(LSEH)}$ $t_{w(LSEL)}$ | OSC32_IN high or low time | - | 250 | - | - | ns |

1. Specified by design. Not tested in production.

**Figure 12. Low-speed external clock source AC timing diagram**




### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 48 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 36*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

**Table 36. HSE oscillator characteristics(1)**

| Symbol | Parameter | Conditions(2) | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{OSC\_IN}$ | Oscillator frequency | - | 4 | 8 | 48 | MHz |
| $R_F$ | Feedback resistor | - | - | 200 | - | kΩ |

**Table 36. HSE oscillator characteristics[(1)] (continued)**

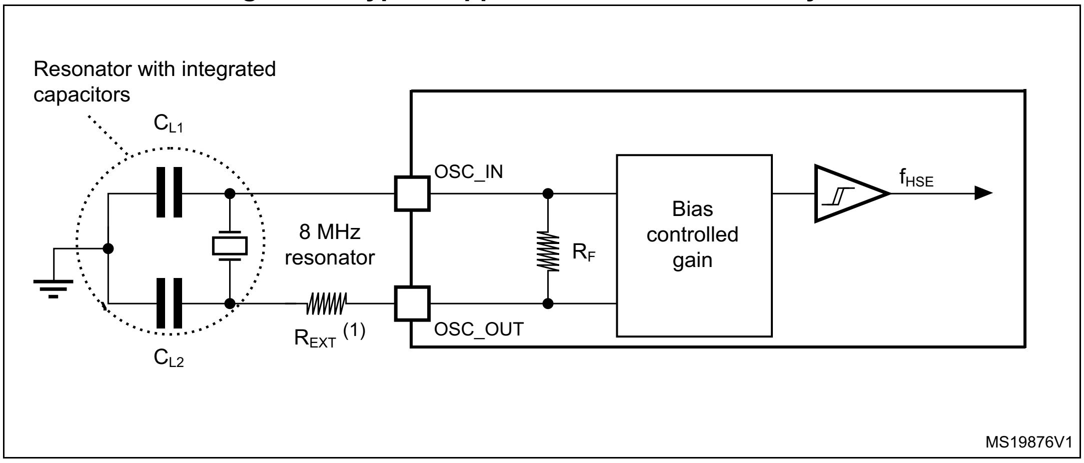
| Symbol | Parameter | Conditions[(2)] | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $I_{DD(HSE)}$ | HSE current consumption | During startup[(3)] | - | - | 5.5 | mA |
| | | $V_{DD}$ = 3 V, Rm = 30 Ω, CL = 10 pF@8 MHz | - | 0.44 | - | |
| | | $V_{DD}$ = 3 V, Rm = 45 Ω, CL = 10 pF@8 MHz | - | 0.45 | - | |
| | | $V_{DD}$ = 3 V, Rm = 30 Ω, CL = 5 pF@48 MHz | - | 0.68 | - | |
| | | $V_{DD}$ = 3 V, Rm = 30 Ω, CL = 10 pF@48 MHz | - | 0.94 | - | |
| | | $V_{DD}$ = 3 V, Rm = 30 Ω, CL = 20 pF@48 MHz | - | 1.77 | - | |
| $G_m$ | Maximum critical crystal transconductance | Startup | - | - | 1.5 | mA/V |
| $t_{SU(HSE)}$[(4)] | Startup time | $V_{DD}$ is stabilized | - | 2 | - | ms |

1. Specified by design. Not tested in production.
2. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For $C_{L1}$ and $C_{L2}$, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 13*). $C_{L1}$ and $C_{L2}$ are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of $C_{L1}$ and $C_{L2}$. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing $C_{L1}$ and $C_{L2}$.

*Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.*

Figure 13. Typical application with an 8 MHz crystal




1. $R_{EXT}$ value depends on the crystal characteristics.

## Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 37*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 37. LSE oscillator characteristics ($f_{LSE}$ = 32.768 kHz)(1)

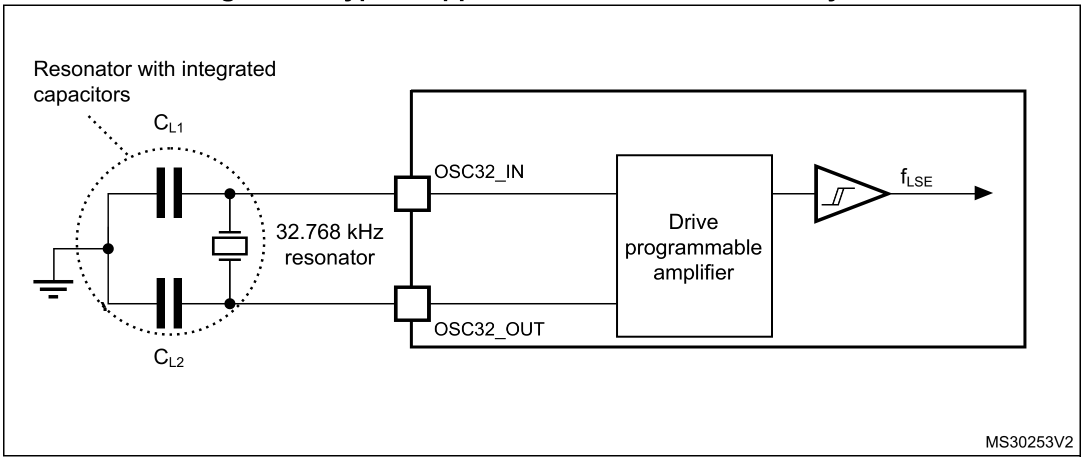
| Symbol | Parameter | Conditions(2) | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $I_{DD(LSE)}$ | LSE current consumption | LSEDRV[1:0] = 00<br>Low drive capability | - | 250 | - | nA |
| | | LSEDRV[1:0] = 01<br>Medium low drive capability | - | 315 | - | |
| | | LSEDRV[1:0] = 10<br>Medium high drive capability | - | 500 | - | |
| | | LSEDRV[1:0] = 11<br>High drive capability | - | 630 | - | |
| $Gm_{critmax}$ | Maximum critical crystal gm | LSEDRV[1:0] = 00<br>Low drive capability | - | - | 0.5 | µA/V |
| | | LSEDRV[1:0] = 01<br>Medium low drive capability | - | - | 0.75 | |
| | | LSEDRV[1:0] = 10<br>Medium high drive capability | - | - | 1.7 | |
| | | LSEDRV[1:0] = 11<br>High drive capability | - | - | 2.7 | |
| $t_{SU(LSE)}$(3) | Startup time | $V_{DD}$ is stabilized | - | 2 | - | s |

1. Specified by design. Not tested in production.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.

3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

*Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.*

**Figure 14. Typical application with a 32.768 kHz crystal**




*Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.*

### 5.3.8 Internal clock source characteristics

The parameters given in Table 38 are derived from tests performed under ambient temperature and supply voltage conditions summarized in Table 21: General operating conditions. The provided curves are characterization results, not tested in production.

#### High-speed internal (HSI16) RC oscillator

**Table 38. HSI16 oscillator characteristics(1)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{HSI16}$ | HSI16 Frequency | $V_{DD}$=3.0 V, $T_A$=30 °C | 15.88 | - | 16.08 | MHz |
| $\Delta_{Temp(HSI16)}$ | HSI16 oscillator frequency drift over temperature | $T_A$= 0 to 85 °C | -1 | - | 1 | % |
| | | $T_A$= -40 to 85 °C | -2 | - | 1.5 | % |
| $\Delta_{VDD(HSI16)}$ | HSI16 oscillator frequency drift over $V_{DD}$ | $V_{DD}$=$V_{DD}$(min) to 3.6 V | -0.1 | - | 0.05 | % |
| TRIM | HSI16 frequency user trimming step | From code 127 to 128 | -8 | -6 | -4 | % |
| | | From code 63 to 64<br>From code 191 to 192 | -5.8 | -3.8 | -1.8 | |
| | | For all other code increments | 0.2 | 0.3 | 0.4 | |
| $D_{HSI16}$(2) | Duty Cycle | - | 45 | - | 55 | % |
| $t_{su(HSI16)}$(2) | HSI16 oscillator start-up time | - | - | 0.8 | 1.2 | µs |

**Table 38. HSI16 oscillator characteristics[1] (continued)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $t_{stab(HSI16)}$[2] | HSI16 oscillator stabilization time | - | - | 3 | 5 | µs |
| $I_{DD(HSI16)}$[2] | HSI16 oscillator power consumption | - | - | 155 | 190 | µA |

1. Based on characterization results, not tested in production.
2. Specified by design. Not tested in production.

### Low-speed internal (LSI) RC oscillator

**Table 39. LSI oscillator characteristics[1]**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{LSI}$ | LSI frequency | $V_{DD}$ = 3.0 V, $T_A$ = 30 °C | 31.04 | - | 32.96 | kHz |
| | | $V_{DD}$ = $V_{DD}$(min) to 3.6 V, $T_A$ = -40 to 85 °C | 29.5 | - | 34 | |
| $t_{SU(LSI)}$[2] | LSI oscillator start-up time | - | - | 80 | 130 | µs |
| $t_{STAB(LSI)}$[2] | LSI oscillator stabilization time | 5% of final frequency | - | 125 | 180 | µs |
| $I_{DD(LSI)}$[2] | LSI oscillator power consumption | - | - | 110 | 180 | nA |

1. Based on characterization results, not tested in production.
2. Specified by design. Not tested in production.

## 5.3.9 PLL characteristics

The parameters given in *Table 40* are derived from tests performed under temperature and $V_{DD}$ supply voltage conditions summarized in *Table 21: General operating conditions*.

**Table 40. PLL characteristics[1]**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{PLL\_IN}$ | PLL input clock frequency[2] | - | 2.66 | - | 16 | MHz |
| $D_{PLL\_IN}$ | PLL input clock duty cycle | - | 45 | - | 55 | % |
| $f_{PLL\_P\_OUT}$ | PLL multiplier output clock P | Voltage scaling Range 1 | 3.09 | - | 122 | MHz |
| | | Voltage scaling Range 2 | 3.09 | - | 40 | |
| $f_{PLL\_Q\_OUT}$ | PLL multiplier output clock Q | Voltage scaling Range 1 | 12 | - | 128 | MHz |
| | | Voltage scaling Range 2 | 12 | - | 33 | |
| $f_{PLL\_R\_OUT}$ | PLL multiplier output clock R | Voltage scaling Range 1 | 12 | - | 64 | MHz |
| | | Voltage scaling Range 2 | 12 | - | 16 | |
| $f_{VCO\_OUT}$ | PLL VCO output | Voltage scaling Range 1 | 96 | - | 344 | MHz |
| | | Voltage scaling Range 2 | 96 | - | 128 | |
| $t_{LOCK}$ | PLL lock time | - | - | 15 | 40 | µs |

**Table 40. PLL characteristics[1] (continued)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Jitter | RMS cycle-to-cycle jitter | System clock 56 MHz | - | 50 | - | ±ps |
| | RMS period jitter | | - | 40 | - | |
| $I_{DD(PLL)}$ | PLL power consumption on $V_{DD}$[1] | VCO freq = 96 MHz | - | 200 | 260 | µA |
| | | VCO freq = 192 MHz | - | 300 | 380 | |
| | | VCO freq = 344 MHz | - | 520 | 650 | |

1. Specified by design. Not tested in production.
2. Make sure to use the appropriate division factor M to obtain the specified PLL input clock values.

### 5.3.10 Flash memory characteristics

**Table 41. Flash memory characteristics[1]**

| Symbol | Parameter | Conditions | Typ | Max | Unit |
|---|---|---|---|---|---|
| $t_{prog}$ | 64-bit programming time | - | 85 | 125 | µs |
| $t_{prog\_row}$ | Row (32 double word) programming time | Normal programming | 2.7 | 4.6 | ms |
| | | Fast programming | 1.7 | 2.8 | |
| $t_{prog\_page}$ | Page (2 Kbyte) programming time | Normal programming | 21.8 | 36.6 | ms |
| | | Fast programming | 13.7 | 22.4 | |
| $t_{ERASE}$ | Page (2 Kbyte) erase time | - | 22.0 | 40.0 | ms |
| $t_{prog\_bank}$ | Bank (64 Kbyte[2]) programming time | Normal programming | 0.7 | 1.2 | s |
| | | Fast programming | 0.4 | 0.7 | |
| $t_{ME}$ | Mass erase time | - | 22.1 | 40.1 | ms |
| $I_{DD(FlashA)}$ | Average consumption from $V_{DD}$ | Programming | 3 | - | mA |
| | | Page erase | 3 | - | |
| | | Mass erase | 5 | - | |
| $I_{DD(FlashP)}$ | Maximum current (peak) | Programming, 2 µs peak duration | 7 | - | mA |
| | | Erase, 41 µs peak duration | 7 | - | |

1. Specified by design. Not tested in production.
2. Values provided also apply to devices with less flash memory than one 64 Kbyte bank

**Table 42. Flash memory endurance and data retention**

| Symbol | Parameter | Conditions | Min[1] | Unit |
|---|---|---|---|---|
| $N_{END}$ | Endurance | $T_A$ = -40 to +85 °C | 1 | kcycles |
| $t_{RET}$ | Data retention | 1 kcycle[2] at $T_A$ = 85 °C | 15 | Years |

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

### 5.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

#### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to $V_{DD}$ and $V_{SS}$ through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 43*. They are based on the EMS levels and classes defined in application note AN1709.

**Table 43. EMS characteristics**

| Symbol | Parameter | Conditions | Level/ Class |
|---|---|---|---|
| $V_{FESD}$ | Voltage limits to be applied on any I/O pin to induce a functional disturbance | $V_{DD}$ = 3.3 V, $T_A$ = +25 °C, $f_{HCLK}$ = 64 MHz, LQFP48, conforming to IEC 61000-4-2 | 2B |
| $V_{EFTB}$ | Fast transient voltage burst limits to be applied through 100 pF on $V_{DD}$ and $V_{SS}$ pins to induce a functional disturbance | $V_{DD}$ = 3.3 V, $T_A$ = +25 °C, $f_{HCLK}$ = 64 MHz, LQFP48, conforming to IEC 61000-4-4 | 5A |

#### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

**Software recommendations**

The software flowchart must include the management of runaway conditions such as:

- corrupted program counter
- unexpected reset
- critical data corruption (for example control registers)

### Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

### Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

**Table 44. EMI characteristics**

| Symbol | Parameter | Conditions | Monitored frequency band | Value | Unit |
|---|---|---|---|---|---|
| $S_{EMI}$ | Peak(1) | $f_{HSE}$ = 8 MHz<br>$f_{HCLK}$ = 64 MHz<br>$V_{DD}$ = 3.6 V, $T_A$ = 25 °C,<br>LQFP48 package<br>compliant with IEC 61967-2 | 0.1 MHz to 30 MHz | 3 | dBµV |
| | | | 30 MHz to 130 MHz | 3 | |
| | | | 130 MHz to 1 GHz | 1 | |
| | | | 1 GHz to 2 GHz | 8 | |
| | Level(2) | | 0.1 MHz to 2 GHz | 2 | - |

1. Refer to AN1709 “EMI radiated test” section.
2. Refer to AN1709 “EMI level classification” section

## 5.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

**Table 45. ESD absolute maximum ratings**

| Symbol | Ratings | Conditions | Class | Maximum value(1) | Unit |
|---|---|---|---|---|---|
| $V_{ESD(HBM)}$ | Electrostatic discharge voltage (human body model) | $T_A$ = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001 | 2 | 2000 | V |
| $V_{ESD(CDM)}$ | Electrostatic discharge voltage (charge device model) | $T_A$ = +25 °C, conforming to ANSI/ESDA/JEDEC JS-002 | C2a | 500 | V |

1. Based on characterization results, not tested in production.

### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current is injected to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

**Table 46. Electrical sensitivity**

| Symbol | Parameter | Conditions | Class |
|---|---|---|---|
| LU | Static latch-up class | $T_A$ = +85 °C conforming to JESD78 | II Level A |

## 5.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below $V_{SS}$ or above $V_{DDIO1}$ (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out-of-range parameter: ADC error above a certain limit (higher than 5 LSB TUE), induced leakage current on adjacent pins out of conventional limits (-5 µA/+0 µA range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

**Table 47. I/O current injection susceptibility(1)**

<table>
<tr><th rowspan="2">Symbol</th><th rowspan="2" colspan="2">Description</th><th colspan="2">Functional susceptibility</th><th rowspan="2">Unit</th></tr>
<tr><th>Negative injection</th><th>Positive injection</th></tr>
<tr><td rowspan="6">$I_{INJ}$</td><td rowspan="6">Injected current on pin</td><td>All except PA1, PA3, PA4, PA5, PA6, PA13, PB0, PB1, PB2, and PB8</td><td>-5</td><td>N/A</td><td rowspan="6">mA</td></tr>
<tr><td>PA1, PA13, PB1, PB2</td><td>0</td><td>+5 / N/A(2)</td></tr>
<tr><td>PA3, PA6, PB0</td><td>-5</td><td>+5 / N/A(2)</td></tr>
<tr><td>PB8</td><td>0</td><td>N/A</td></tr>
<tr><td>PA4</td><td>-5</td><td>0(2)</td></tr>
<tr><td>PA5</td><td>0</td><td>+5/0(2)</td></tr>
</table>

1. Based on characterization results, not tested in production.
2. The injection current value is applicable when the switchable diode is activated, N/A when not activated.

## 5.3.14 I/O port characteristics

### General input/output characteristics

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under the conditions summarized in *Table 21: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant.

*Note: For information on GPIO configuration, refer to the application note AN4899 “STM32 GPIO configuration for hardware settings and low-power consumption” available from the ST website www.st.com.*

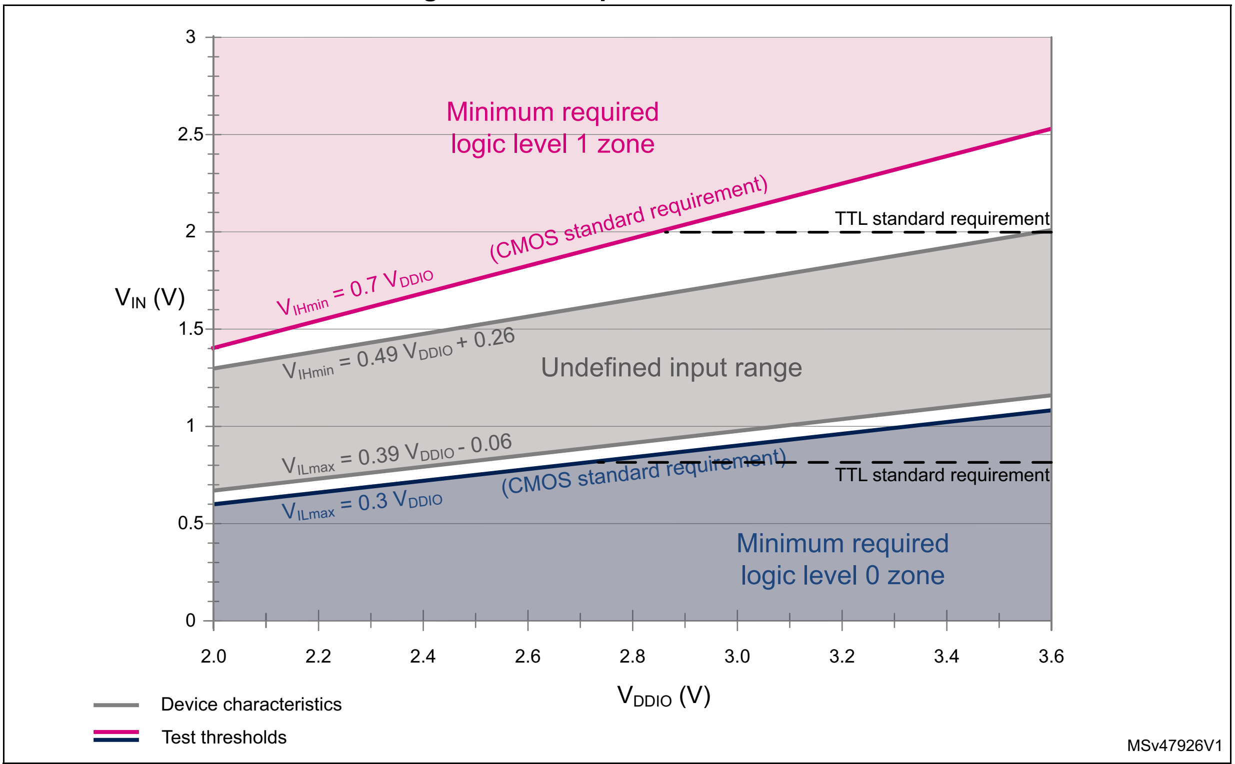
**Table 48. I/O static characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{IL}$(1) | I/O input low level voltage | All | $V_{DD}(min) < V_{DDIO1} < 3.6$ V | - | - | 0.3 x $V_{DDIO1}$ (2) | V |
| | | | | | | 0.39 x $V_{DDIO1}$ - 0.06 (3) | |
| $V_{IH}$(1) | I/O input high level voltage | All | $V_{DD}(min) < V_{DDIO1} < 3.6$ V | 0.7 x $V_{DDIO1}$ (2) | - | - | V |
| | | | | 0.49 x $V_{DDIO1}$ + 0.26 (3) | - | - | |
| $V_{hys}$(3) | I/O input hysteresis | FT_xx, NRST | $V_{DD}(min) < V_{DDIO1} < 3.6$ V | - | 200 | - | mV |
| $I_{lkg}$ | Input leakage current(3) | All except FT_e, TT_a | $0 < V_{IN} \leq V_{DDIO1}$ | - | - | ±70 | nA |
| | | | $V_{DDIO1} \leq V_{IN} \leq V_{DDIO1}+1$ V | - | - | 600(4) | |
| | | | $V_{DDIO1} +1$ V $< V_{IN} \leq 5.5$ V(3) | - | - | 150(4) | |
| | | FT_e (5) | $0 < V_{IN} \leq V_{DDIO1}$ | - | - | 5 | µA |
| | | TT_a | $V_{DDIO1} < V_{IN} \leq V_{DDIO1} + 0.3$ V | - | - | 2000(4) | nA |
| $R_{PU}$ | Weak pull-up equivalent resistor (6) | $V_{IN} = V_{SS}$ | | 25 | 40 | 55 | kΩ |
| $R_{PD}$ | Weak pull-down equivalent resistor(6) | $V_{IN} = V_{DDIO1}$ | | 25 | 40 | 55 | kΩ |
| $C_{IO}$ | I/O pin capacitance | - | | - | 5 | - | pF |

1. Refer to *Figure 15: I/O input characteristics.*
2. Tested in production.
3. Guaranteed by design.
4. This value represents the pad leakage of the I/O itself. The total product pad leakage is provided by this formula: $I_{Total\_Ileak\_max}$ = 10 µA + [number of I/Os where $V_{IN}$ is applied on the pad] x $I_{lkg}$(Max).
5. FT_e with diode enabled. Input leakage current of FT_e I/Os with the diode disabled is the same as standard I/Os.
6. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters, as shown in Figure 15.

**Figure 15. I/O input characteristics**



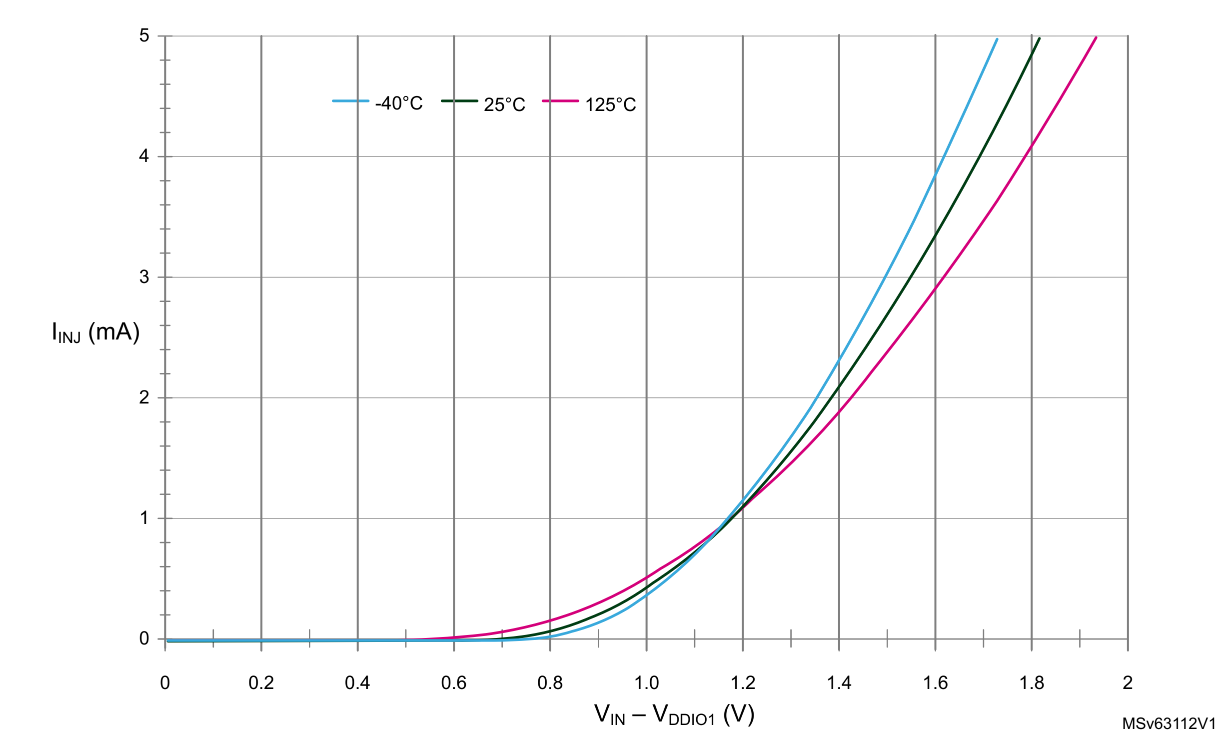

## Characteristics of FT_e I/Os

The following table and figure specify input characteristics of FT_e I/Os.

**Table 49. Input characteristics of FT_e I/Os**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $I_{INJ}$ | Injected current on pin | - | - | - | 5 | mA |
| $V_{DDIO1}$-$V_{IN}$ | Voltage over $V_{DDIO1}$ | $I_{INJ}$ = 5 mA | - | - | 2 | V |
| $R_d$ | Diode dynamic serial resistor | $I_{INJ}$ = 5 mA | - | - | 300 | Ω |

**Figure 16. Current injection into FT_e input with diode active**




## Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±6 mA, and up to ±15 mA with relaxed $V_{OL}$/$V_{OH}$.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 5.2*:

- The sum of the currents sourced by all the I/Os on $V_{DDIO1,}$ plus the maximum consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating $I_{VDD}$ (see *Table 18: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on $V_{SS}$, plus the maximum consumption of the MCU sunk on $V_{SS}$, cannot exceed the absolute maximum rating $I_{VSS}$ (see *Table 18: Voltage characteristics*).

## Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT OR TT unless otherwise specified).

**Table 50. Output voltage characteristics[1][2]**

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $V_{OL}$ | Output low level voltage for an I/O pin | CMOS port[3]<br>$\|I_{IO}\|$ 6 mA<br>$V_{DDIO1} \geq 2.7$ V | - | 0.4 | V |
| $V_{OH}$ | Output high level voltage for an I/O pin | | $V_{DDIO1}$ - 0.4 | - | V |
| $V_{OL}$ [4] | Output low level voltage for an I/O pin | TTL port[3]<br>$\|I_{IO}\| = 6$ mA<br>$V_{DDIO1} \geq 2.7$ V | - | 0.4 | V |
| $V_{OH}$ [4] | Output high level voltage for an I/O pin | | 2.4 | - | V |
| $V_{OL}$ [4] | Output low level voltage for an I/O pin | All I/Os<br>$\|I_{IO}\| = 15$ mA<br>$V_{DDIO1} \geq 2.7$ V | - | 1.3 | V |
| $V_{OH}$ [4] | Output high level voltage for an I/O pin | | $V_{DDIO1}$ - 1.3 | - | V |
| $V_{OL}$ [4] | Output low level voltage for an I/O pin | $\|I_{IO}\| = 3$ mA<br>$V_{DDIO1} \geq V_{DD}(min)$ | - | 0.4 | V |
| $V_{OH}$ [4] | Output high level voltage for an I/O pin | | $V_{DDIO1}$ - 0.45 | - | V |
| $V_{OLFM+}$ [4] | Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with _f option) | $\|I_{IO}\| = 20$ mA<br>$V_{DDIO1} \geq 2.7$ V | - | 0.4 | V |
| | | $\|I_{IO}\| = 9$ mA<br>$V_{DDIO1} \geq V_{DD}(min)$ | - | 0.4 | |

1. The $I_{IO}$ current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 18: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings $\Sigma I_{IO}$.
2. As PC13, PC14 and PC15 are supplied through the power switch, the sum of currents sourced by those I/Os must not exceed 3 mA.
3. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
4. Specified by design. Not tested in production.

### Output buffer timing characteristics

The definition and values of input/output AC characteristics are given in *Figure 17* and *Table 51*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

**Table 51. Non-FT_c I/O output timing characteristics[1][2]**

| Speed | Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|---|
| 00 | $f_{max}$ | Maximum frequency | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 2 | MHz |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 0.35 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 3 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 0.45 | |
| | $t_r/t_f$ | Output rise and fall time | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 100 | ns |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 225 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 75 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 150 | |

Table 51. Non-FT_c I/O output timing characteristics(1)(2) (continued)

| Speed | Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|---|
| 01 | $f_{max}$ | Maximum frequency | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 10 | MHz |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 2 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 15 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 2.5 | |
| | $t_r/t_f$ | Output rise and fall time | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 30 | ns |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 60 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 15 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 30 | |
| 10 | $f_{max}$ | Maximum frequency | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 30 | MHz |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 15 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 60 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 30 | |
| | $t_r/t_f$ | Output rise and fall time | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 11 | ns |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 22 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 4 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 8 | |
| 11 | $f_{max}$ | Maximum frequency | C=30 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 60 | MHz |
| | | | C=30 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 30 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 80(3) | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 40 | |
| | $t_r/t_f$ | Output rise and fall time | C=30 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 5.5 | ns |
| | | | C=30 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 11 | |
| | | | C=10 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 2.5 | |
| | | | C=10 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 5 | |
| Fm+ | $f_{max}$ | Maximum frequency | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 1 | MHz |
| | $t_f$ | Output fall time(4) | | - | 5 | ns |

1. The I/O speed is configured with the OSPEEDRy[1:0] bitfield. The FM+ mode is configured through the SYSCFG_CFGR1 register. Refer to the reference manual RM0444 for the description of the GPIO port configuration.
2. Specified by design. Not tested in production.
3. This value represents the I/O capability but the maximum system frequency is limited to 64 MHz.
4. The fall time is defined between 70% and 30% of the output waveform, according to $I^2C$ specification.

Table 52. FT_c I/O output timing characteristics(1)(2)

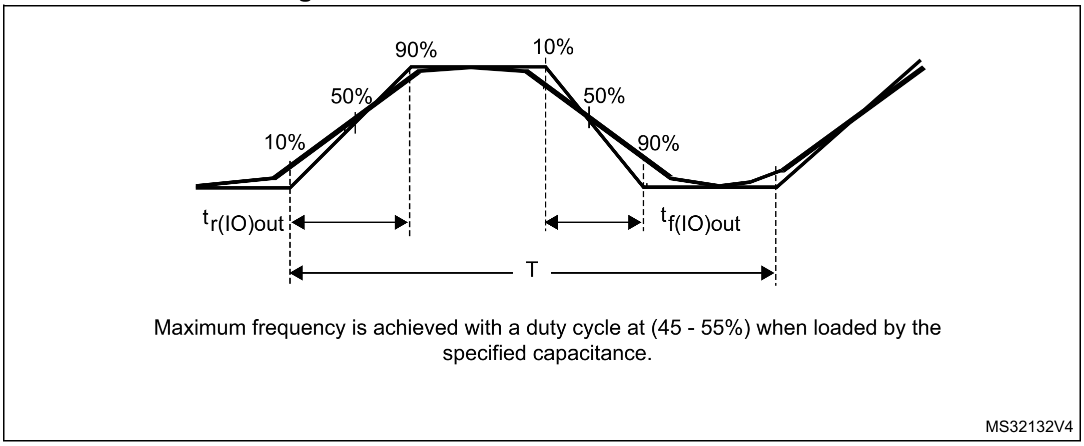
| Speed | Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|---|
| 0 | $f_{max}$ | Maximum frequency | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 2 | MHz |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 1 | |
| | $t_r/t_f$ | Output rise and fall time | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 170 | ns |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 330 | |

**Table 52. FT_c I/O output timing characteristics(1)(2) (continued)**

| Speed | Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|---|
| 1 | $f_{max}$ | Maximum frequency | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 10 | MHz |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 5 | |
| | $t_r/t_f$ | Output rise and fall time | C=50 pF, 2.7 V ≤ $V_{DDIO1}$ ≤ 3.6 V | - | 35 | ns |
| | | | C=50 pF, 1.6 V ≤ $V_{DDIO1}$ ≤ 2.7 V | - | 65 | |

1. The I/O speed is configured using the OSPEEDRy[0] bit. Refer to the reference manual RM0444 for description of the GPIO port configuration.
2. Specified by design. Not tested in production.

**Figure 17. I/O AC characteristics definition**




## 5.3.15 NRST input characteristics

The NRST input driver uses CMOS technology. It is connected to a permanent pull-up resistor, $R_{PU}$.

Unless otherwise specified, the parameters given in the following table are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

**Table 53. NRST pin characteristics(1)**

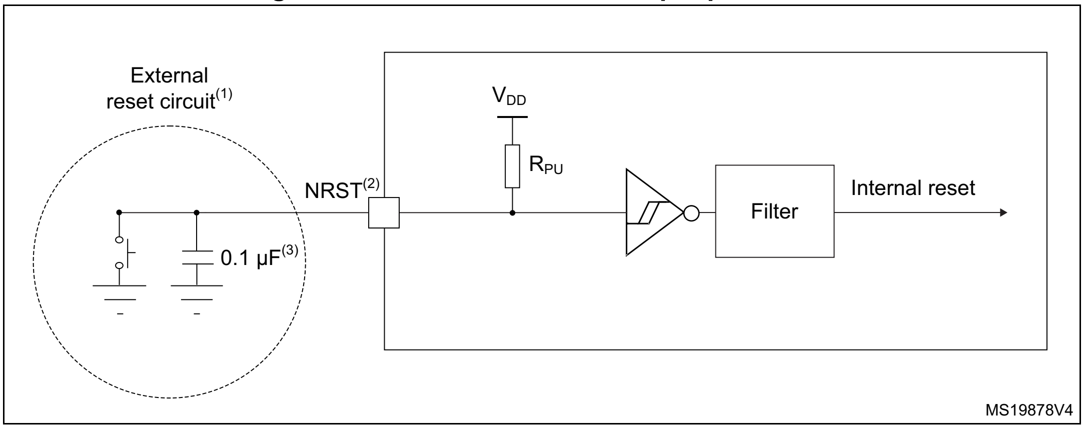
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{IL(NRST)}$ | NRST input low level voltage | - | - | - | 0.3 x $V_{DDIO1}$ | V |
| $V_{IH(NRST)}$ | NRST input high level voltage | - | 0.7 x $V_{DDIO1}$ | - | - | V |
| $V_{hys(NRST)}$ | NRST Schmitt trigger voltage hysteresis | - | - | 200 | - | mV |
| $R_{PU}$ | Weak pull-up equivalent resistor(2) | $V_{IN} = V_{SS}$ | 25 | 40 | 55 | kΩ |

**Table 53. NRST pin characteristics[1] (continued)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{F(NRST)}$ | NRST input filtered pulse | - | - | - | 70 | ns |
| $V_{NF(NRST)}$ | NRST input not filtered pulse | $2.0\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ | 350 | - | - | ns |

1. Specified by design. Not tested in production.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

**Figure 18. Recommended NRST pin protection**




1. The reset network protects the device against parasitic resets.
2. The user must ensure that, upon power-on, the level on the NRST pin can exceed the minimum $V_{IH(NRST)}$ level. Otherwise, the device does not exit the power-on reset.
3. The external capacitor on NRST must be placed as close as possible to the device.

## 5.3.16 Extended interrupt and event controller input (EXTI) characteristics

The pulse on the interrupt input must equal or exceed the minimum length, to guarantee that it is detected by the event controller.

**Table 54. EXTI input characteristics[1]**

| Symbol | Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| PLEC | Pulse length to event controller | | - | - | ns |

1. Specified by design. Not tested in production.

## 5.3.17 Analog switch booster

**Table 55. Analog switch booster characteristics[1]**

| Symbol | Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| $V_{DD}$ | Supply voltage | $V_{DD}$(min) | - | 3.6 | V |
| $t_{SU(BOOST)}$ | Booster startup time | - | - | 240 | μs |

**Table 55. Analog switch booster characteristics(1) (continued)**

| Symbol | Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| $I_{DD(BOOST)}$ | Booster consumption for $V_{DD} \leq 2.7$ V | - | - | 500 | µA |
| | Booster consumption for $2.7 \text{ V} \leq V_{DD} \leq 3.6$ V | - | - | 900 | |

1. Specified by design. Not tested in production.

## 5.3.18 Analog-to-digital converter characteristics

Unless otherwise specified, the parameters given in *Table 56* are preliminary values derived from tests performed under ambient temperature, $f_{PCLK}$ frequency and $V_{DDA}$ supply voltage conditions summarized in *Table 21: General operating conditions*.

*Note: It is recommended to perform a calibration after each power-up.*

**Table 56. ADC characteristics(1)**

| Symbol | Parameter | Conditions(2) | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DDA}$ | Analog supply voltage | - | 2.0 | - | 3.6 | V |
| $V_{REF+}$ | Positive reference voltage | - | 2 | - | $V_{DDA}$ | V |
| $f_{ADC}$ | ADC clock frequency | Range 1 | 0.14 | - | 35 | MHz |
| | | Range 2 | 0.14 | - | 16 | |
| $D_{ADC}$(3) | ADC analog clock duty cycle | - | 45 | - | 55 | % |
| $f_s$ | Sampling rate | 12 bits | - | - | 2.50 | MSps |
| | | 10 bits | - | - | 2.92 | |
| | | 8 bits | - | - | 3.50 | |
| | | 6 bits | - | - | 4.38 | |
| $f_{TRIG}$ | External trigger frequency | $f_{ADC}$ = 35 MHz; 12 bits | - | - | 2.33 | MHz |
| | | 12 bits | - | - | $f_{ADC}/15$ | |
| $V_{AIN}$ (4) | Conversion voltage range | - | $V_{SSA}$ | - | $V_{REF+}$ | V |
| $R_{AIN}$ | External input impedance | - | - | - | 50 | kΩ |
| $C_{ADC}$ | Internal sample and hold capacitor | - | - | 5 | - | pF |
| $t_{STAB}$ | ADC power-up time | - | | 2 | | Conversion cycle |
| $t_{CAL}$ | Calibration time | $f_{ADC}$ = 35 MHz | | 2.35 | | µs |
| | | - | | 82 | | $1/f_{ADC}$ |

**Table 56. ADC characteristics(1) (continued)**

| Symbol | Parameter | Conditions(2) | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $W_{LATENCY}$ | ADC_DR register write latency | CKMODE[1:0] = 00 | 1.5 $f_{ADC}$ + 2 $f_{PCLK}$ cycles | - | 1.5 $f_{ADC}$ + 3 $f_{PCLK}$ cycles | - |
| | | CKMODE[1:0] = 01 | - | 4.5 | - | $1/f_{PCLK}$ |
| | | CKMODE[1:0] = 10 | - | 8.5 | - | |
| | | CKMODE[1:0] = 11 | - | 2.5 | - | |
| $t_{LATR}$ | Trigger conversion latency | CKMODE[1:0] = 00 | 2 | - | 3 | $1/f_{ADC}$ |
| | | CKMODE[1:0] = 01 | 6.5 | | | $1/f_{PCLK}$ |
| | | CKMODE[1:0] = 10 | 12.5 | | | |
| | | CKMODE[1:0] = 11 | 3.5 | | | |
| $t_s$ | Sampling time | $f_{ADC}$ = 35 MHz | 0.043 | - | 4.59 | µs |
| | | | 1.5 | - | 160.5 | $1/f_{ADC}$ |
| $t_{ADCVREG\_STUP}$ | ADC voltage regulator start-up time | - | - | - | 20 | µs |
| $t_{CONV}$ | Total conversion time (including sampling time) | $f_{ADC}$ = 35 MHz Resolution = 12 bits | 0.40 | - | 4.95 | µs |
| | | Resolution = 12 bits | $t_s$ + 12.5 cycles for successive approximation = 14 to 173 | | | $1/f_{ADC}$ |
| $t_{IDLE}$ | Laps of time allowed between two conversions without rearm | - | - | - | 100 | µs |
| $I_{DDA(ADC)}$ | ADC consumption from $V_{DDA}$ | $f_s$ = 2.5 MSps | - | 410 | - | µA |
| | | $f_s$ = 1 MSps | - | 164 | - | |
| | | $f_s$ = 10 kSps | - | 17 | - | |
| $I_{DDV(ADC)}$ | ADC consumption from $V_{REF+}$ | $f_s$ = 2.5 MSps | - | 65 | - | µA |
| | | $f_s$ = 1 MSps | - | 26 | - | |
| | | $f_s$ = 10 kSps | - | 0.26 | - | |

1. Specified by design. Not tested in production.
2. I/O analog switch voltage booster must be enabled (BOOSTEN = 1 in the SYSCFG_CFGR1) when $V_{DDA}$ < 2.4 V and disabled when $V_{DDA} \geq$ 2.4 V.
3. This requirement is granted when the incoming clock (PCLK or ADC asynchronous clock) is divided by two or more in the ADC. For other cases, refer to the reference manual section *ADC clock* for information on how to fulfill this requirement.
4. $V_{REF+}$ is internally connected to $V_{DDA}$ on some packages.Refer to *Section 4: Pinouts, pin description and alternate functions* for further details.

**Table 57. Maximum ADC $R_{AIN}$**

| Resolution | Sampling cycle at 35 MHz | Sampling time at 35 MHz [ns] | Max. $R_{AIN}$ (1)(2) (Ω) |
|---|---|---|---|
| 12 bits | 1.5 | 43 | 50 |
| | 3.5 | 100 | 680 |
| | 7.5 | 214 | 2200 |
| | 12.5 | 357 | 4700 |
| | 19.5 | 557 | 8200 |
| | 39.5 | 1129 | 15000 |
| | 79.5 | 2271 | 33000 |
| | 160.5 | 4586 | 50000 |
| 10 bits | 1.5 | 43 | 68 |
| | 3.5 | 100 | 820 |
| | 7.5 | 214 | 3300 |
| | 12.5 | 357 | 5600 |
| | 19.5 | 557 | 10000 |
| | 39.5 | 1129 | 22000 |
| | 79.5 | 2271 | 39000 |
| | 160.5 | 4586 | 50000 |
| 8 bits | 1.5 | 43 | 82 |
| | 3.5 | 100 | 1500 |
| | 7.5 | 214 | 3900 |
| | 12.5 | 357 | 6800 |
| | 19.5 | 557 | 12000 |
| | 39.5 | 1129 | 27000 |
| | 79.5 | 2271 | 50000 |
| | 160.5 | 4586 | 50000 |
| 6 bits | 1.5 | 43 | 390 |
| | 3.5 | 100 | 2200 |
| | 7.5 | 214 | 5600 |
| | 12.5 | 357 | 10000 |
| | 19.5 | 557 | 15000 |
| | 39.5 | 1129 | 33000 |
| | 79.5 | 2271 | 50000 |
| | 160.5 | 4586 | 50000 |

1. Specified by design. Not tested in production.
2. I/O analog switch voltage booster must be enabled (BOOSTEN = 1 in the SYSCFG_CFGR1) when $V_{DDA}$ < 2.4 V and disabled when $V_{DDA}$ ≥ 2.4 V.

**Table 58. ADC accuracy(1)(2)(3)**

| Symbol | Parameter | Conditions(4) | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| ET | Total unadjusted error | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | 3 | 6.5 | LSB |
| EO | Offset error | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | 1.5 | 4.5 | LSB |
| EG | Gain error | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | 3 | 5 | LSB |
| ED | Differential linearity error | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | 1.2 | 1.5 | LSB |
| EL | Integral linearity error | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | 2.5 | 3 | LSB |
| ENOB | Effective number of bits | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | 9.6 | 10.2 | - | bit |
| SINAD | Signal-to-noise and distortion ratio | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | 59.5 | 63 | - | dB |
| SNR | Signal-to-noise ratio | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | 60 | 64 | - | dB |
| THD | Total harmonic distortion | $V_{DDA}$=$V_{REF+}$ < 3.6 V; $f_{ADC}$ = 35 MHz; $f_s$ ≤ 2.5 MSps; $T_A$ = entire range | - | -74 | -70 | dB |

1. Based on characterization results, not tested in production.
2. ADC DC accuracy values are measured after internal calibration.
3. Injecting negative current on any analog input pin significantly reduces the accuracy of A-to-D conversion of signal on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins susceptible to receive negative current.
4. I/O analog switch voltage booster enabled (BOOSTEN = 1 in the SYSCFG_CFGR1) when $V_{DDA}$ < 2.4 V and disabled when $V_{DDA}$ ≥ 2.4 V.

**Figure 19. ADC accuracy characteristics**

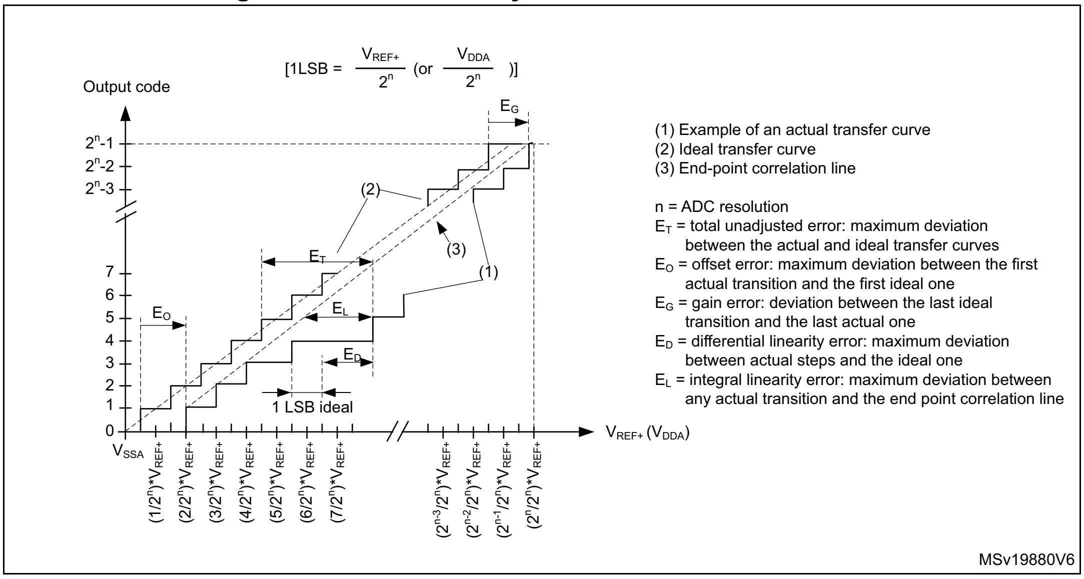
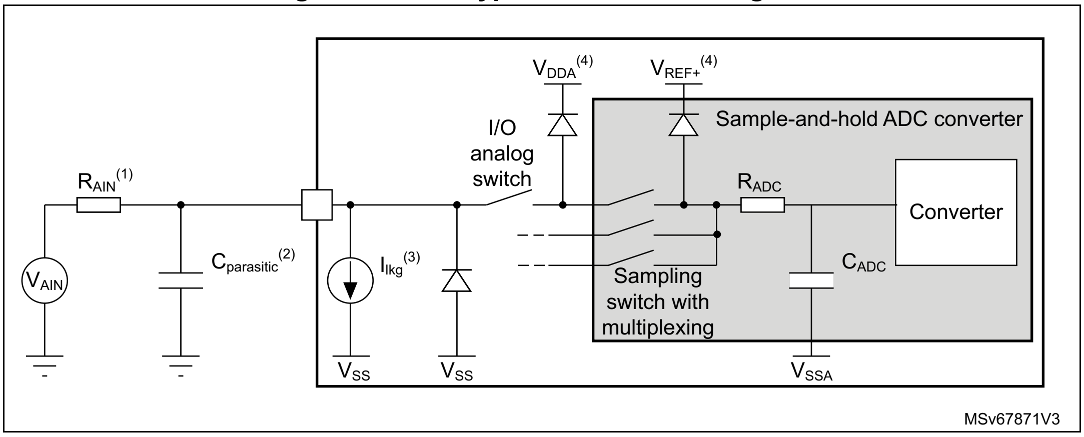



**Figure 20. ADC typical connection diagram**




1. Refer to *Table 56: ADC characteristics* for the values of $R_{AIN}$ and $C_{ADC}$.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 48: I/O static characteristics* for the value of the pad capacitance). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, $f_{ADC}$ should be reduced.
3. Refer to *Table 48: I/O static characteristics* for the values of $I_{lkg}$.
4. Refer to *Figure 8: Power supply scheme*.

## General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 8: Power supply scheme*. The 100 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

### 5.3.19 Temperature sensor characteristics

**Table 59. TS characteristics**

| Symbol | Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| $T_L$(1) | $V_{TS}$ linearity with temperature | - | ±1 | ±2 | °C |
| Avg_Slope(2) | Average slope | 2.3 | 2.5 | 2.7 | mV/°C |
| $V_{30}$ | Voltage at 30°C (±5 °C)(3) | 0.742 | 0.76 | 0.785 | V |
| $t_{START(TS\_BUF)}$(1) | Sensor Buffer Start-up time in continuous mode(4) | - | 8 | 15 | µs |
| $t_{START}$(1) | Start-up time when entering in continuous mode(4) | - | 70 | 120 | µs |
| $t_{S\_temp}$(1) | ADC sampling time when reading the temperature | 5 | - | - | µs |
| $I_{DD(TS)}$(1) | Temperature sensor consumption from $V_{DD}$, when selected by ADC | - | 4.7 | 7 | µA |

1. Specified by design. Not tested in production.
2. Based on characterization results, not tested in production.
3. Measured at $V_{DDA}$ = 3.0 V ±10 mV. The $V_{30}$ ADC conversion result is stored in the TS_CAL1 byte.
4. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

### 5.3.20 $V_{BAT}$ monitoring characteristics

**Table 60. $V_{BAT}$ monitoring characteristics**

| Symbol | Parameter | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| R | Resistor bridge for $V_{BAT}$ | - | 39 | - | kΩ |
| Q | Ratio on $V_{BAT}$ measurement | - | 3 | - | - |
| Er(1) | Error on Q | -10 | - | 10 | % |
| $t_{S\_vbat}$(1) | ADC sampling time when reading the VBAT | 12 | - | - | µs |

1. Specified by design. Not tested in production.

**Table 61. $V_{BAT}$ charging characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{BC}$ | Battery charging resistor | VBRS = 0 | - | 5 | - | kΩ |
| | | VBRS = 1 | - | 1.5 | - | |

### 5.3.21 Timer characteristics

The parameters given in the following tables are specified by design and not tested in production. Refer to *Section 5.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

**Table 62. TIMx[1] characteristics**

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $t_{res(TIM)}$ | Timer resolution time | - | 1 | - | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK}$ = 64 MHz | 15.625 | - | ns |
| $f_{EXT}$ | Timer external clock frequency on CH1 to CH4 | - | 0 | $f_{TIMxCLK}/2$ | MHz |
| | | $f_{TIMxCLK}$ = 64 MHz | 0 | 40 | |
| $Res_{TIM}$ | Timer resolution | TIMx | - | 16 | bit |
| $t_{COUNTER}$ | 16-bit counter clock period | - | 1 | 65536 | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK}$ = 64 MHz | 0.015625 | 1024 | µs |
| $t_{MAX\_COUNT}$ | Maximum possible count with 32-bit counter | - | - | 65536 × 65536 | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK}$ = 64 MHz | - | 67.10 | s |

1. TIMx is used as a general term to refer to a timer (for example, TIM1).

**Table 63. IWDG min/max timeout period at 32 kHz LSI clock[1]**

| Prescaler divider | PR[2:0] bits | Min timeout RL[11:0]= 0x000 | Max timeout RL[11:0]= 0xFFF | Unit |
|---|---|---|---|---|
| /4 | 0 | 0.125 | 512 | ms |
| /8 | 1 | 0.250 | 1024 | |
| /16 | 2 | 0.500 | 2048 | |
| /32 | 3 | 1.0 | 4096 | |
| /64 | 4 | 2.0 | 8192 | |
| /128 | 5 | 4.0 | 16384 | |
| /256 | 6 or 7 | 8.0 | 32768 | |

1. The exact timings further depend on the phase of the APB interface clock versus the LSI clock, which causes an uncertainty of one RC period.

## 5.3.22 Characteristics of communication interfaces

### I$^2$C-bus interface characteristics

The I$^2$C-bus interface meets timing requirements of the I$^2$C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The timings are ensured by design as long as the I2C peripheral is properly configured (refer to the reference manual RM0444) and when the I2CCLK frequency is greater than the minimum shown in the following table.

**Table 64. Minimum I2CCLK frequency**

| Symbol | Parameter | Condition | | Typ | Unit |
|---|---|---|---|---|---|
| $f_{I2CCLK(min)}$ | Minimum I2CCLK frequency for correct operation of I2C peripheral | Standard-mode | | 2 | MHz |
| | | Fast-mode | Analog filter enabled | 9 | |
| | | | DNF = 0 | | |
| | | | Analog filter disabled | 9 | |
| | | | DNF = 1 | | |
| | | Fast-mode Plus | Analog filter enabled | 18 | |
| | | | DNF = 0 | | |
| | | | Analog filter disabled | 16 | |
| | | | DNF = 1 | | |

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and $V_{DDIO1}$ is disabled, but is still present. Only FT_f I/O pins support Fm+ low-level output current maximum requirement. Refer to *Section 5.3.14: I/O port characteristics* for the I2C I/Os characteristics.

All I2C SDA and SCL I/Os embed an analog filter. Refer to the following table for its characteristics:

**Table 65. I2C analog filter characteristics(1)**

| Symbol | Parameter | Min | Max | Unit |
|---|---|---|---|---|
| $t_{AF}$ | Limiting duration of spikes suppressed by the filter(2) | 50 | 260 | ns |

1. Based on characterization results, not tested in production.
2. Spikes shorter than the limiting duration are suppressed.

### SPI/I²S characteristics

Unless otherwise specified, the parameters given in *Table 66* for SPI are derived from tests performed under the ambient temperature, $f_{PCLKx}$ frequency and supply voltage conditions summarized in *Table 21: General operating conditions*. The additional general conditions are:

- OSPEEDRy[1:0] set to 11 (output speed)
- capacitive load C = 30 pF
- measurement points at CMOS levels: 0.5 x $V_{DD}$

Refer to *Section 5.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

**Table 66. SPI characteristics(1)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{SCK}$ $1/t_{c(SCK)}$ | SPI clock frequency | Master mode $V_{DD}(min) < V_{DD} < 3.6$ V Range 1 | - | - | 32 | MHz |
| | | Master transmitter $V_{DD}(min) < V_{DD} < 3.6$ V Range 1 | | | 32 | |
| | | Slave receiver $V_{DD}(min) < V_{DD} < 3.6$ V Range 1 | | | 32 | |
| | | Slave transmitter/full duplex $2.7 < V_{DD} < 3.6$ V Range 1 | | | 32 | |
| | | Slave transmitter/full duplex $V_{DD}(min) < V_{DD} < 3.6$ V Range 1 | | | 23 | |
| | | $V_{DD}(min) < V_{DD} < 3.6$ V Range 2 | | | 8 | |
| $t_{su(NSS)}$ | NSS setup time | Slave mode, SPI prescaler = 2 | $4 \times T_{PCLK}$ | - | - | ns |
| $t_{h(NSS)}$ | NSS hold time | Slave mode, SPI prescaler = 2 | $2 \times T_{PCLK}$ | - | - | ns |
| $t_{w(SCKH)}$ | SCK high time | Master mode | $T_{PCLK} - 1.5$ | $T_{PCLK}$ | $T_{PCLK} + 1.5$ | ns |
| $t_{w(SCKL)}$ | SCK low time | Master mode | $T_{PCLK} - 1.5$ | $T_{PCLK}$ | $T_{PCLK} + 1.5$ | ns |
| $t_{su(MI)}$ | Master data input setup time | - | 1 | - | - | ns |
| $t_{su(SI)}$ | Slave data input setup time | - | 1 | - | - | ns |
| $t_{h(MI)}$ | Master data input hold time | - | 5 | - | - | ns |
| $t_{h(SI)}$ | Slave data input hold time | - | 1 | - | - | ns |
| $t_{a(SO)}$ | Data output access time | Slave mode | 9 | - | 34 | ns |
| $t_{dis(SO)}$ | Data output disable time | Slave mode | 9 | - | 16 | ns |
| $t_{v(SO)}$ | Slave data output valid time | $2.7 < V_{DD} < 3.6$ V Range 1 | - | 9 | 14 | ns |
| | | $V_{DD}(min) < V_{DD} < 3.6$ V Range 1 | - | 9 | 21 | |
| | | $V_{DD}(min) < V_{DD} < 3.6$ V Voltage Range 2 | - | 11 | 24 | |
| $t_{v(MO)}$ | Master data output valid time | - | - | 3 | 5 | ns |

**Table 66. SPI characteristics[1] (continued)**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $t_{h(SO)}$ | Slave data output hold time | - | 5 | - | - | ns |
| $t_{h(MO)}$ | Master data output hold time | - | 1 | - | - | ns |

1. Based on characterization results, not tested in production.

**Figure 21. SPI timing diagram - slave mode and CPHA = 0**

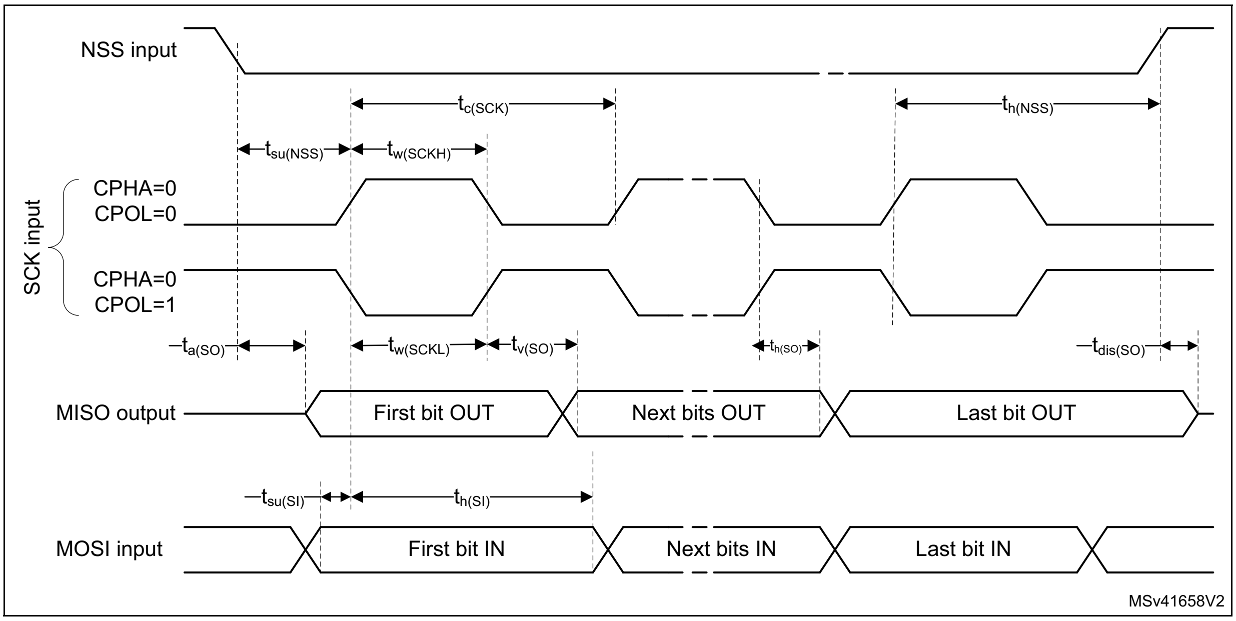



**Figure 22. SPI timing diagram - slave mode and CPHA = 1**

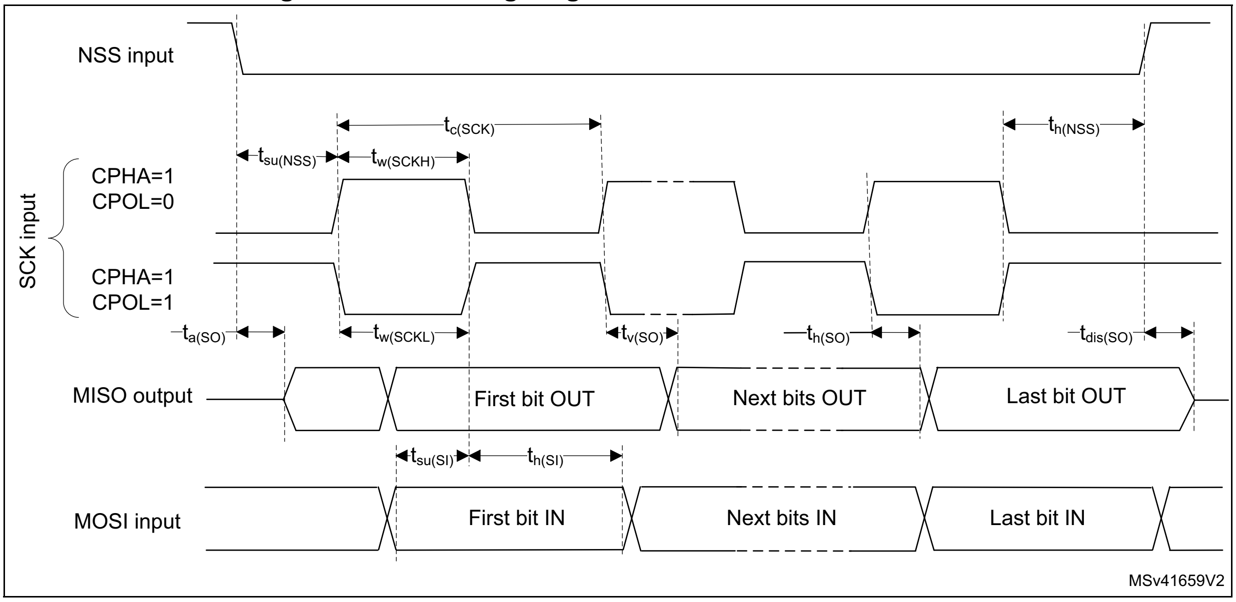


**Figure 23. SPI timing diagram - master mode**

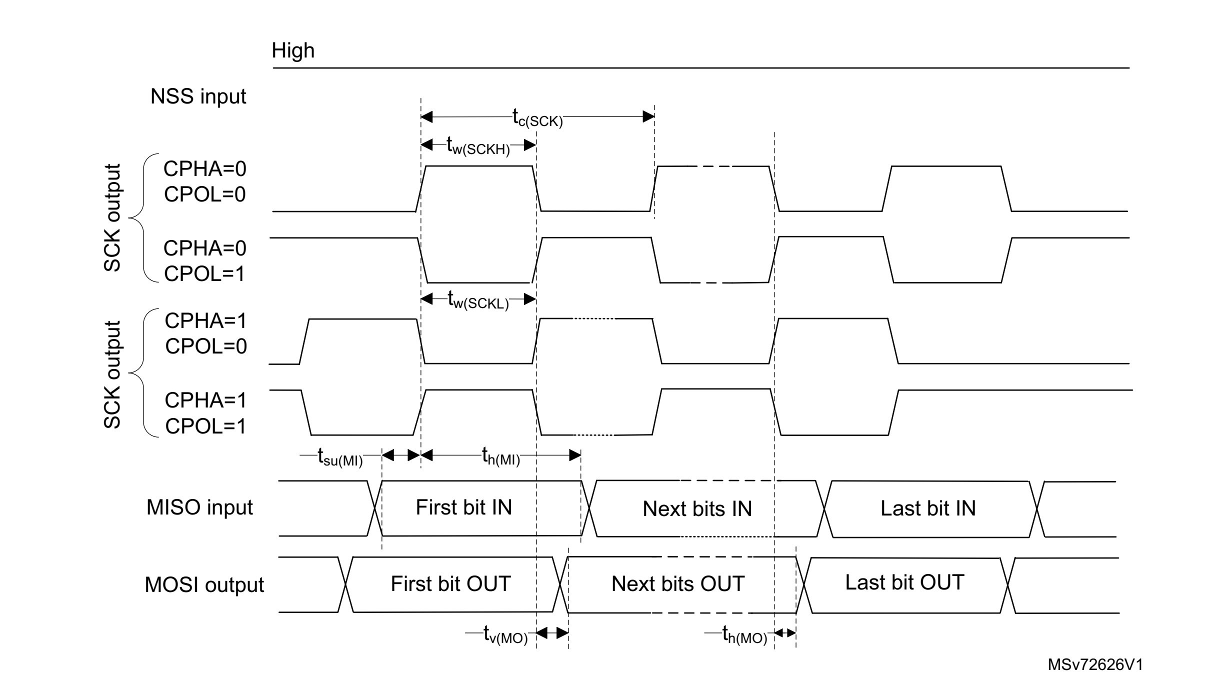



**Table 67. I2S characteristics(1)**

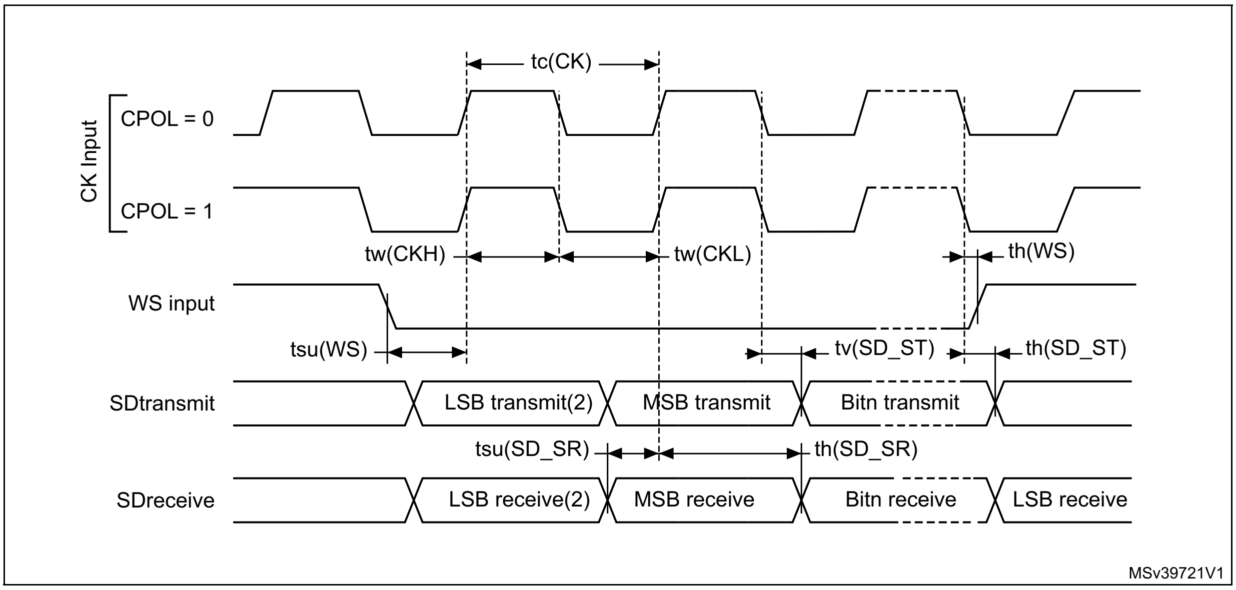
| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $f_{MCK}$ | I2S main clock output | $f_{MCK}$= 256 x Fs; (Fs = audio sampling frequency) $Fs_{min}$ = 8 kHz; $Fs_{max}$ = 192 kHz; | 2.048 | 49.152 | MHz |
| $f_{CK}$ | I2S clock frequency | Master data | - | 64xFs | MHz |
| | | Slave data | - | 64xFs | |
| $D_{CK}$ | I2S clock frequency duty cycle | Slave receiver | 30 | 70 | % |
| $t_{v(WS)}$ | WS valid time | Master mode | - | 8 | ns |
| $t_{h(WS)}$ | WS hold time | Master mode | 2 | - | ns |
| $t_{su(WS)}$ | WS setup time | Slave mode | 4 | - | ns |
| $t_{h(WS)}$ | WS hold time | Slave mode | 2 | - | ns |
| $t_{su(SD\_MR)}$ | Data input setup time | Master receiver | 4 | - | ns |
| $t_{su(SD\_SR)}$ | | Slave receiver | 5 | - | ns |
| $t_{h(SD\_MR)}$ | Data input hold time | Master receiver | 4.5 | - | ns |
| $t_{h(SD\_SR)}$ | | Slave receiver | 2 | - | ns |
| $t_{v(SD\_ST)}$ | Data output valid time - slave transmitter | after enable edge; 2.7 < $V_{DD}$ < 3.6V | - | 16 | ns |
| | | after enable edge; $V_{DD}$(min) < $V_{DD}$ < 3.6V | | 23 | |

Table 67. $I^2S$ characteristics[(1)] (continued)

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $t_{v(SD\_MT)}$ | Data output valid time - master transmitter | after enable edge | - | 5.5 | ns |
| $t_{h(SD\_ST)}$ | Data output hold time - slave transmitter | after enable edge | 8 | - | ns |
| $t_{h(SD\_MT)}$ | Data output hold time - master transmitter | after enable edge | 1 | - | ns |

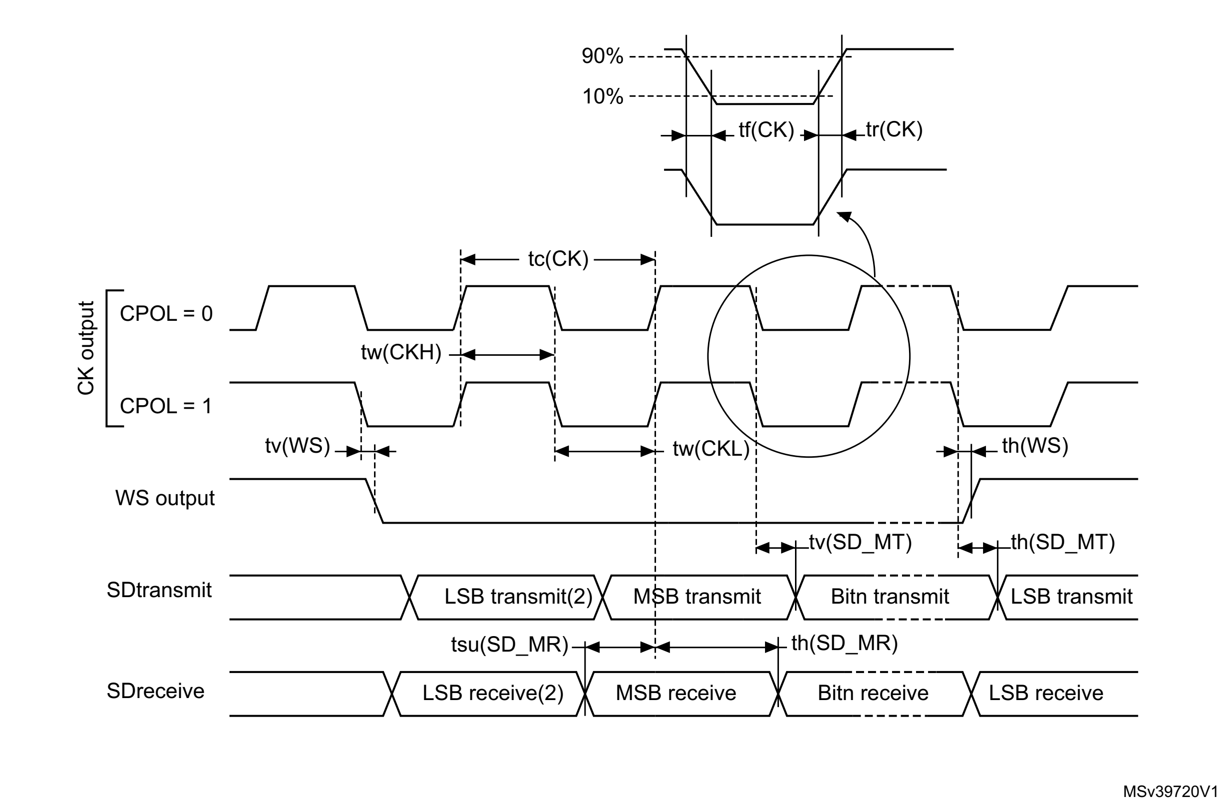
1. Based on characterization results, not tested in production.

Figure 24. $I^2S$ slave timing diagram (Philips protocol)




1. Measurement points are done at CMOS levels: 0.3 $V_{DDIO1}$ and 0.7 $V_{DDIO1}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

**Figure 25. I²S master timing diagram (Philips protocol)**




1. Based on characterization results, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

### USART (SPI mode) characteristics

Unless otherwise specified, the parameters given in Table 68 for USART are derived from tests performed under the ambient temperature, $f_{PCLKx}$ frequency and supply voltage conditions summarized in Table 21: General operating conditions. The additional general conditions are:

- OSPEEDRy[1:0] set to 10 (output speed)
- capacitive load C = 30 pF
- measurement points at CMOS levels: 0.5 x $V_{DD}$

Refer to Section 5.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, CK, TX, and RX for USART).

**Table 68. USART characteristics in SPI mode**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $f_{CK}$ | USART clock frequency | Master mode | - | - | 8 | MHz |
| | | Slave mode | - | - | 21 | |
| $t_{su(NSS)}$ | NSS setup time | Slave mode | $T_{ker}$(1) + 2 | - | - | ns |
| $t_{h(NSS)}$ | NSS hold time | Slave mode | 2 | - | - | ns |

**Table 68. USART characteristics in SPI mode**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $t_{w(CKH)}$ | CK high time | Master mode | $1 / f_{CK} / 2 - 1$ | $1 / f_{CK} / 2$ | $1 / f_{CK} / 2 + 1$ | ns |
| $t_{w(CKL)}$ | CK low time | | | | | ns |
| $t_{su(RX)}$ | Data input setup time | Master mode | $T_{ker}$(1) + 2 | - | - | ns |
| | | Slave mode | 4 | - | - | ns |
| $t_{h(RX)}$ | Data input hold time | Master mode | 1 | - | - | ns |
| | | Slave mode | 0.5 | - | - | ns |
| $t_{v(TX)}$ | Data output valid time | Master mode | - | 0.5 | 1 | ns |
| | | Slave mode | - | 10 | 19 | ns |
| $t_{h(TX)}$ | Data output hold time | Master mode | 0 | - | - | ns |
| | | Slave mode | 7 | - | - | ns |

1. $T_{ker}$ is the *usart_ker_ck_pres* clock period

**Figure 26. USART timing diagram in SPI master mode**

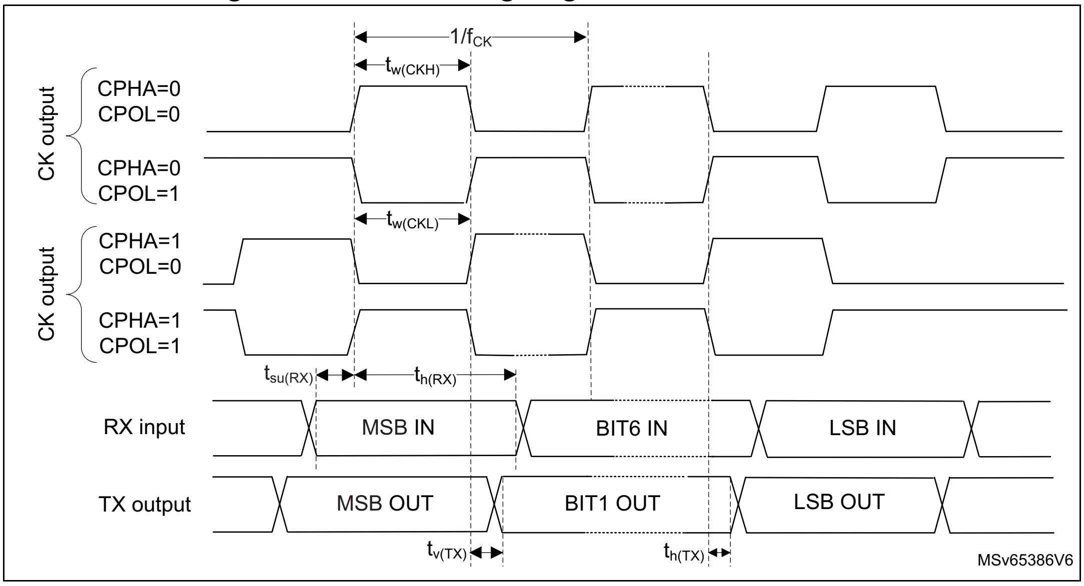
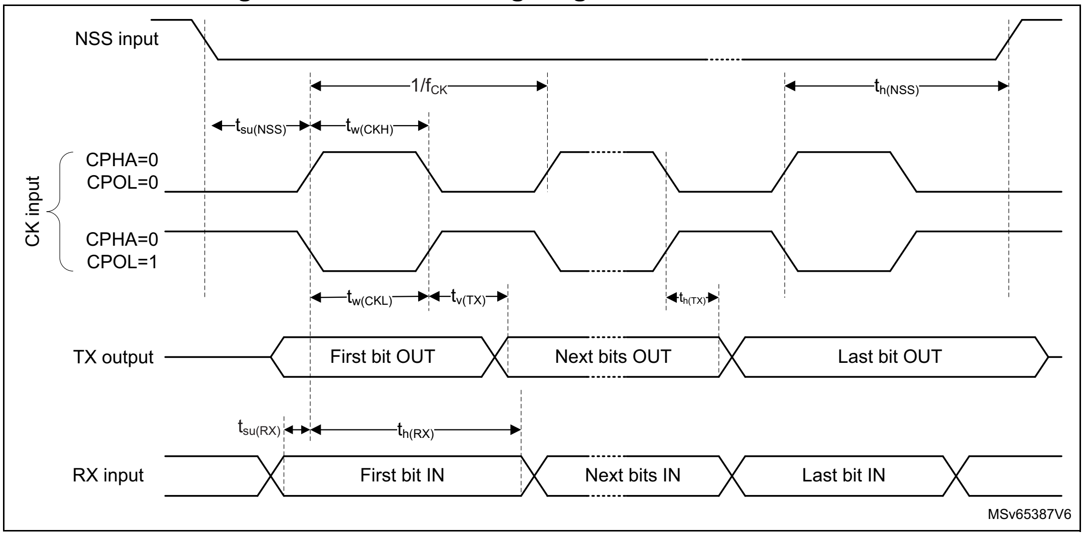


**Figure 27. USART timing diagram in SPI slave mode**



# 6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.

## 6.1 Device marking

Refer to technical note “Reference device marking schematics for STM32 microcontrollers and microprocessors” (TN1433) available on *www.st.com*, for the location of pin 1 / ball A1 as well as the location and orientation of the marking areas versus pin 1 / ball A1.

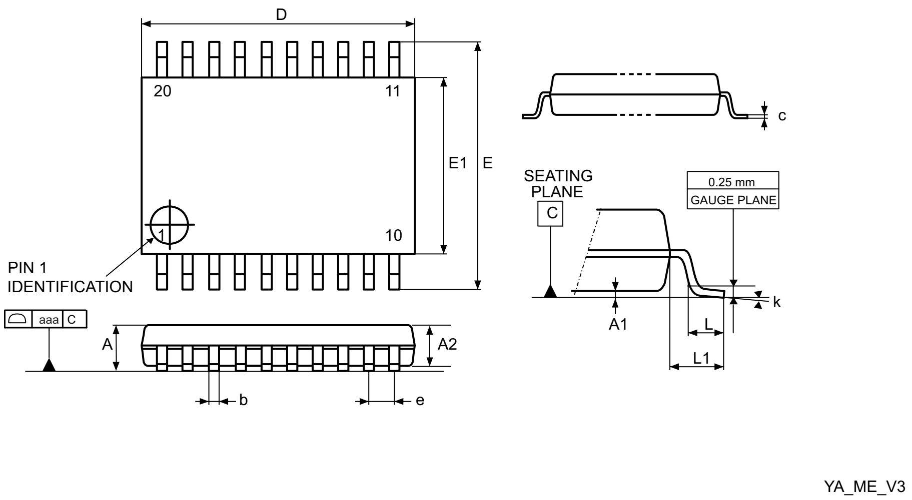
Parts marked as “ES”, “E” or accompanied by an engineering sample notification letter, are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST’s Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

A WLCSP simplified marking example (if any) is provided in the corresponding package information subsection.

## 6.2 TSSOP20 package information (YA)

TSSOP20 is a 20-lead, 6.5 x 4.4 mm thin small-outline package with 0.65 mm pitch.

**Figure 28. TSSOP20 – Outline**



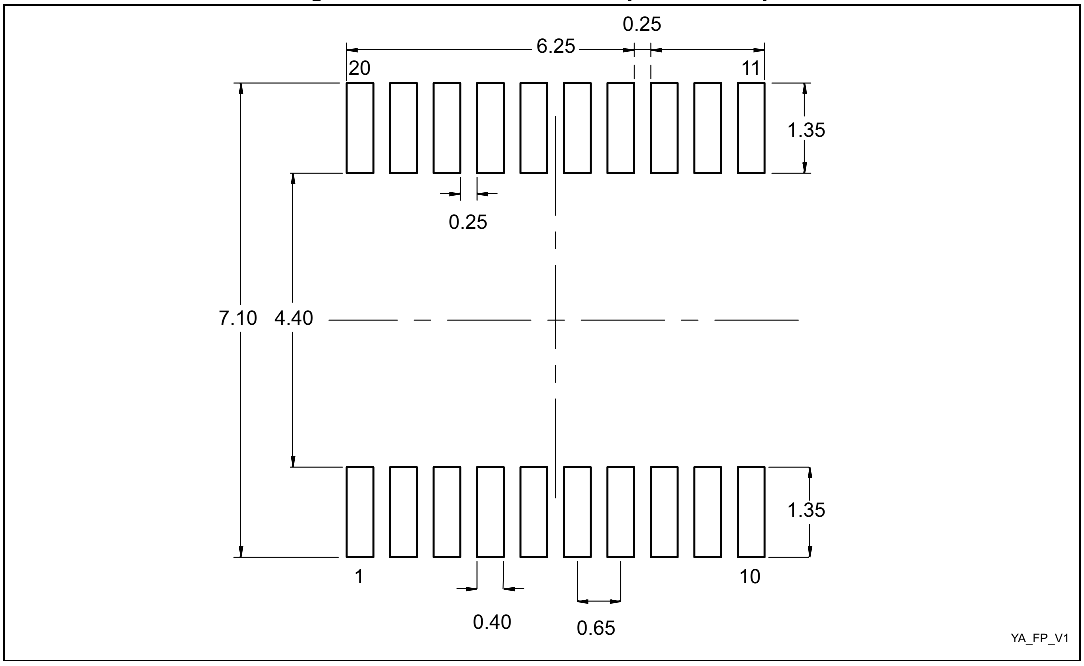

1. Drawing is not to scale.

**Table 69. TSSOP20 – Mechanical data**

| Symbol | millimeters | | | inches[1] | | |
|---|---|---|---|---|---|---|
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | - | - | 1.200 | - | - | 0.0472 |
| A1 | 0.050 | - | 0.150 | 0.0020 | - | 0.0059 |
| A2 | 0.800 | 1.000 | 1.050 | 0.0315 | 0.0394 | 0.0413 |
| b | 0.190 | - | 0.300 | 0.0075 | - | 0.0118 |
| c | 0.090 | - | 0.200 | 0.0035 | - | 0.0079 |
| D[2] | 6.400 | 6.500 | 6.600 | 0.2520 | 0.2559 | 0.2598 |
| E | 6.200 | 6.400 | 6.600 | 0.2441 | 0.2520 | 0.2598 |
| E1[3] | 4.300 | 4.400 | 4.500 | 0.1693 | 0.1732 | 0.1772 |
| e | - | 0.650 | - | - | 0.0256 | - |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | - | 1.000 | - | - | 0.0394 | - |
| k | 0° | - | 8° | 0° | - | 8° |
| aaa | - | - | 0.100 | - | - | 0.0039 |

1. Values in inches are converted from mm and rounded to four decimal digits.
2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per side.
3. Dimension "E1" does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25 mm per side.

**Figure 29. TSSOP20 – Footprint example**




1. Dimensions are expressed in millimeters.

## 6.3 LQFP32 package information (5V)

This LQFP is a 32-pin, 7 x 7 mm, low-profile quad flat package.

*Note:* *Figure 30 is not to scale.*

*Refer to the notes section for the list of notes on Figure 30 and Table 70.*

**Figure 30. LQFP32 - Outline**

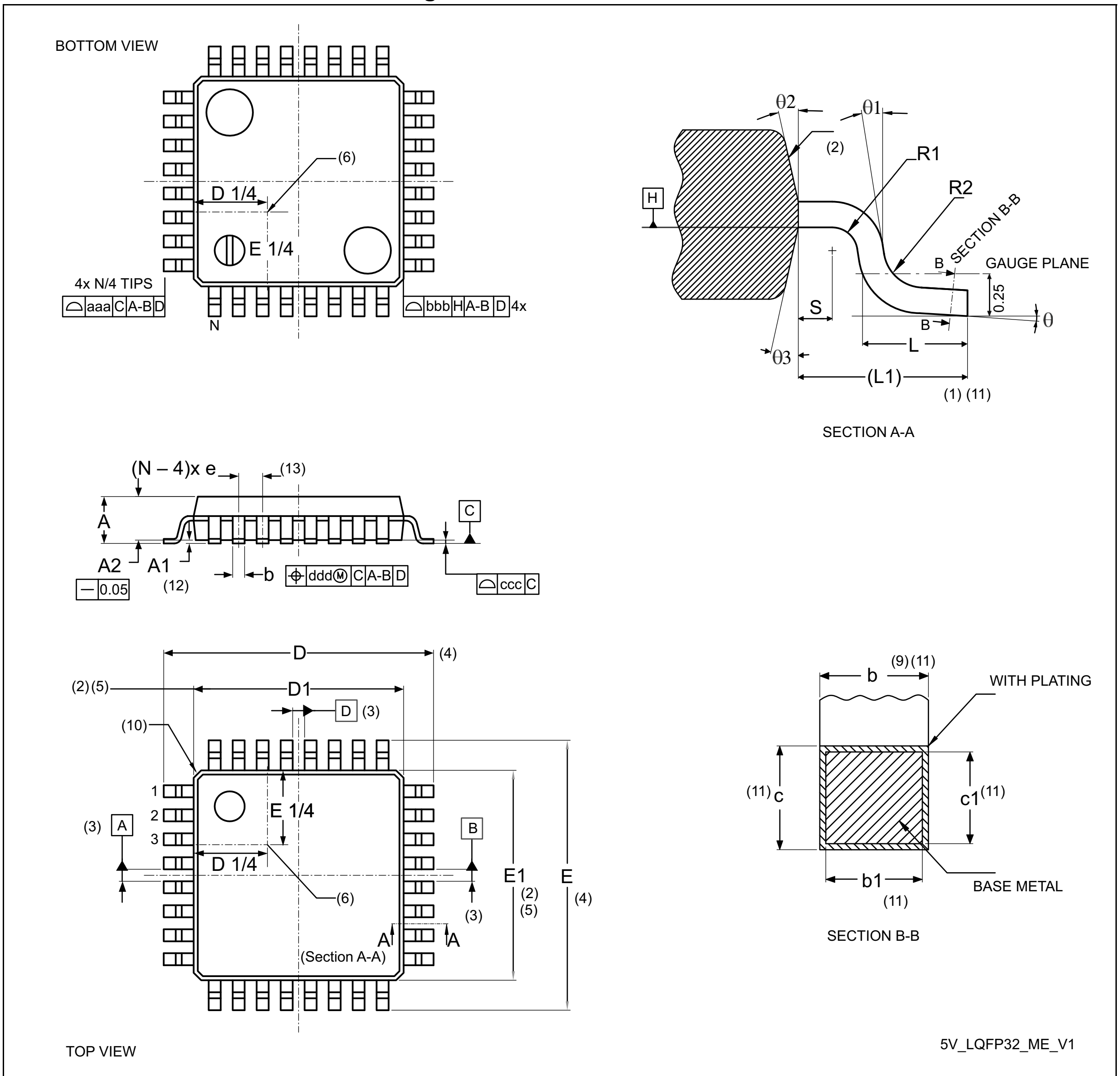


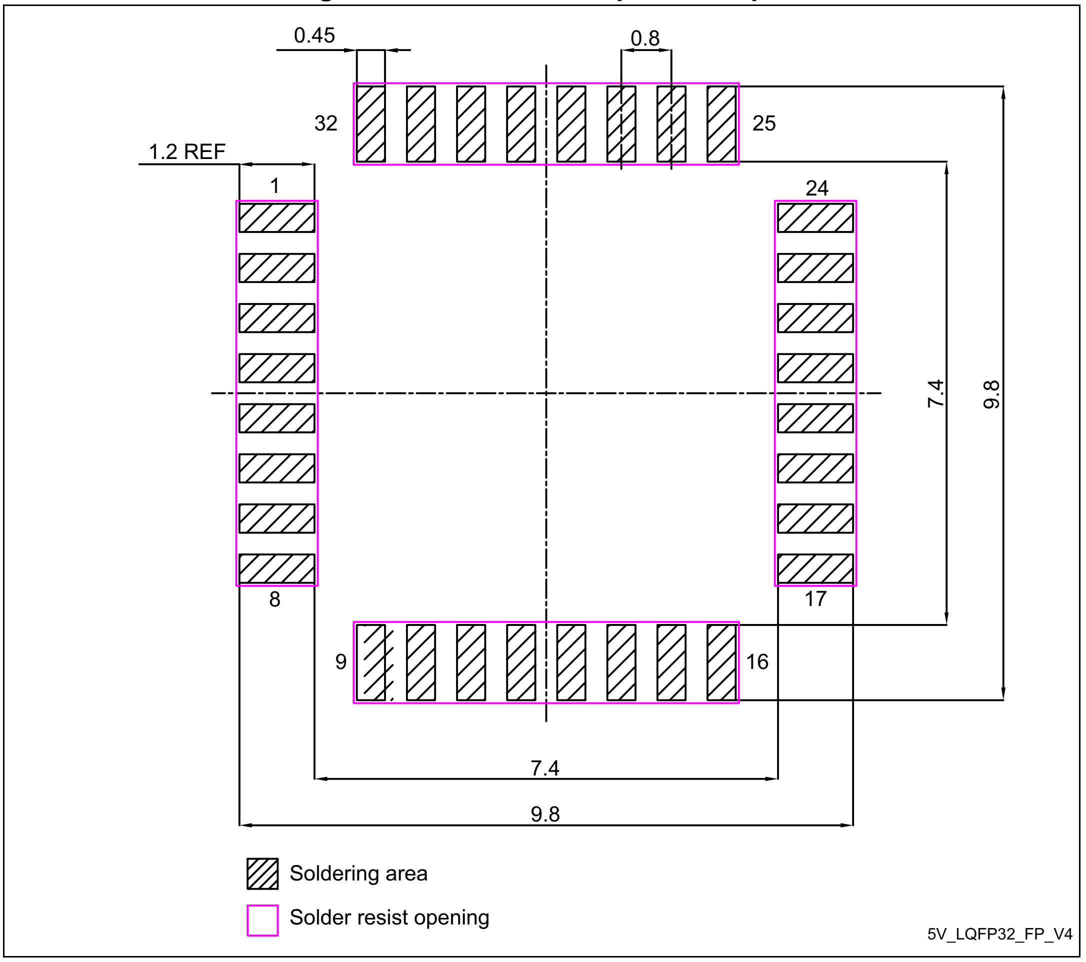
Table 70. LQFP32 - Mechanical data

| Symbol | millimeters | | | inches[14] | | |
|---|---|---|---|---|---|---|
| | Min | Typ | Max | Min | Typ | Max |
| θ | 0° | 3.5° | 7° | 0° | 3.5° | 7° |
| θ1 | 0° | - | - | 0° | - | - |
| θ2 | 10° | 12° | 14° | 10° | 12° | 14° |
| θ3 | 10° | 12° | 14° | 10° | 12° | 14° |
| A | - | - | 1.60 | - | - | 0.0630 |
| A1[12] | 0.05 | - | 0.15 | 0.0020 | - | 0.0059 |
| A2 | 1.35 | 1.40 | 1.45 | 0.0531 | 0.0551 | 0.0571 |
| b[9][11] | 0.30 | 0.37 | 0.45 | 0.0118 | 0.0146 | 0.0177 |
| b1[11] | 0.30 | 0.35 | 0.40 | 0.0118 | 0.0128 | 0.0157 |
| c[11] | 0.09 | - | 0.20 | 0.0035 | - | 0.0079 |
| c1[11] | 0.09 | - | 0.16 | 0.0035 | - | 0.0063 |
| D[4] | 9.00 BSC | | | 0.3543 BSC | | |
| D1[2][5] | 7.00 BSC | | | 0.2756 BSC | | |
| e | 0.80 BSC | | | 0.0315 BSC | | |
| E[4] | 9.00 BSC | | | 0.3543 BSC | | |
| E1[2][5] | 7.00 BSC | | | 0.2756 BSC | | |
| L | 0.45 | 0.60 | 0.75 | 0.0177 | 0.0236 | 0.0295 |
| L1 | 1.00 REF | | | 0.0394 REF | | |
| N[13] | 32 | | | | | |
| R1 | 0.08 | - | - | 0.0031 | - | - |
| R2 | 0.08 | - | 0.20 | 0.0031 | - | 0.0079 |
| S | 0.20 | - | - | 0.0079 | - | - |
| aaa[1][7][15] | 0.20 | | | 0.0079 | | |
| bbb[1][7][15] | 0.20 | | | 0.0079 | | |
| ccc[1][7][15] | 0.10 | | | 0.0039 | | |
| ddd[1][7][15] | 0.20 | | | 0.0079 | | |

### Notes:

1. Dimensioning and tolerancing schemes conform to ASME Y14.5M-1994.
2. The top package body size may be smaller than the bottom package size by as much as 0.15 mm.
3. Datums A-B and D to be determined at datum plane H.
4. To be determined at the seating datum plane C.
5. Dimensions D1 and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is “0.25 mm” per side. D1 and E1 are maximum plastic body size dimensions including mold mismatch.
6. Details of pin 1 identifier are optional but must be located within the zone indicated.
7. All dimensions are in millimeters.
8. No intrusion is allowed inwards the leads.
9. Dimension b does not include a dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum “b” dimension by more than 0.08 mm. Dambar cannot be located on the lower radius or the foot. The minimum space between the protrusion and an adjacent lead is 0.07 mm for 0.4 mm and 0.5 mm pitch packages.
10. The exact shape of each corner is optional.
11. These dimensions apply to the flat section of the lead between 0.10 mm and 0.25 mm from the lead tip.
12. A1 is defined as the distance from the seating plane to the lowest point on the package body.
13. N is the number of terminal positions for the specified body size.
14. Values in inches are converted from mm and rounded to four decimal digits.
15. Recommended values and tolerances.

**Figure 31. LQFP32 – Footprint example**




1. Dimensions are expressed in millimeters.

## 6.4 LQFP48 package information (5B)

This LQFP is a 48-pin, 7 x 7 mm low-profile quad flat package.

*Note: See list of notes in the notes section.*

**Figure 32. LQFP48 - Outline(15)**

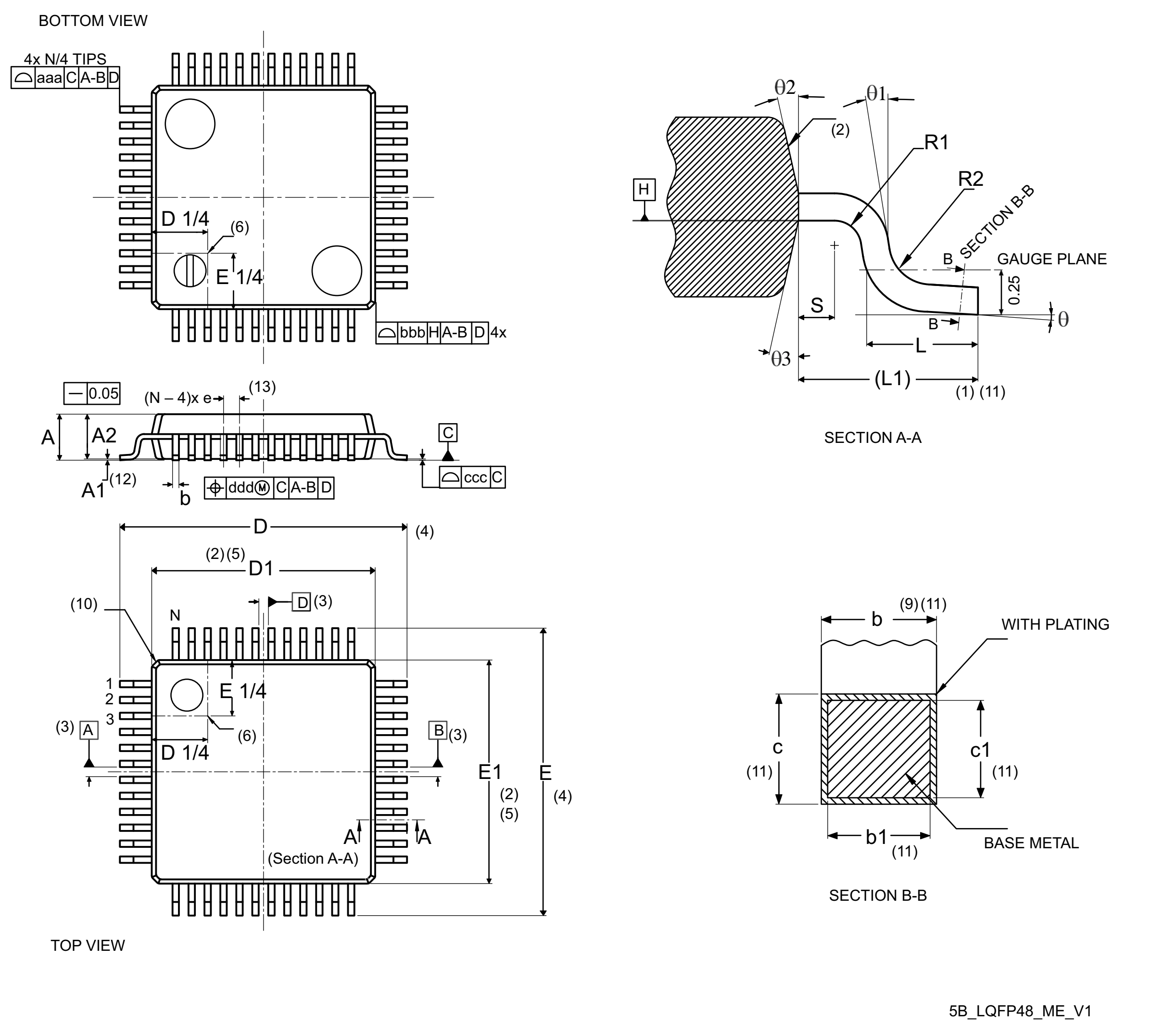


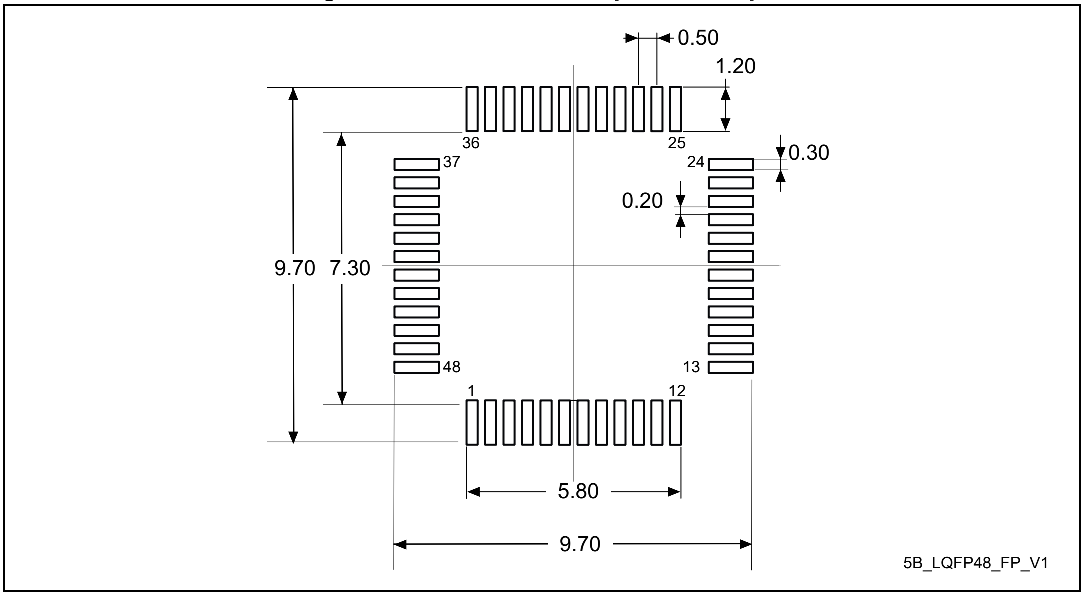
**Table 71. LQFP48 - Mechanical data**

| Symbol | millimeters | | | inches[14] | | |
|---|---|---|---|---|---|---|
| | Min | Typ | Max | Min | Typ | Max |
| A | - | - | 1.60 | - | - | 0.0630 |
| A1[12] | 0.05 | - | 0.15 | 0.0020 | - | 0.0059 |
| A2 | 1.35 | 1.40 | 1.45 | 0.0531 | 0.0551 | 0.0571 |
| b[9][11] | 0.17 | 0.22 | 0.27 | 0.0067 | 0.0087 | 0.0106 |
| b1[11] | 0.17 | 0.20 | 0.23 | 0.0067 | 0.0079 | 0.0090 |
| c[11] | 0.09 | - | 0.20 | 0.0035 | - | 0.0079 |
| c1[11] | 0.09 | - | 0.16 | 0.0035 | - | 0.0063 |
| D[4] | 9.00 BSC | | | 0.3543 BSC | | |
| D1[2][5] | 7.00 BSC | | | 0.2756 BSC | | |
| E[4] | 9.00 BSC | | | 0.3543 BSC | | |
| E1[2][5] | 7.00 BSC | | | 0.2756 BSC | | |
| e | 0.50 BSC | | | 0.1970 BSC | | |
| L | 0.45 | 0.60 | 0.75 | 0.0177 | 0.0236 | 0.0295 |
| L1 | 1.00 REF | | | 0.0394 REF | | |
| N[13] | 48 | | | | | |
| $\theta$ | 0° | 3.5° | 7° | 0° | 3.5° | 7° |
| $\theta 1$ | 0° | - | - | 0° | - | - |
| $\theta 2$ | 10° | 12° | 14° | 10° | 12° | 14° |
| $\theta 3$ | 10° | 12° | 14° | 10° | 12° | 14° |
| R1 | 0.08 | - | - | 0.0031 | - | - |
| R2 | 0.08 | - | 0.20 | 0.0031 | - | 0.0079 |
| S | 0.20 | - | - | 0.0079 | - | - |
| aaa[1][7] | 0.20 | | | 0.0079 | | |
| bbb[1][7] | 0.20 | | | 0.0079 | | |
| ccc[1][7] | 0.08 | | | 0.0031 | | |
| ddd[1][7] | 0.08 | | | 0.0031 | | |

## Notes:

1. Dimensioning and tolerancing schemes conform to ASME Y14.5M-1994.
2. The Top package body size may be smaller than the bottom package size by as much as 0.15 mm.
3. Datums A-B and D to be determined at datum plane H.
4. To be determined at seating datum plane C.
5. Dimensions D1 and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is “0.25 mm” per side. D1 and E1 are Maximum plastic body size dimensions including mold mismatch.
6. Details of pin 1 identifier are optional but must be located within the zone indicated.
7. All Dimensions are in millimeters.
8. No intrusion allowed inwards the leads.
9. Dimension “b” does not include dambar protrusion. Allowable dambar protrusion shall not cause the lead width to exceed the maximum “b” dimension by more than 0.08 mm. Dambar cannot be located on the lower radius or the foot. Minimum space between protrusion and an adjacent lead is 0.07 mm for 0.4 mm and 0.5 mm pitch packages.
10. Exact shape of each corner is optional.
11. These dimensions apply to the flat section of the lead between 0.10 mm and 0.25 mm from the lead tip.
12. A1 is defined as the distance from the seating plane to the lowest point on the package body.
13. “N” is the number of terminal positions for the specified body size.
14. Values in inches are converted from mm and rounded to 4 decimal digits.
15. Drawing is not to scale.

**Figure 33. LQFP48 - Footprint example**




1. Dimensions are expressed in millimeters.

## 6.5 Thermal characteristics

The operating junction temperature $T_J$ must never exceed the maximum given in *Table 21: General operating conditions*.

The maximum junction temperature in °C that the device can reach if respecting the operating conditions, is:

$$T_J(max) = T_A(max) + P_D(max) \times \Theta_{JA}$$

where:

- $T_A(max)$ is the maximum operating ambient temperature in °C,
- $\Theta_{JA}$ is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D = P_{INT} + P_{I/O}$,
  - $P_{INT}$ is power dissipation contribution from product of $I_{DD}$ and $V_{DD}$
  - $P_{I/O}$ is power dissipation contribution from output ports where:
    $P_{I/O} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIO1} - V_{OH}) \times I_{OH})$,
    taking into account the actual $V_{OL}$ / $I_{OL}$ and $V_{OH}$ / $I_{OH}$ of the I/Os at low and high level in the application.

**Table 72. Package thermal characteristics**

| Symbol | Parameter | Package | Value | Unit |
|---|---|---|---|---|
| $\Theta_{JA}$ | Thermal resistance junction-ambient | TSSOP20 6.4 × 4.4 mm | 80 | °C/W |
| | | LQFP32 7 × 7 mm | 65 | |
| | | LQFP48 7 × 7 mm | 65 | |
| $\Theta_{JB}$ | Thermal resistance junction-board | TSSOP20 6.4 × 4.4 mm | 19 | °C/W |
| | | LQFP32 7 × 7 mm | 33 | |
| | | LQFP48 7 × 7 mm | 33 | |
| $\Theta_{JC}$ | Thermal resistance junction-case | TSSOP20 6.4 × 4.4 mm | 49 | °C/W |
| | | LQFP32 7 × 7 mm | 17 | |
| | | LQFP48 7 × 7 mm | 17 | |

### 6.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (still air). Available from www.jedec.org.

# 7 Ordering information

Example STM32 G 050 C 8 T 6 xyy

**Device family**

STM32 = Arm® based 32-bit microcontroller

**Product type**

G = general-purpose

**Device subfamily**

050 = STM32G050

**Pin count**

F = 20

K = 32

C = 48

**Flash memory size**

6 = 32 Kbytes

8 = 64 Kbytes

**Package type**

T = LQFP

P = TSSOP

**Temperature range**

6 = -40 to 85°C (105°C junction)

**Options**

␣TR = tape and reel packing

␣␣␣ = tray packing

other = 3-character ID incl. custom Flash code and packing information

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, contact your nearest ST sales office.

# 8 Important security notice

The STMicroelectronics group of companies (ST) places a high value on product security, which is why the ST product(s) identified in this documentation may be certified by various security certification bodies and/or may implement our own security measures as set forth herein. However, no level of security certification and/or built-in security measures can guarantee that ST products are resistant to all forms of attacks. As such, it is the responsibility of each of ST's customers to determine if the level of security provided in an ST product meets the customer needs both in relation to the ST product alone, as well as when combined with other components and/or software for the customer end product or application. In particular, take note that:

- ST products may have been certified by one or more security certification bodies, such as Platform Security Architecture (www.psacertified.org) and/or Security Evaluation standard for IoT Platforms (www.trustcb.com). For details concerning whether the ST product(s) referenced herein have received security certification along with the level and current status of such certification, either visit the relevant certification standards website or go to the relevant product page on www.st.com for the most up to date information. As the status and/or level of security certification for an ST product can change from time to time, customers should re-check security certification status/level as needed. If an ST product is not shown to be certified under a particular security standard, customers should not assume it is certified.
- Certification bodies have the right to evaluate, grant and revoke security certification in relation to ST products. These certification bodies are therefore independently responsible for granting or revoking security certification for an ST product, and ST does not take any responsibility for mistakes, evaluations, assessments, testing, or other activity carried out by the certification body with respect to any ST product.
- Industry-based cryptographic algorithms (such as AES, DES, or MD5) and other open standard technologies which may be used in conjunction with an ST product are based on standards which were not developed by ST. ST does not take responsibility for any flaws in such cryptographic algorithms or open technologies or for any methods which have been or may be developed to bypass, decrypt or crack such algorithms or technologies.
- While robust security testing may be done, no level of certification can absolutely guarantee protections against all attacks, including, for example, against advanced attacks which have not been tested for, against new or unidentified forms of attack, or against any form of attack when using an ST product outside of its specification or intended use, or in conjunction with other components or software which are used by customer to create their end product or application. ST is not responsible for resistance against such attacks. As such, regardless of the incorporated security features and/or any information or support that may be provided by ST, each customer is solely responsible for determining if the level of attacks tested for meets their needs, both in relation to the ST product alone and when incorporated into a customer end product or application.
- All security features of ST products (inclusive of any hardware, software, documentation, and the like), including but not limited to any enhanced security features added by ST, are provided on an "AS IS" BASIS. AS SUCH, TO THE EXTENT PERMITTED BY APPLICABLE LAW, ST DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING BUT NOT LIMITED TO THE IMPLIED WARRANTIES OF MERCHANTABILITY OR FITNESS FOR A PARTICULAR PURPOSE, unless the applicable written and signed contract terms specifically provide otherwise.

# 9 Revision history

**Table 73. Document revision history**

| Date | Revision | Changes |
|---|---|---|
| 16-Dec-2020 | 1 | Initial release |
| 09-Feb-2021 | 2 | Modified classes in *Table 45: ESD absolute maximum ratings*.<br>Added maximum values in *Table 28: Current consumption in Stop 1 mode*.<br>Document status changed to *Production data*. |
| 17-Jun-2025 | 3 | Updated cover page;<br>Updated *Section 1: Introduction*;<br>In *Section 2: Description*, updated leading text, *Table 2: STM32G050x6/x8 family device features and peripheral counts*, and *Figure 1: Block diagram*;<br>In *Section 3: Functional overview*, updated *Section 3.3: Embedded flash memory*: removed information on PCROP, removed section 3.3.1 Securable area, added information on OTP in *Table 3: Access status versus readout protection level and execution modes*; updated *Section 3.5: Boot modes*, *Section 3.7: Power supply management* and *Figure 2: Power supply overview*, *Section 3.14: Analog-to-digital converter (ADC)* in which *Table 5: Temperature sensor calibration values* by removing TS_CAL2 row,*Section 3.15.1: Advanced-control timer (TIM1)*;<br>In *Section 4: Pinouts, pin description and alternate functions*, package figures updated and re-ordered from smallest to largest, updated *Table 11: Terms and symbols used in Pin assignment and description table*, updated information for pins NRST, PA11 and PA12 in *Table 12: Pin assignment and description*;<br>In *Section 5.2: Absolute maximum ratings*, added information on mission profile and updated *Table 18: Voltage characteristics*;<br>In *Section 5.3: Operating conditions*, all table footnotes “Guaranteed by design” changed to “Specified by design. Not tested in production”, updated *Table 21: General operating conditions*, *Table 23: Embedded reset and power control block characteristics* - corrected $V_{POR}$ and $V_{PDR}$ values, *Section : I/O system current consumption*, *Table 44: EMI characteristics*, *Section : General input/output characteristics* (a note added), *Table 50: Output voltage characteristics*, title change for *Section : Output buffer timing characteristics* and *Table 51: Non-FT_c I/O output timing characteristics*, added *Table 52: FT_c I/O output timing characteristics*, updated *Figure 17: I/O AC characteristics definition*, *Figure 18: Recommended NRST pin protection*, added *Section 5.3.16: Extended interrupt and event controller input (EXTI) characteristics*, updated *Table 56: ADC characteristics*, *Table 58: ADC accuracy*, *Figure 19: ADC accuracy characteristics*, *Figure 20: ADC typical connection diagram*, *Figure 21: SPI timing diagram - slave mode and CPHA = 0*, *Figure 22: SPI timing diagram - slave mode and CPHA = 1*, *Figure 23: SPI timing diagram - master mode*, title of *Section : USART (SPI mode) characteristics* and *Table 68: USART characteristics in SPI mode*, added *Figure 26: USART timing diagram in SPI master mode* and *Figure 27: USART timing diagram in SPI slave mode*;<br>Updated *Section 6: Package information*, with added *Section 6.1: Device marking*, and removed corresponding subsections for all packages;<br>Updated *Table 72: Package thermal characteristics*;<br>Added *Section 8: Important security notice*. |